

Cheiron school 2015 , 12th Sep. 2015, SPring-8
Hard X-ray beamline Optics

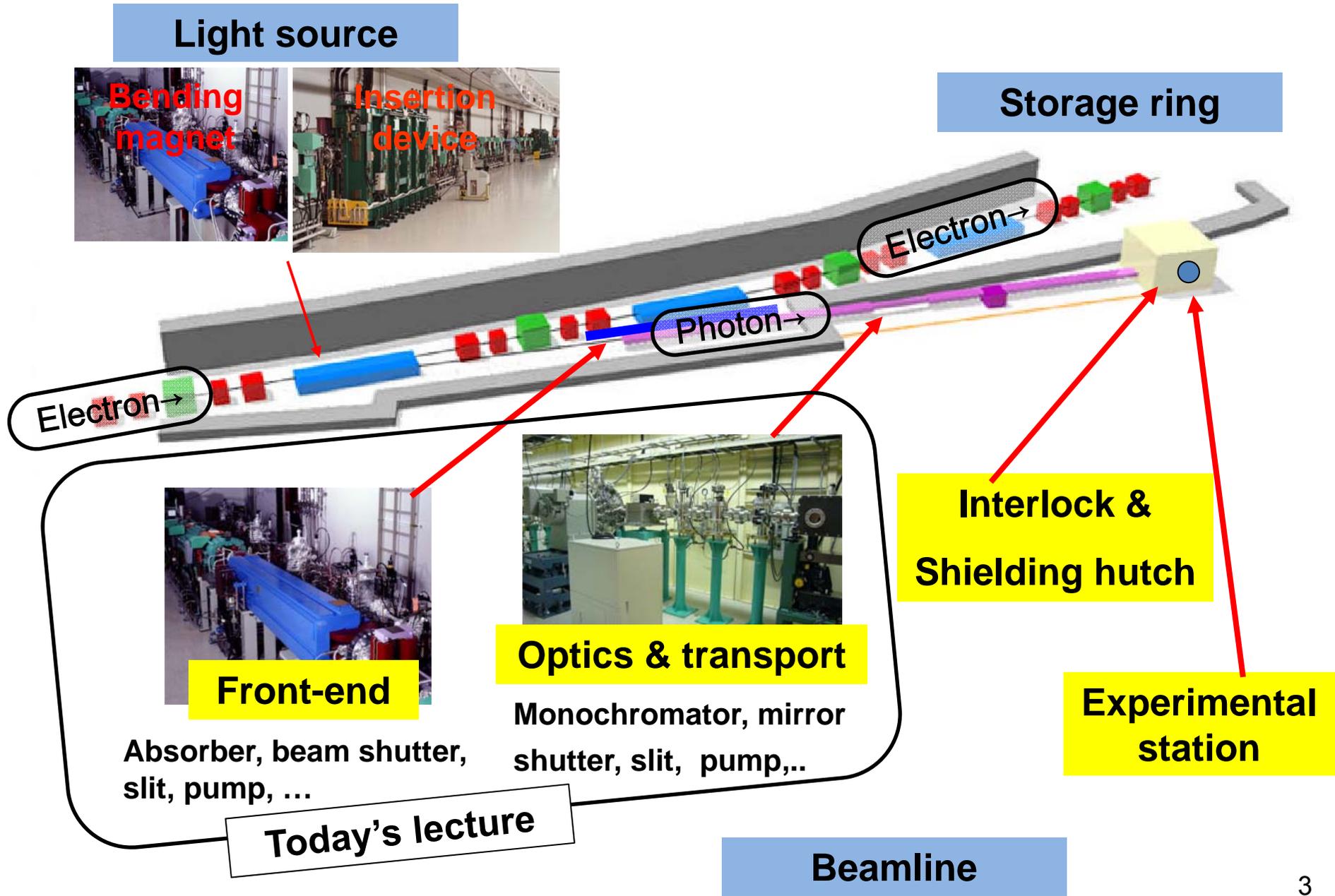
Hard X-ray Beamline Optics

~Engineering of x-ray beamline ~

Haruhiko Ohashi

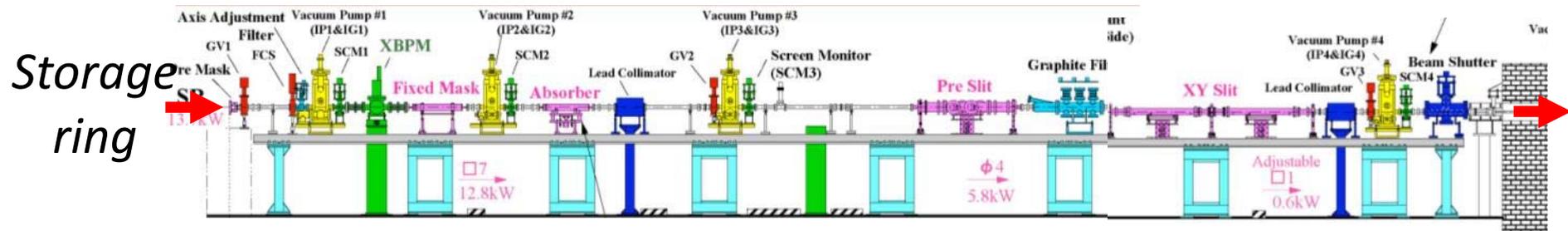
JASRI / SPring-8

Where is "beamline" ?

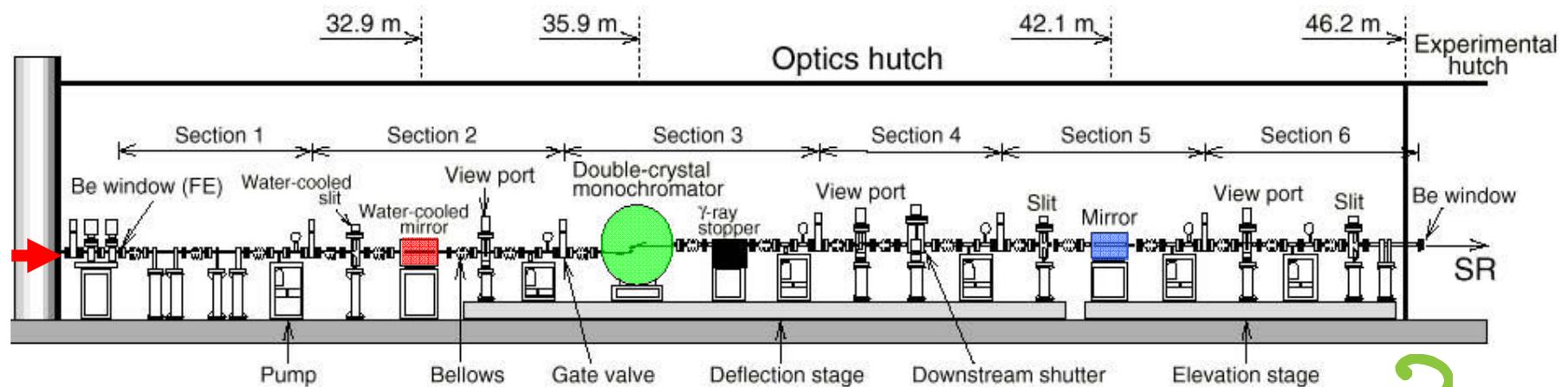


Introduction

“X-ray beamline looks complicated?”



Inside shielding tunnel (front end)



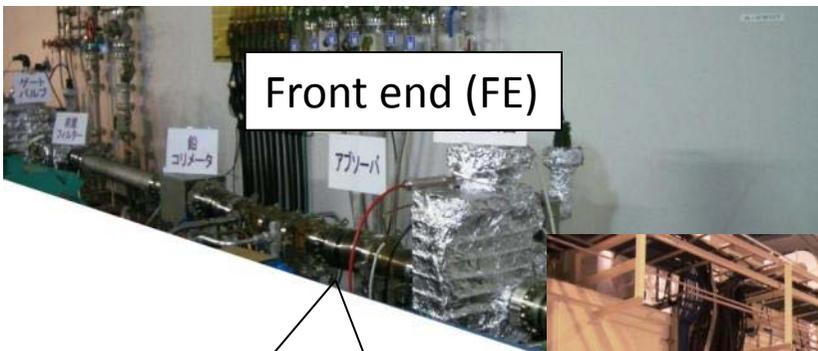
Outside shielding tunnel (optics hutch)

What function of each component ?



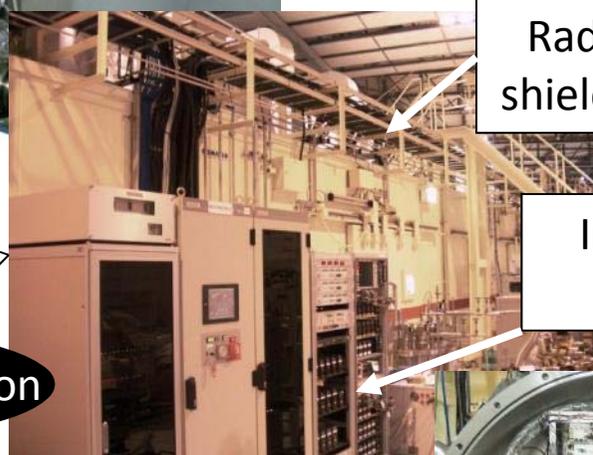


Light source (IDs/BM)



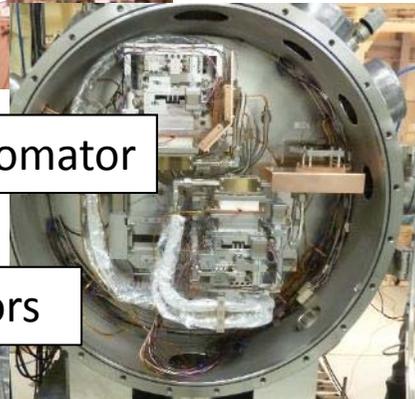
Front end (FE)

X-ray beamline



Radiation shield hutch

Interlock system

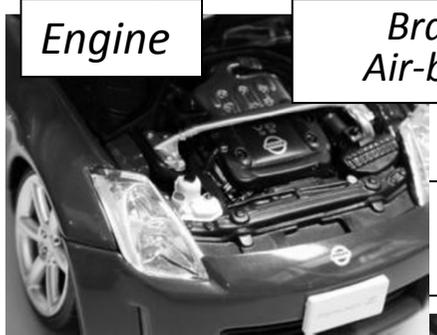


Monochromator

Mirrors



End station



Engine

Brake
Air-bags



Transmission
Gear



Steering wheel
Dashboard
Gear lever

A vehicle

Light source
(Power)

Human safety

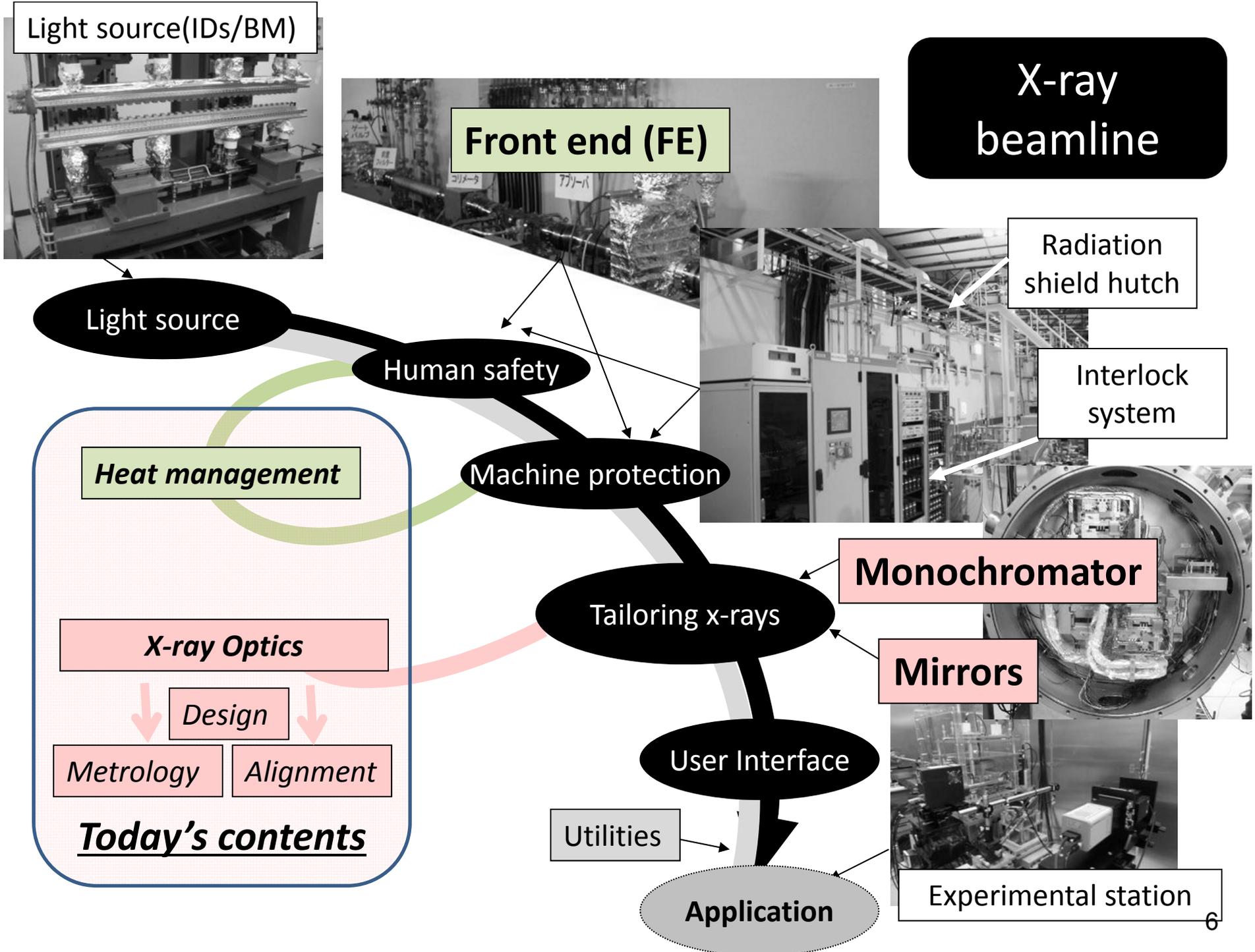
Machine protection

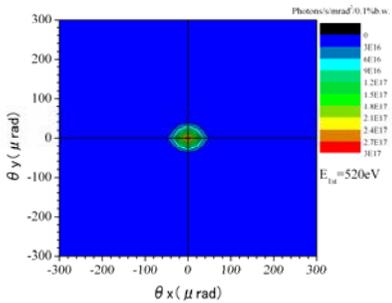
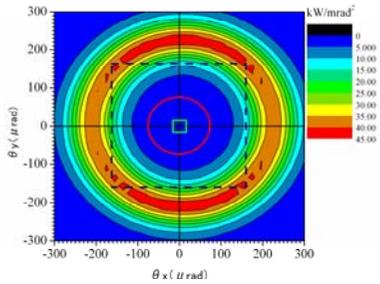
Tailoring x-rays
(Power control)

User Interface

Application
(drive)

Radiator
Body

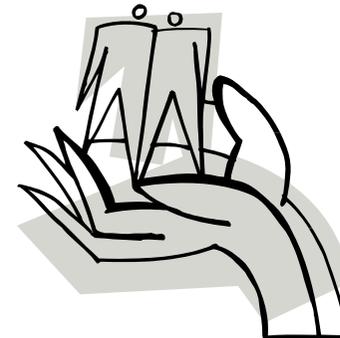




Heat management for human safety & machine protection



Front end
(FE)

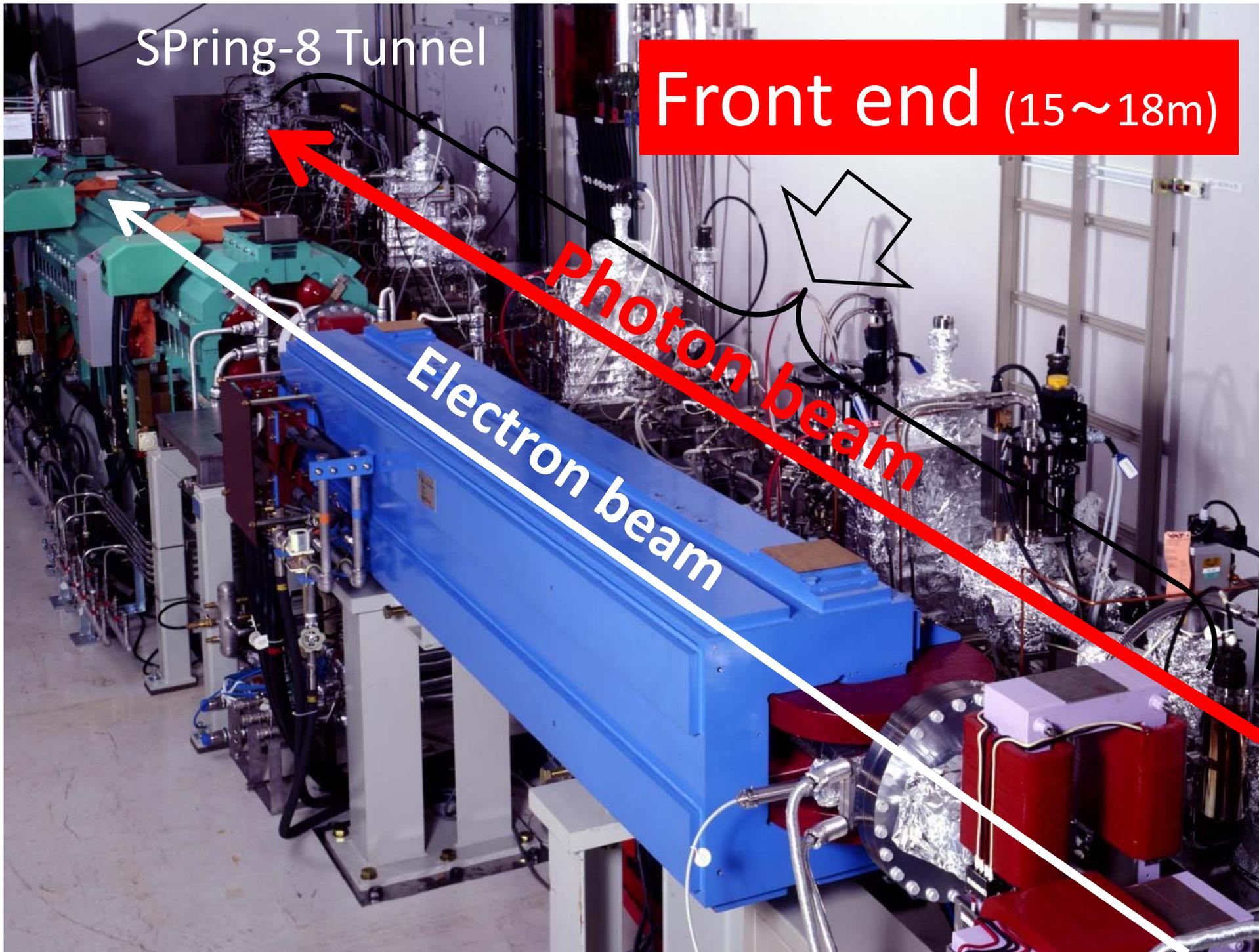


SPring-8 Tunnel

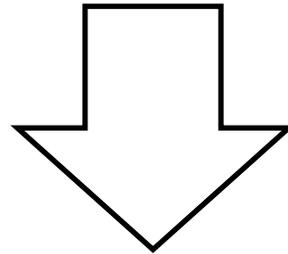
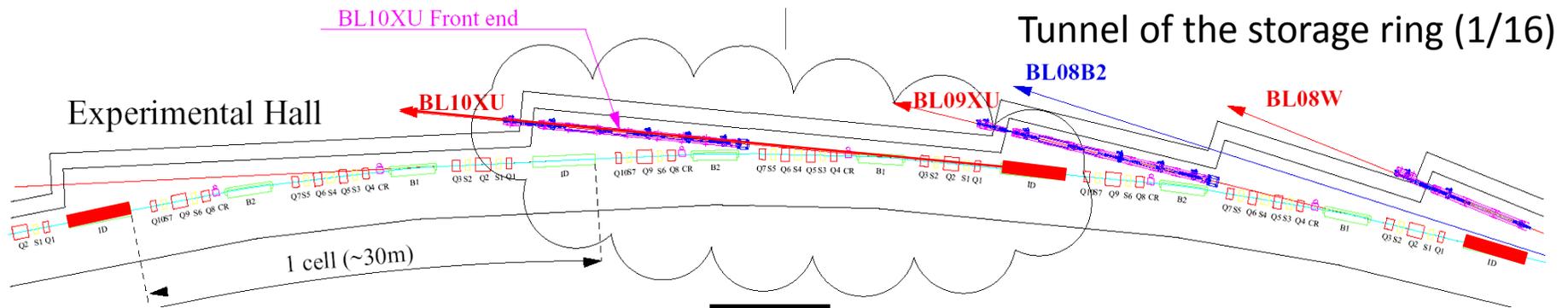
Front end (15~18m)

Photon beam

Electron beam



Schematic Layout inside the SPring-8 Tunnel



Front end (FE)

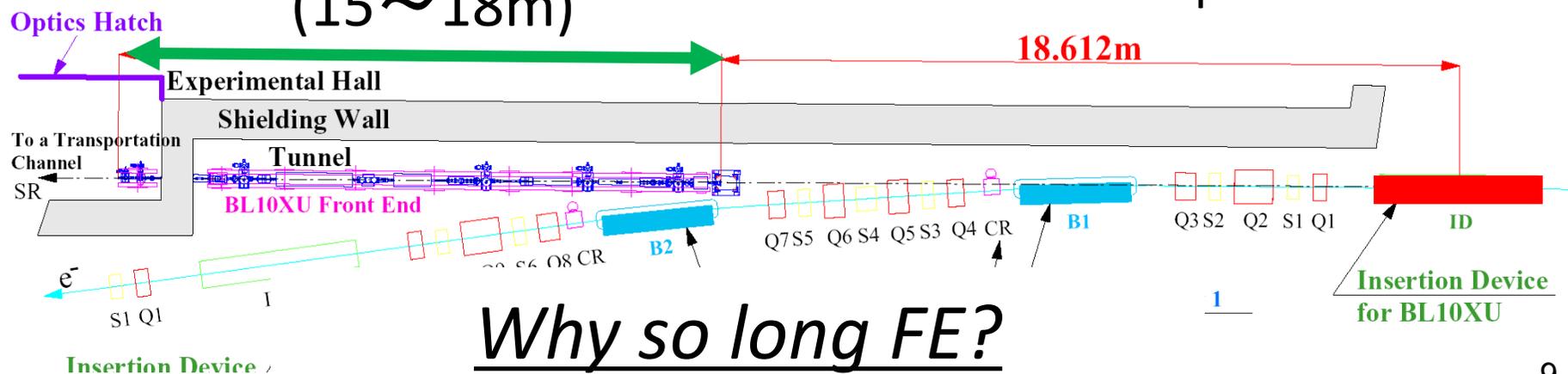
(15 ~ 18m)

Standard
in-vacuum undulator

Power density :

500 kW/mrad²

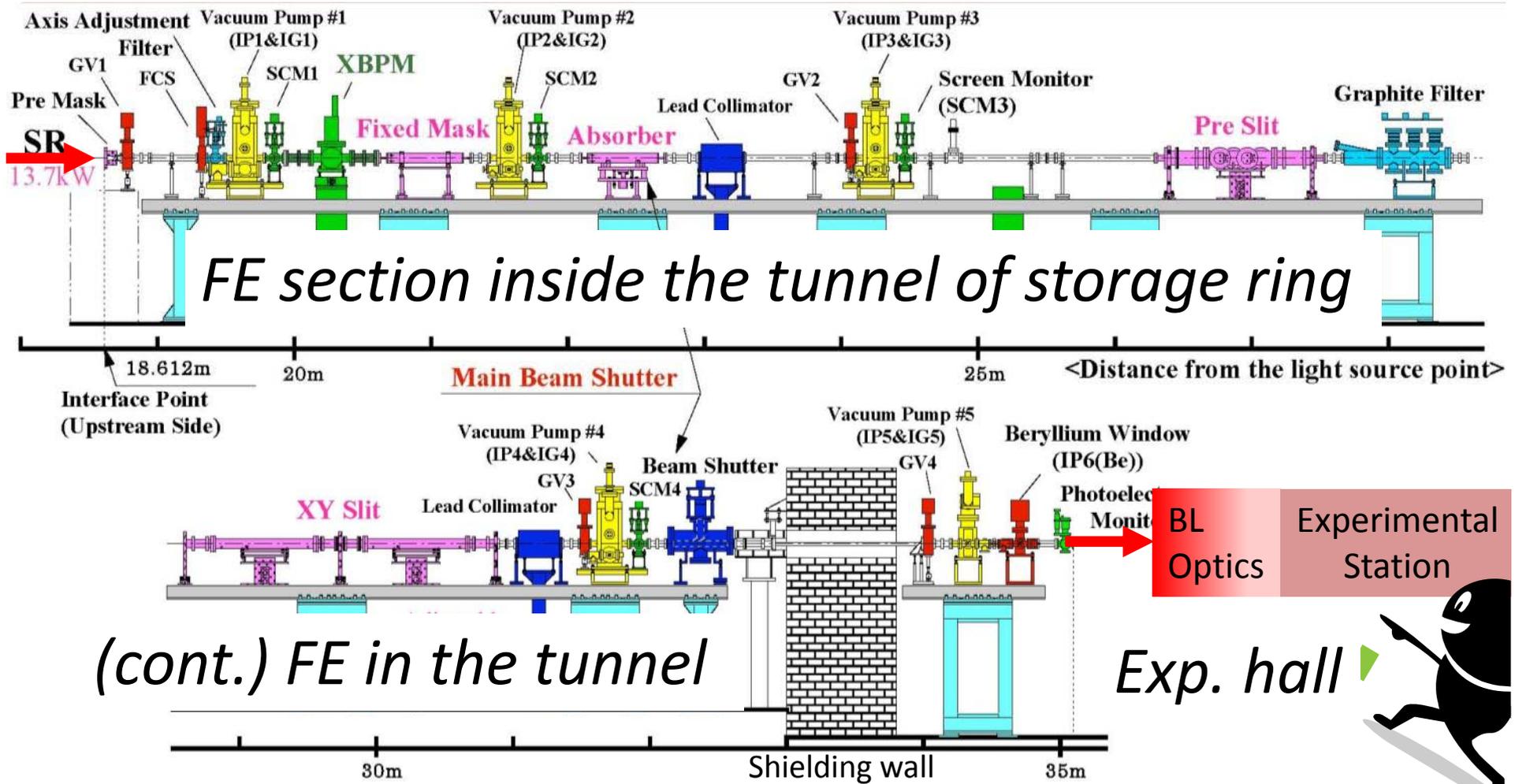
Total power : 13 kW



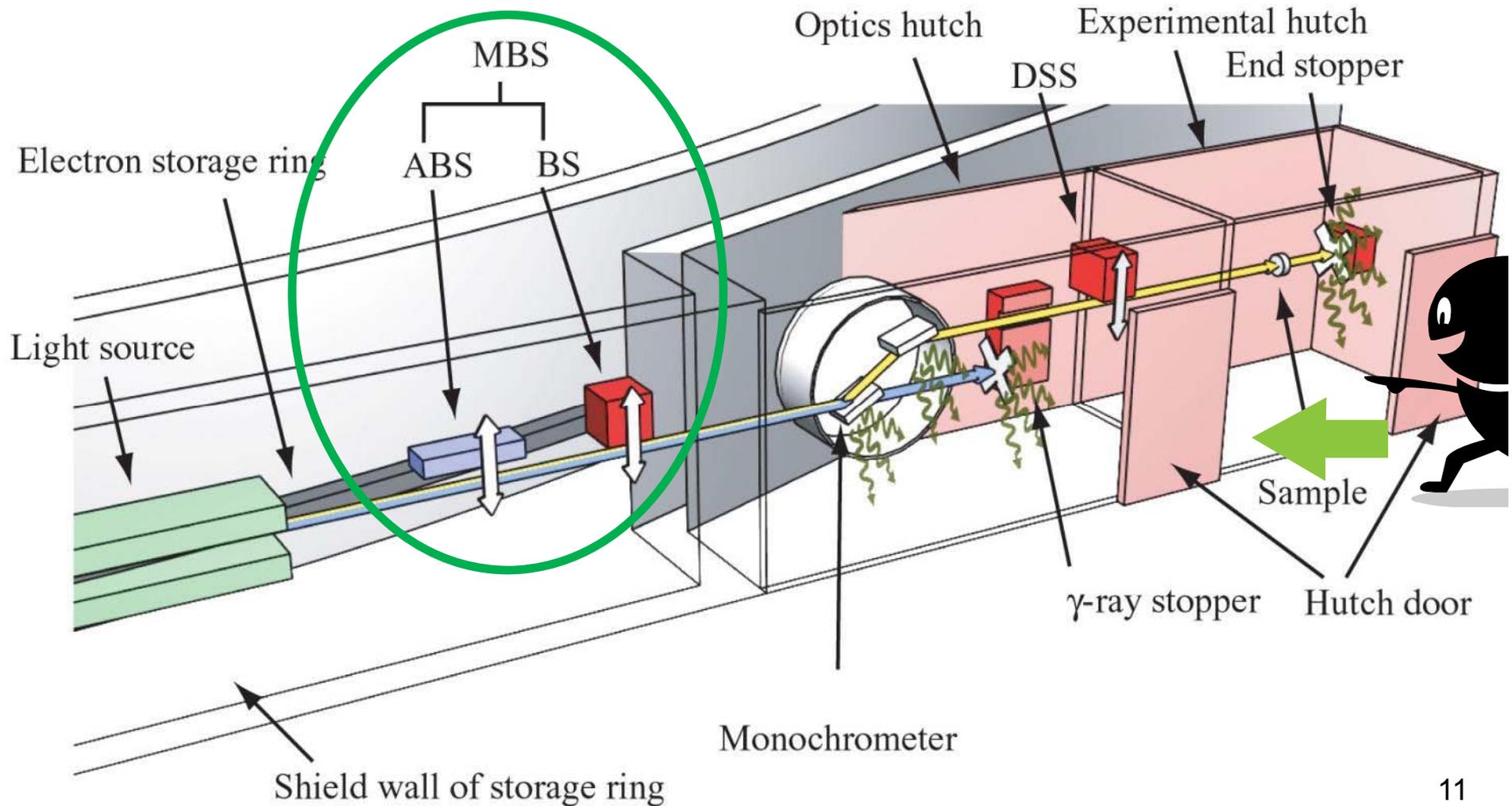
Key functions & components of FE

- ✓ *Shielding for human safety*
- ✓ *Handling high heat load for safety*
- ✓ *Handling high heat load for optics*
- ✓ *Monitoring the x-ray beam position*
- ✓ *Protection of the ring vacuum*

- Beam shutter (BS)**, collimator
- Absorber**, masks
- XY slit**, filters
- XBPM** (x-ray BPM), **SCM** (screen monitor)
- FCS** (fast closing shutter), **Vacuum system**



What's "Main Beam Shutter" ?

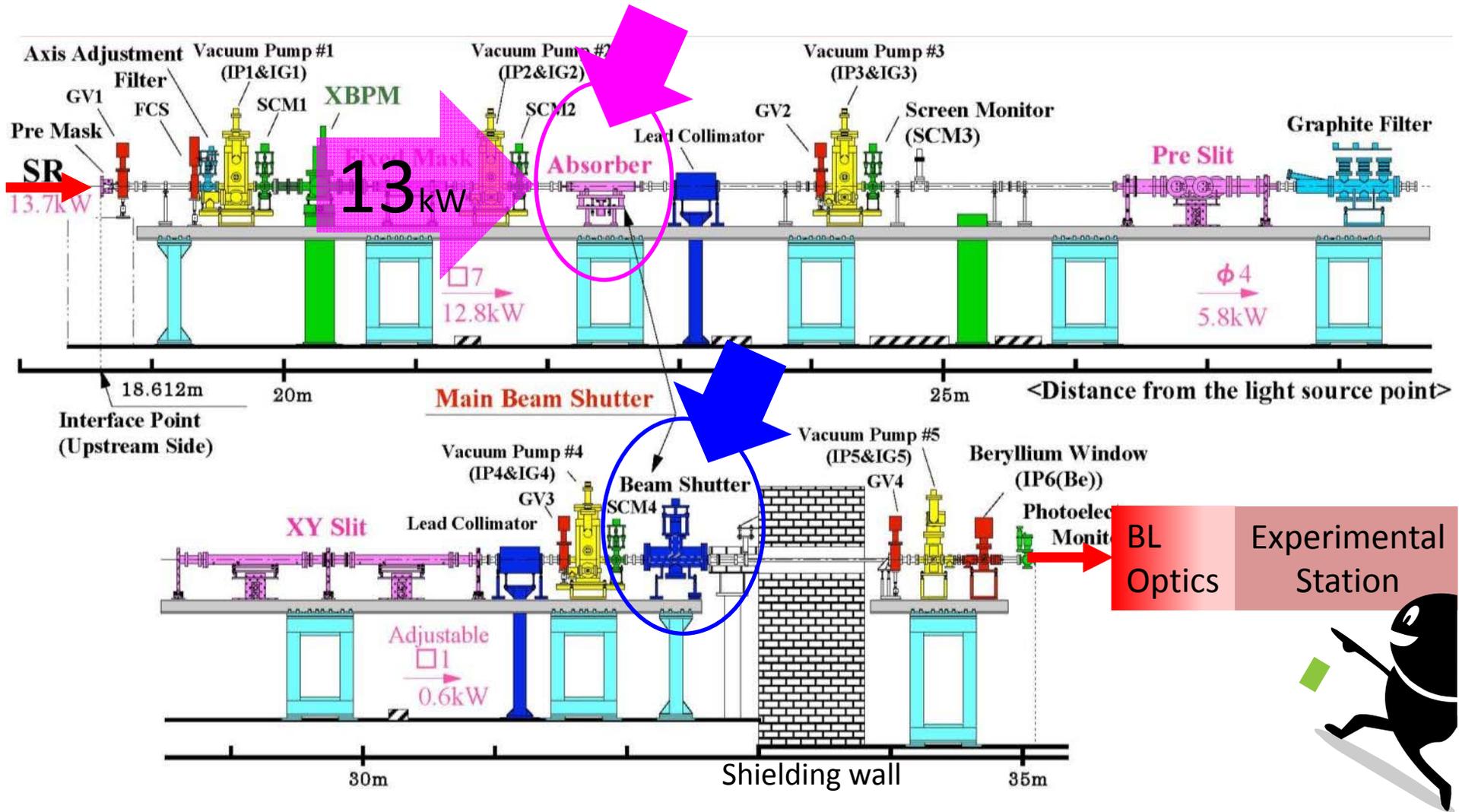


Key functions & components of FE

For safety

- ✓ *Shielding for human safety*
- ✓ *Handling high heat load for safety*

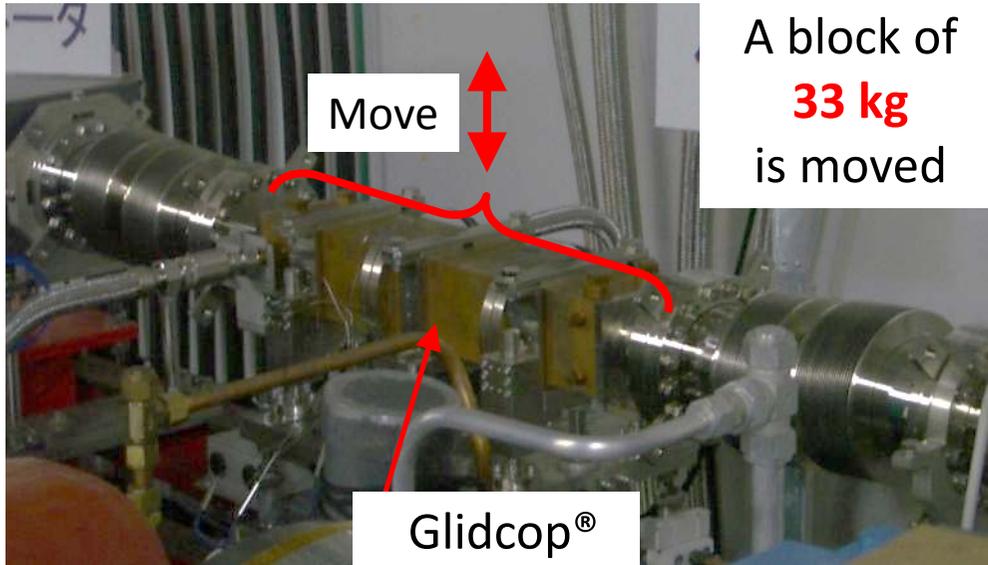
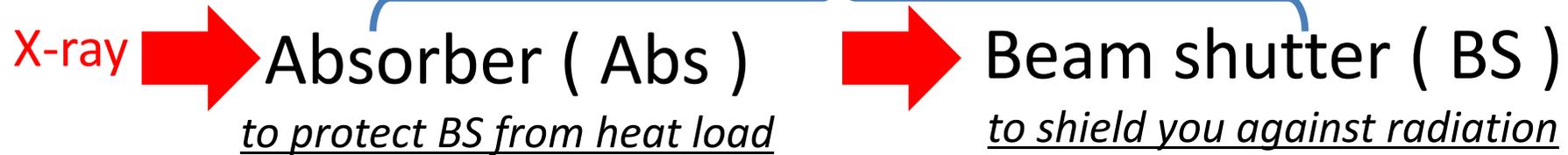
Beam shutter (BS), collimator
Absorber, masks



MBS (= **ABS** + **BS**) is closed \rightarrow MBS accepts the incident power from ID.



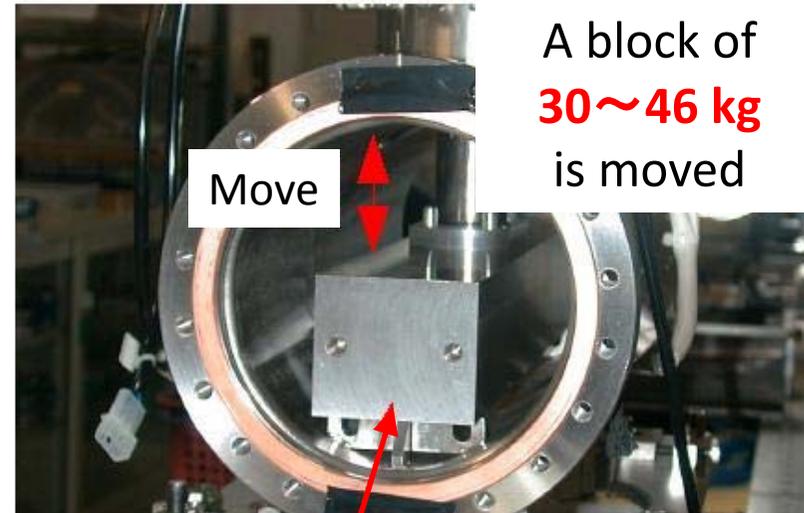
When we operate a main beam shutter (MBS), what happens ?



A block of **33 kg** is moved

Glidcop®

(copper that is dispersion-strengthened with ultra-fine particles of aluminum oxide)

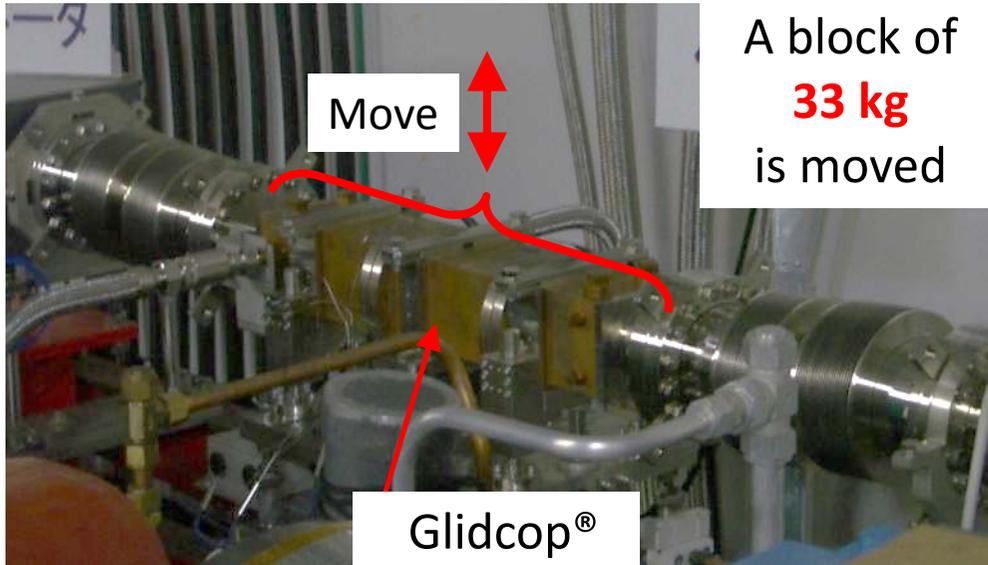
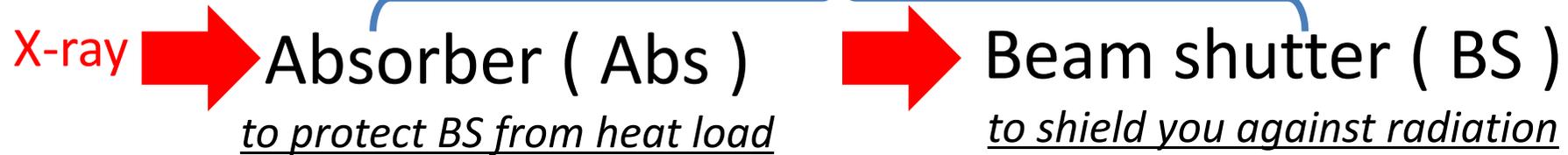


A block of **30~46 kg** is moved

Heavy metal (alloy of tungsten)

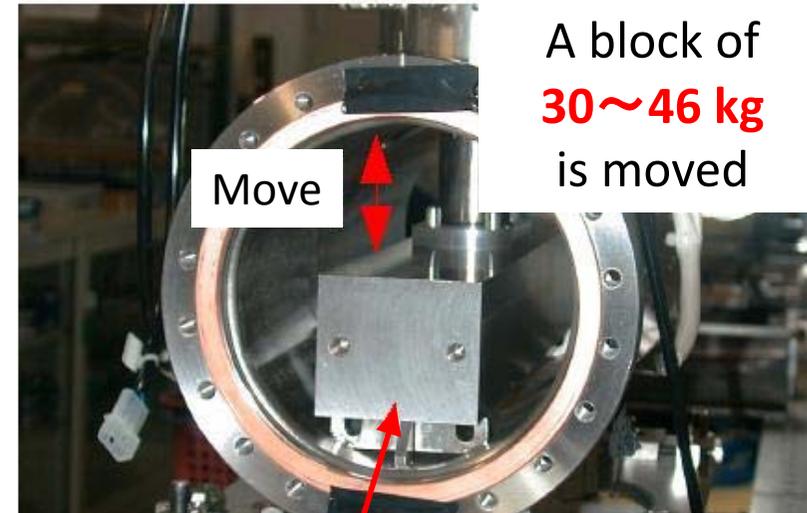
the thermal conductivity not so high

When we operate a main beam shutter (MBS), what happens ?



A block of **33 kg** is moved

(copper that is dispersion-strengthened with ultra-fine particles of aluminum oxide)



A block of **30~46 kg** is moved

Heavy metal (alloy of tungsten)

the thermal conductivity not so high



After BS is fully opened, Abs is opened.
After Abs is fully closed, BS is closed.
The sequences are essential to keeping safety.



ABS and BS work on ways together

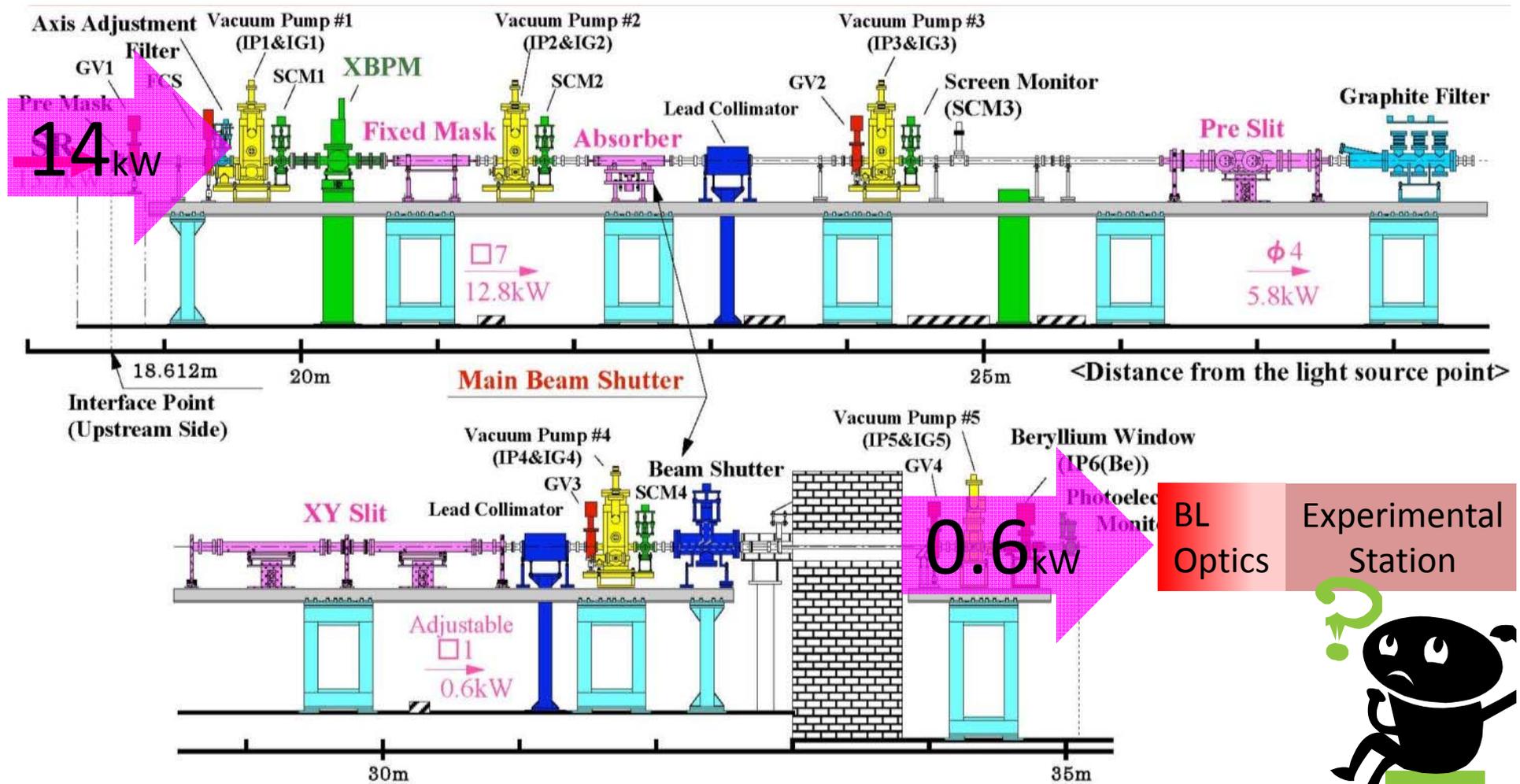
to protect us from radiation when we enter the hutch.

What components remove most “power” from ID ?

For managing heat load

Total power from ID = 14 kW

The power through FE section = 0.6 kW



BL Optics Experimental Station



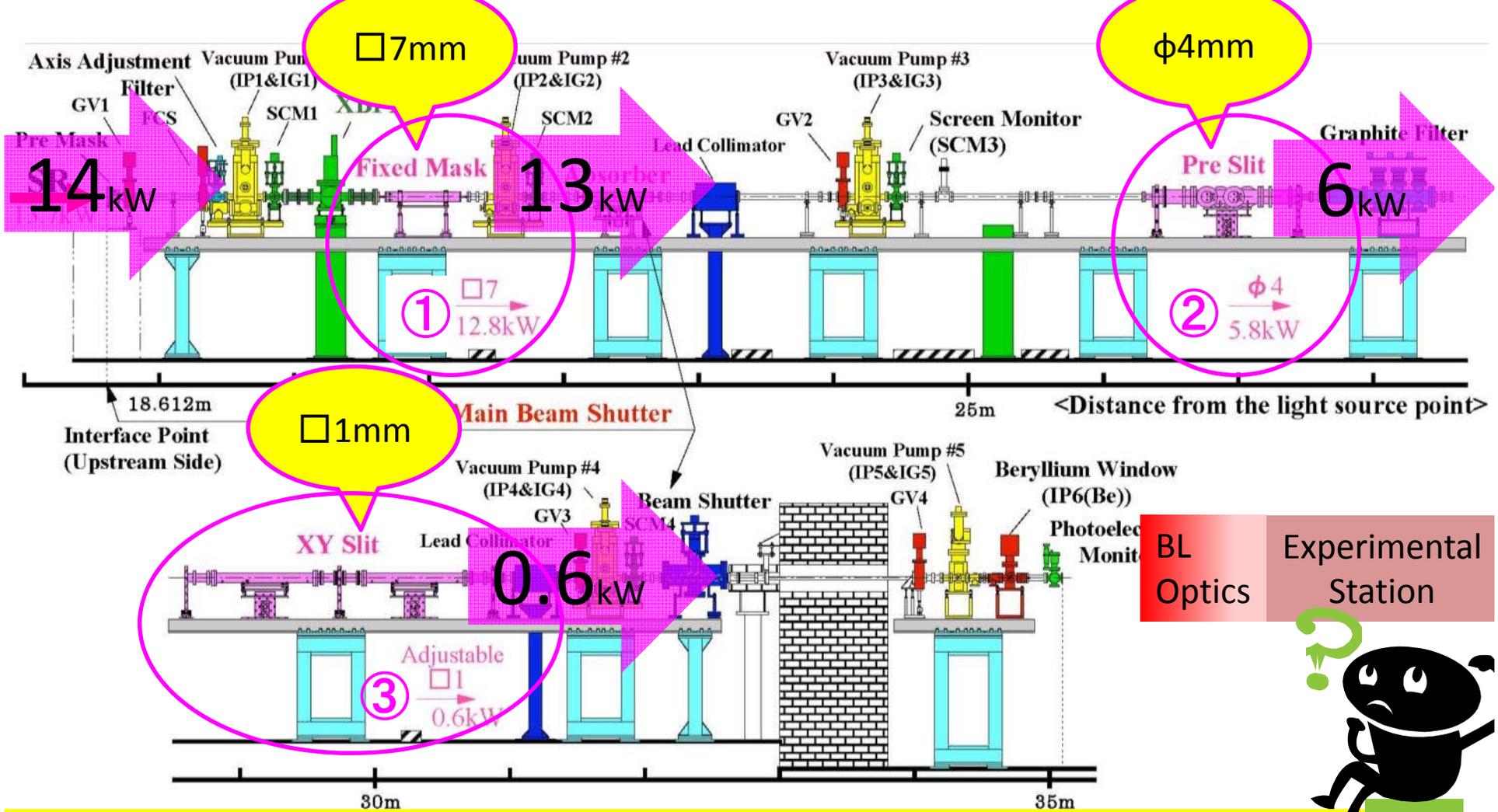
What components remove most “power” from ID ?

For managing heat load

Absorber, masks (to prevent BS from melting)

XY slit, filters (to prevent optics from distorting)

These components (①, ② and ③) cut off the power to prevent optics from distorting by heat load.



BL Optics Experimental Station



Someone may enlarge opening of XY slit to get more “flux” → You can NOT get it!

FE: “For users to take lion’s share”

For managing heat load

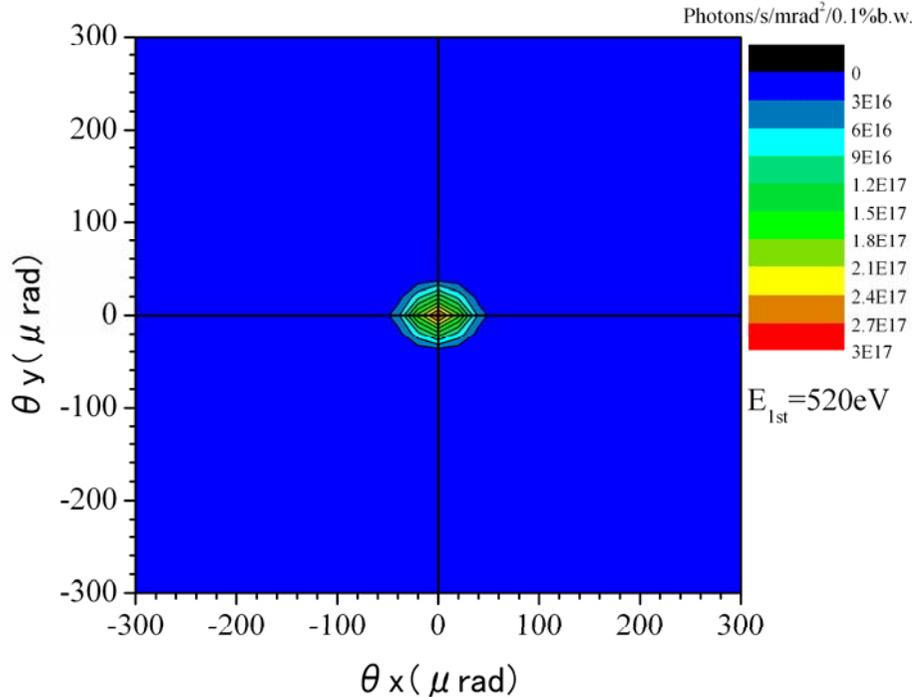
Adding a spatial limitation to photon beam, supplying only a good quality part around the central axis of ID to transport optical system safely and stably.

① Fixed Mask Aperture 322μrad x 322μrad

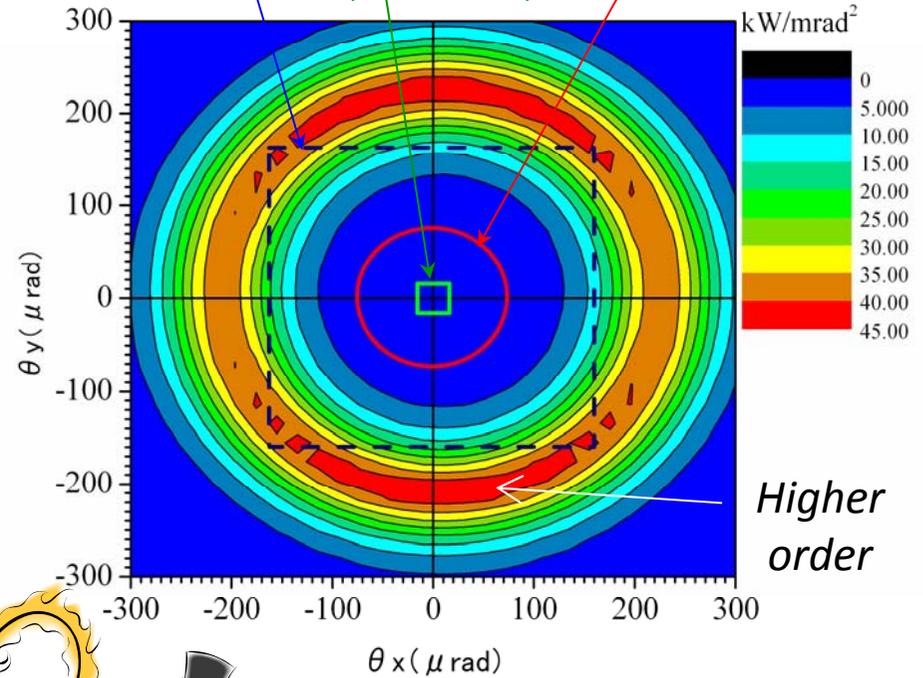
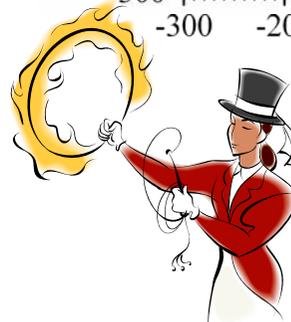
② Pre Slit Aperture φ152μrad

③ XY Slit Aperture 35μrad x 35μrad

The size of XY slit is set to 1.05mm □. XY slit is installed ~30m away from ID.



1st harmonic
Flux Density



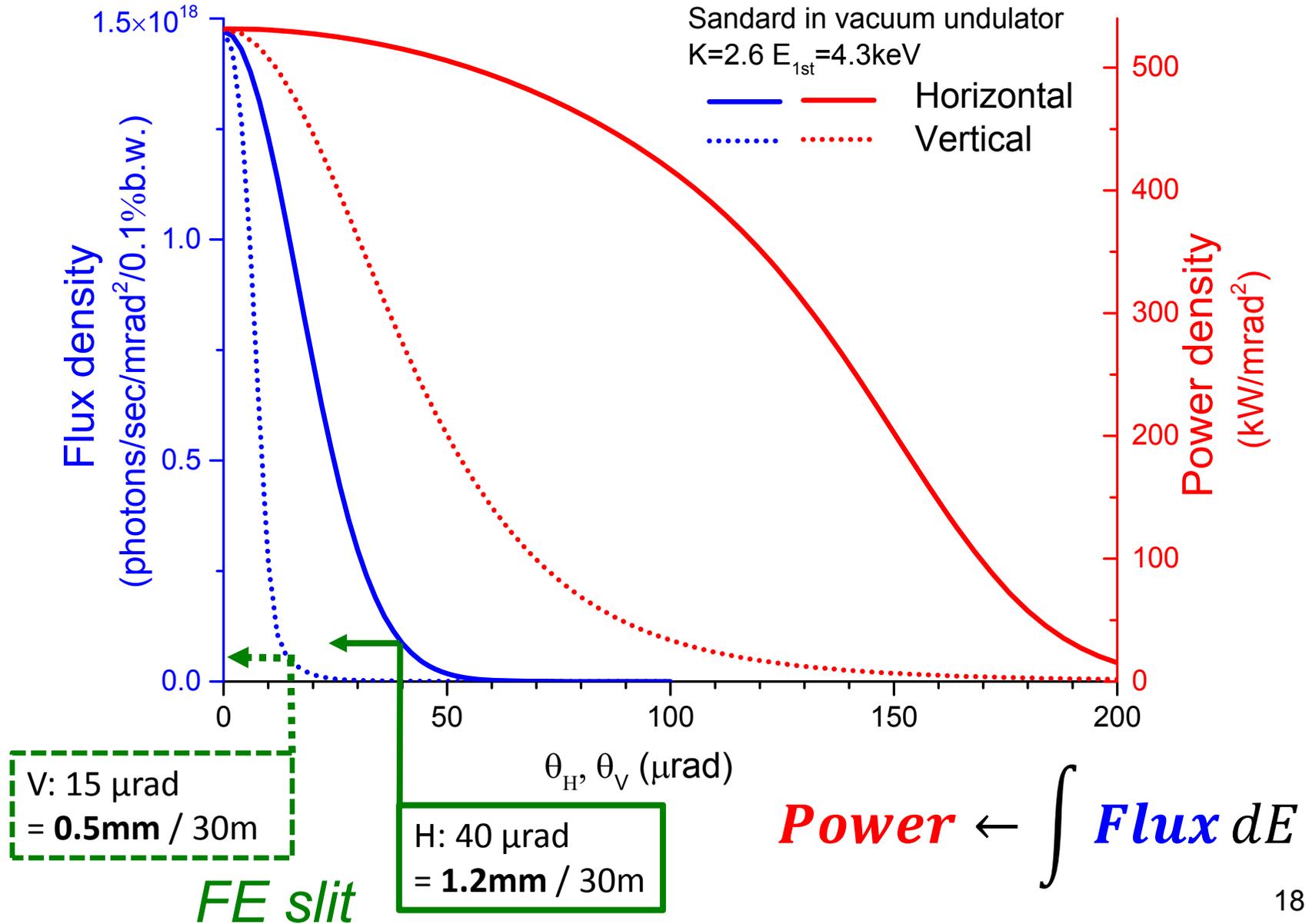
Power Density

Helical Mode Operation
at BL15XU 17

Comparison of the Spatial Distribution

For managing heat load

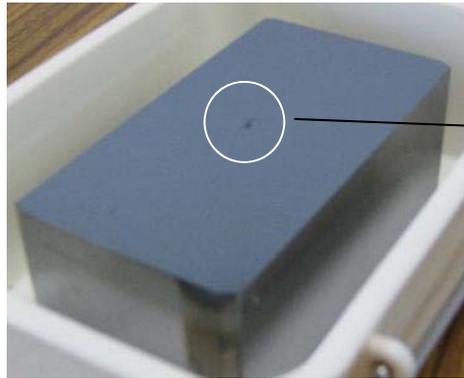
between 1st harmonic Flux density and Power density



If an optical component is irradiated
by too much power

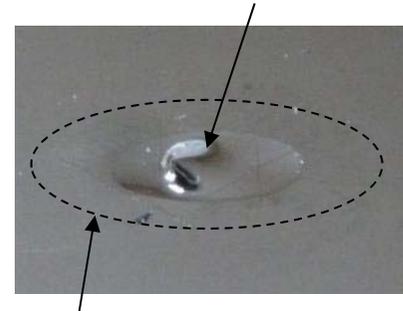
One user opened FE slit excessively.

2kW

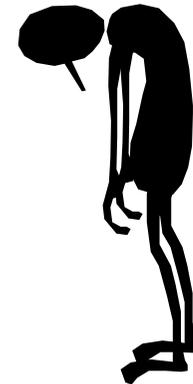


LN2-cooled
Si crystal

Melted



Damaged area

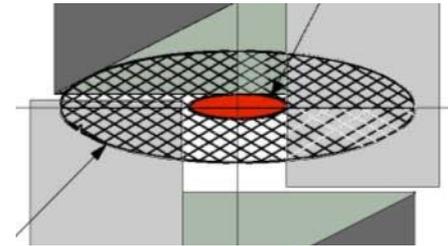


Slit : *“Too much is as bad as too little”*

How to manage high heat load by FE XY slit ?

For managing heat load

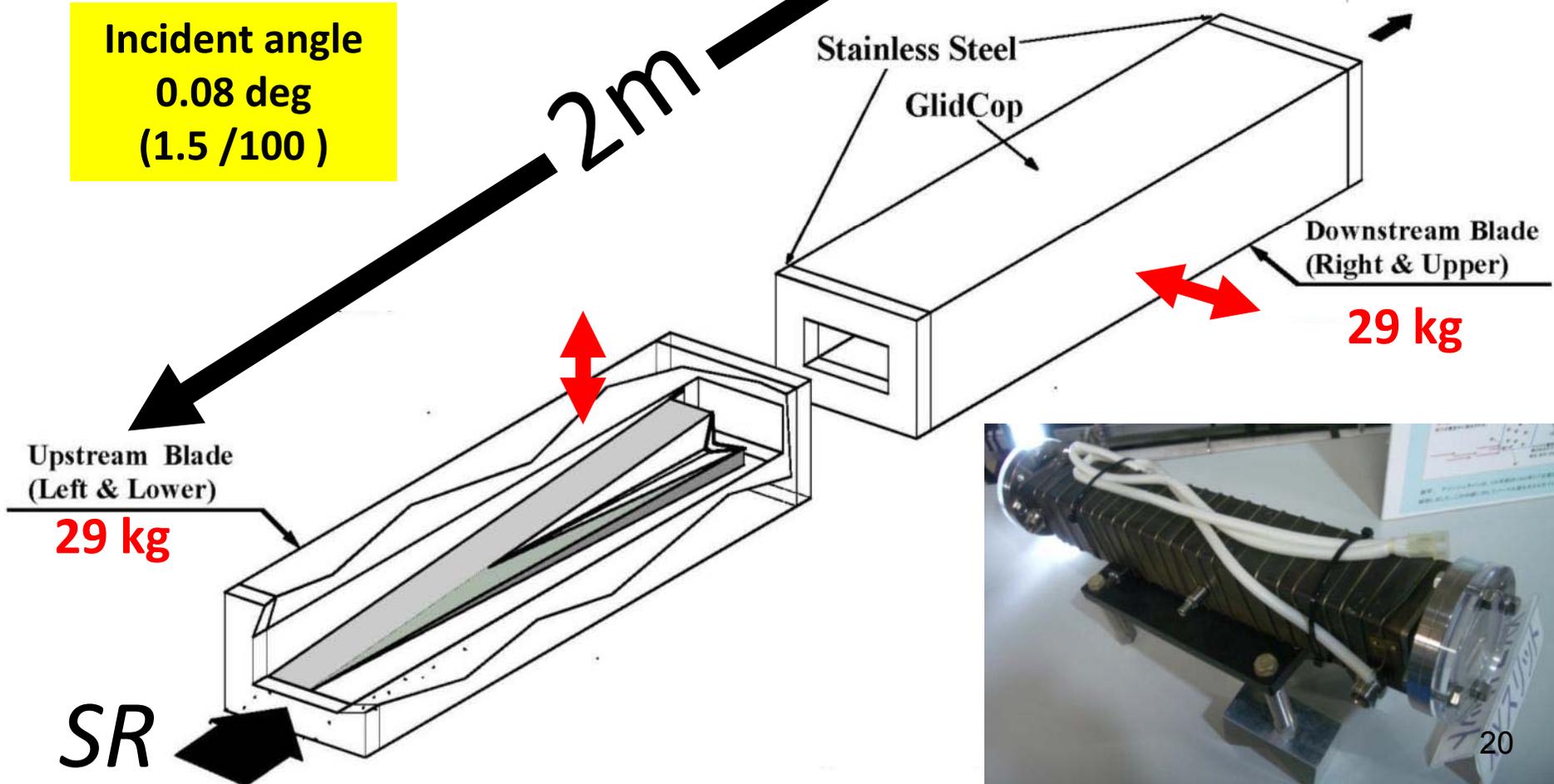
1st harmonic flux



Spatial distribution of power

Incident angle
0.08 deg
(1.5 / 100)

2m



Key issues of front end

1. *Key functions of components in front end :*

They have their proper functions, proper missions based on the principles of human **radiation safety**, **vacuum protection**, **heat-load** and **radiation damage** protection of themselves.

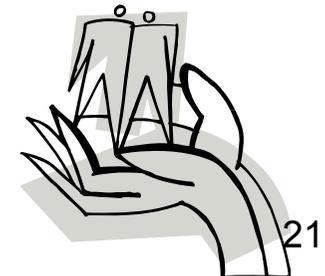
They have to deal with every mode of ring operation and every mode of beamline activities.

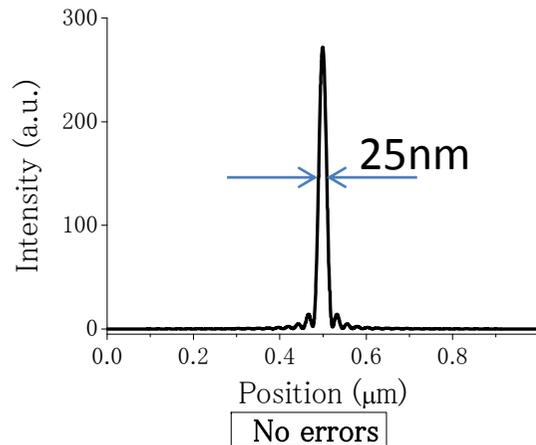
2. *Any troubles in one beamline should **not make any negative effect to the other beamlines.***

3. *Strongly required to be a **reliable and stable** system.*

We have to adopt key technologies which are reliable, stable and fully established as far as possible.

Higher the initial cost, the lower the running cost from the long-range cost-conscious point of view.





*Tailoring x-rays
to application*



X-ray mirrors

design, errors, metrology
& alignment

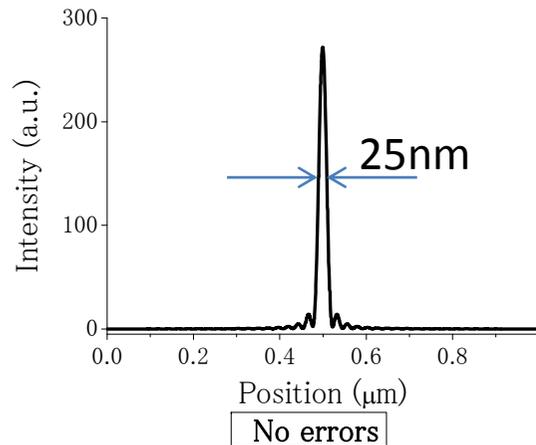


The functions of x-ray mirrors

- ✓ Deflecting
- ✓ Low pass filter
- ✓ Focusing
- ✓ Collimating

- Separation from γ -ray
- Branch / switch beamline
- Higher order suppression
- Micro- / nano- probe
- Imaging
- Energy resolution
w. multilayer or crystal mono.



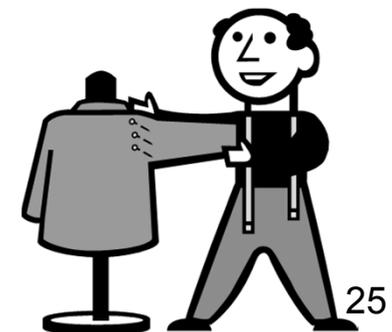


*Tailoring x-rays
to application*



X-ray mirrors

design, errors, metrology
& alignment



Design parameters of x-ray mirror

Requirement

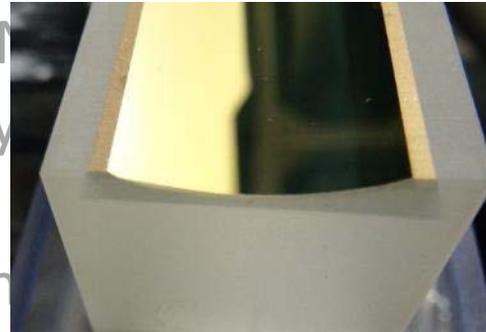
the beam properties both of incident and reflected x-rays

(size, angular divergence / convergence, direction, energy region, power...)

We have to know well what kinds beam irradiate on the mirror.

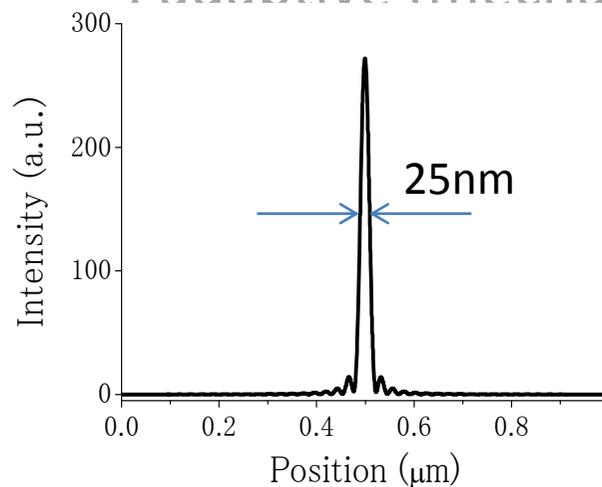
Design parameters

- ✓ Coating (Au, Pt, Mo, Cr), thickness
- ✓ Multilayer / graded ML
- ✓ Incident angle / grazing
- ✓ Substrate shape (flat, spherical) → How to select



: adaptive (mechanically bent, bimorph)

- ✓ Substrate shape
- ✓ Substrate size
- ✓ w/o cooling
- ✓ Substrate material



dal...
dth
iter or LN₂...
op...
ess...



In addition,
some errors s

Design parameters of x-ray mirror

Requirement

the beam properties both of incident and reflected x-rays

(size, angular divergence / convergence, direction, energy region, power...)

We have to know well what kinds beam irradiate on the mirror.

Design parameters

- ✓ Coating material : Rh, Pt, Ni ... (w/o binder , Cr), thickness
: multilayers (ML), laterally graded ML
- ✓ Incident angle : grazing angle (mrad)
- ✓ Surface shape : flat, sphere, cylinder, elliptic ...
: adaptive (mechanically bent, bimorph)
- ✓ Substrate shape : rectangular, trapezoidal...
- ✓ Substrate size : length, thickness, width
- ✓ w/o cooling : indirect or direct, water or LN₂...
- ✓ Substrate material : Si, SiO₂, SiC, Glidcop...

⇒ How to select



In addition,

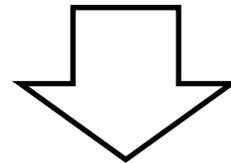
some errors such as figure error, roughness...

How to select coating material and incident angle ?

Reflectivity for grazing incident mirrors

$$R(\lambda, \theta, n) = \left| \frac{k_1 - k_2}{k_1 + k_2} \right|^2$$

$$k_1 = \frac{2\pi}{\lambda} \cos \theta, k_2 = \frac{2\pi}{\lambda} \sqrt{n^2 - \cos^2 \theta}$$



The complex index of refraction

Coating material (1)

“*the complex index of refraction*”

The complex atomic scattering factor for the *forward scattering*

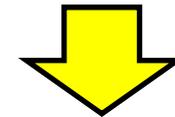
$$f = f_1 + if_2$$

The complex index of refraction

$$n = 1 - \delta - i\beta$$

$$E \propto e^{-i(\omega t - kr)}$$

Small
for x-ray region



$$\left\{ \begin{array}{l} \delta = \frac{Nr_0\lambda^2}{2\pi} f_1(\lambda) \\ \beta = \frac{Nr_0\lambda^2}{2\pi} f_2(\lambda) \end{array} \right.$$

	$\delta (\times 10^{-5})$	$\beta (\times 10^{-7})$
Si	0.488	0.744
Quartz	0.555	2.33
Pt	3.26	20.7
Au	2.96	19.5

$$r_0 = \frac{e^2}{4\pi mc^2} = 2.82 \times 10^{-15} m$$

$$\beta = \frac{\mu\lambda}{4\pi}$$

μ : linear **absorption** coefficient

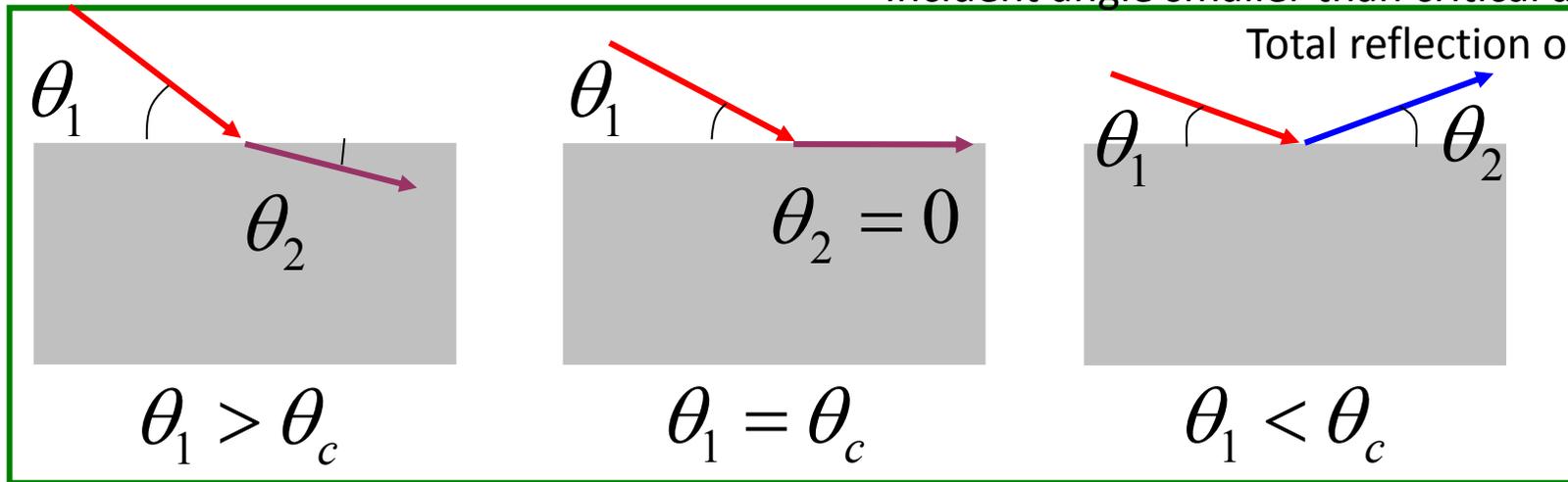
N: Number of atoms per volume

Coating material (2)

“total reflection”

$$\cos(\theta_1)/\cos(\theta_2) = n_2/n_1 \quad \leftarrow \text{Snell's law}$$

Incident angle smaller than critical angle,



$$\cos(\theta_c) = n = 1 - \delta, \cos(\theta_c) \approx 1 - \theta_c^2 / 2$$

$$\theta_c \cong \sqrt{2\delta} = 1.6 \times 10^{-2} \lambda \sqrt{\rho} = 20 \sqrt{\rho} / E$$

For example,

θ_c (rad), ρ (g/cm³), λ (nm), E (eV)

Rh ($\rho = 12.4$ g/cm³) $\lambda = 0.1$ nm, $\theta_c = 5.68$ mrad

Coating material (3) : “cut off, absorption”

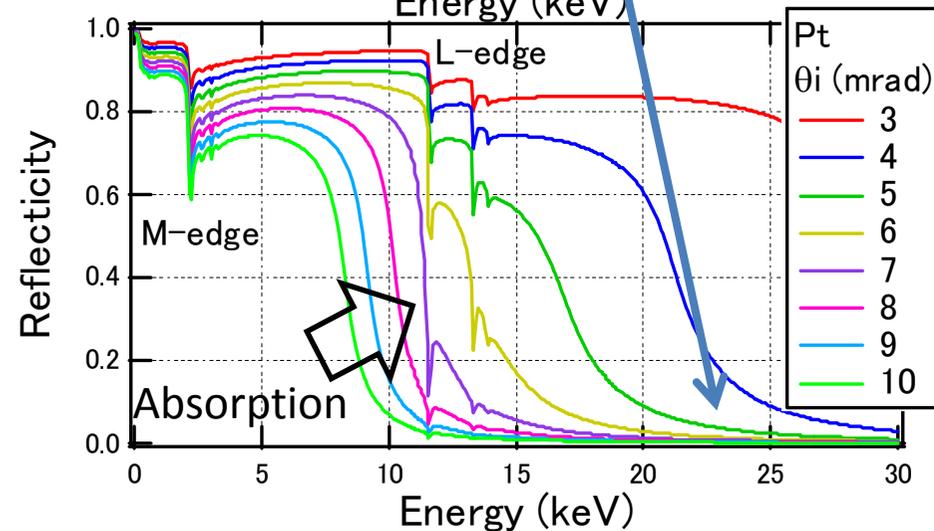
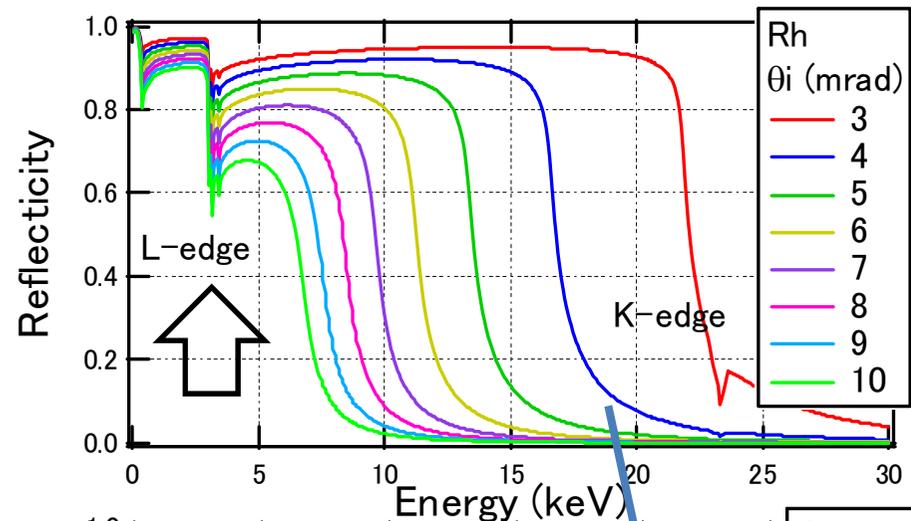
The cut off energy of total reflection E_c

$$E_c \approx 20 \sqrt{\rho} / \theta_i$$

E_c (eV), ρ (g / cm³), θ_c (mrad)

Rh (12.4 g / cm³)

Pt (21.4 g / cm³)



Cut off energy, absorption → incident angle

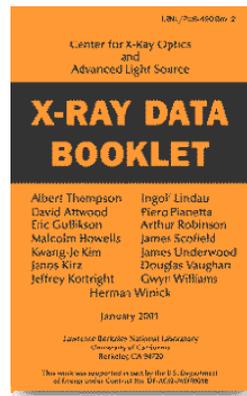
→ Opening of the mirror, length, width of mirror, power density³¹

Atomic scattering factors, Reflectivity

*You can easily find optical property in “X-Ray Data Booklet”
by Center for X-ray Optics and Advanced Light Source,
Lawrence Berkeley National Lab.*

In the site the reflectivity of x-ray mirrors can be calculated.

<http://xdb.lbl.gov/>

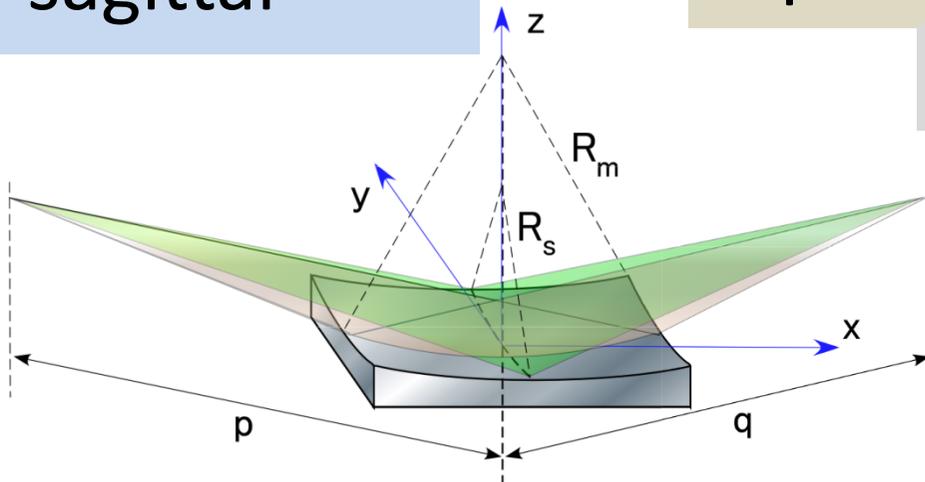


Many thanks to the authors !

Surface shape (1)

Purpose of the mirror	for example,	Easy to make or cost
<ul style="list-style-type: none"> deflecting low pass filter 	<ul style="list-style-type: none"> flat 	
<ul style="list-style-type: none"> focusing collimate 	<ul style="list-style-type: none"> spherical 	
	<ul style="list-style-type: none"> cylindrical 	
	<ul style="list-style-type: none"> toroidal 	
	<ul style="list-style-type: none"> elliptical 	
<ul style="list-style-type: none"> meridional sagittal 	<ul style="list-style-type: none"> parabolic... 	
	<ul style="list-style-type: none"> adaptive 	

Take care of aberration

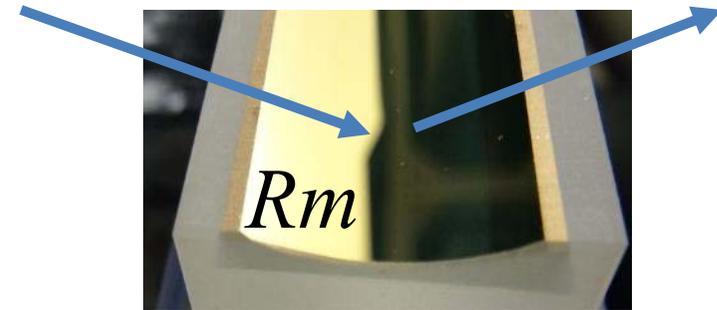


Surface shape (2) radius and depth

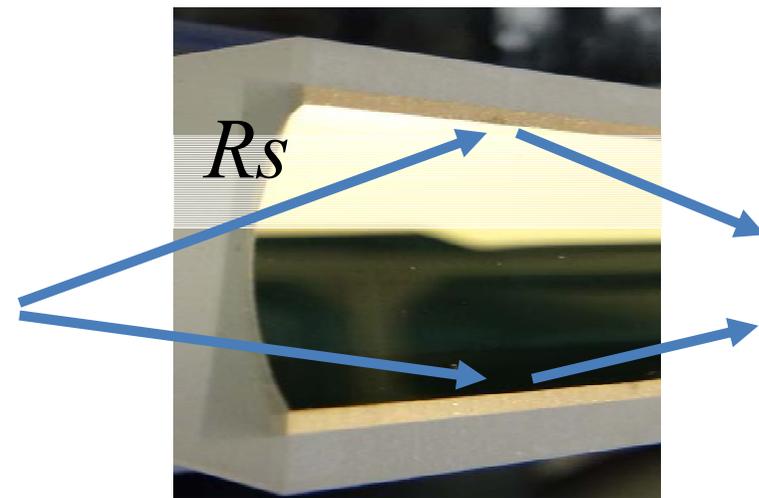
add photos

$$R_m = \frac{2}{(1/p + 1/q)\sin(\theta_i)}$$

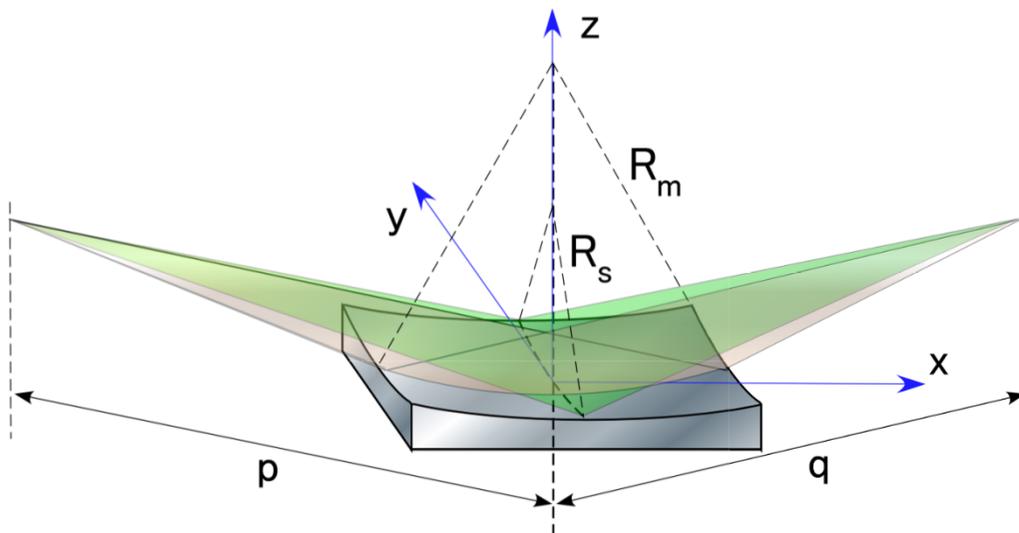
$$R_s = \frac{2\sin(\theta_i)}{(1/p + 1/q)} = R_m \sin^2(\theta_i)$$



Meridional focusing



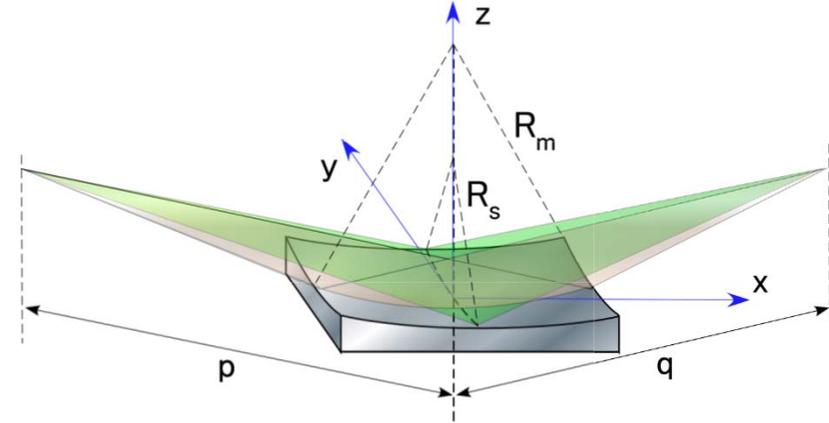
Sagittal focusing



Surface shape (2) radius and depth

$$R_m = \frac{2}{(1/p + 1/q)\sin(\theta_i)}$$

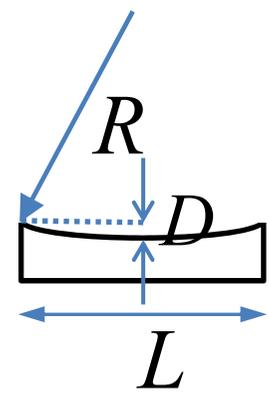
$$R_s = \frac{2\sin(\theta_i)}{(1/p + 1/q)} = R_m \sin^2(\theta_i)$$



➔ For parallel beam $q \rightarrow \infty, 1/q = 0$

Depth at the center

$$D = R - \sqrt{R^2 - \left(\frac{L}{2}\right)^2} \approx \frac{L^2}{8R}$$



For example,

$p=15 \sim 50m, q=5 \sim 20m, \theta_i=1 \sim 10mrad$

$R_m=0.1 \sim 10 \text{ km}, R_s=30 \sim 100 \text{ mm}$

$R_m=1 \text{ km}, L=1m \rightarrow D=125 \mu m$

$R_s=30 \text{ mm}, L=20mm \rightarrow D=1.7 \text{ mm}$

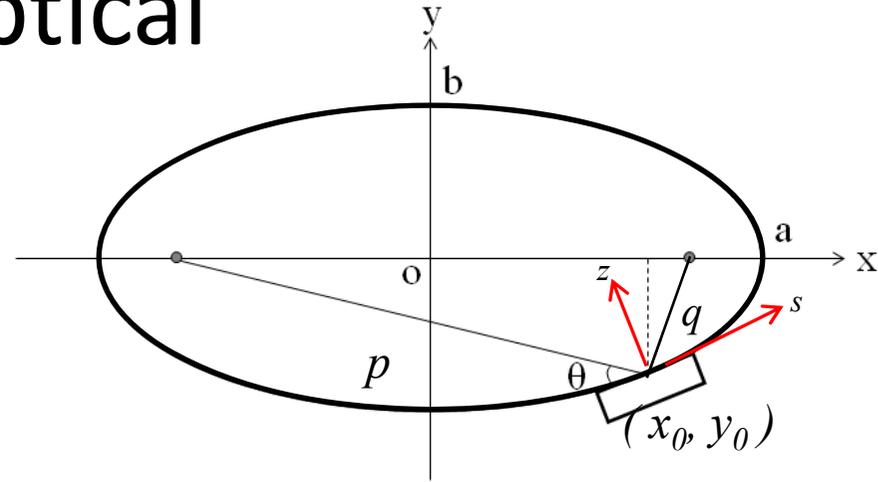


Sagittal focusing mirror

$R_s \sim 30mm$

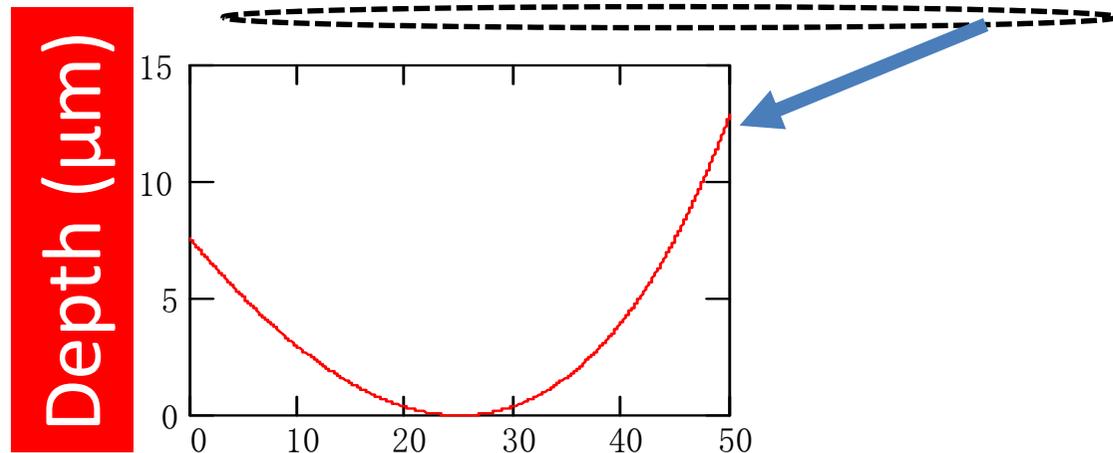
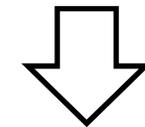
Surface shape (3) elliptical

$$\frac{x^2}{a^2} + \frac{y^2}{b^2} = 1$$



For example,

$$p = 975 \text{ m}, q = 50 \text{ mm}, \theta = 3 \text{ mrad}$$



Position on the mirror surface (mm)

Precise fabrication is not easy.

Design parameters of x-ray mirror

Requirement

the beam properties both of incident and reflected x-rays

(size, angular divergence / convergence, direction, energy region, power...)

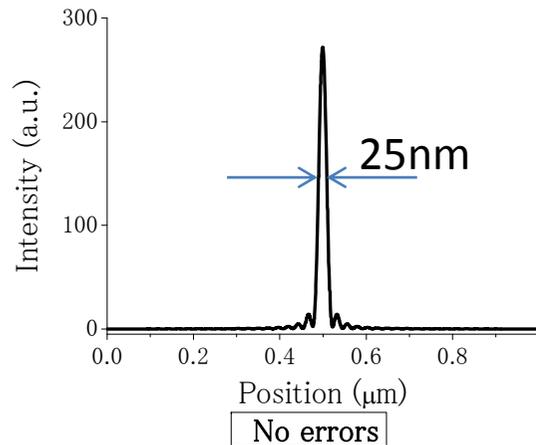
Design parameters

- ✓ Coating material : Rh, Pt, Ni ... (w/o binder , Cr), thickness
: multilayers (ML), laterally graded ML
- ✓ Incident angle : grazing angle (mrad)
- ✓ Surface shape : flat, sphere, cylinder, elliptic ...
: adaptive (mechanically bent, bimorph)
- ✓ Substrate shape : rectangular, trapezoidal...
- ✓ Substrate size : length, thickness, width
- ✓ **w/o cooling** : **indirect or direct, water or LN₂...**
- ✓ **Substrate material** : **Si, SiO₂, SiC, Glidcop...**

In addition,

some errors such as figure error, roughness...





*Tailoring x-rays
to application*



X-ray mirrors

design, **errors**, metrology
& alignment



“An actual mirror has some errors.”

The tolerance should be specified to order the mirror

- Roughness*
- Density of coating material*
- Radius error*
- Figure error*

The cost (price and lead time) depends entirely on tolerance.

We must consider or discuss how to measure it.

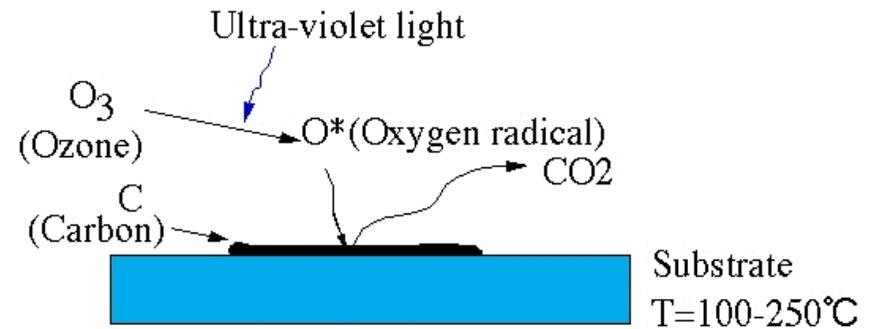
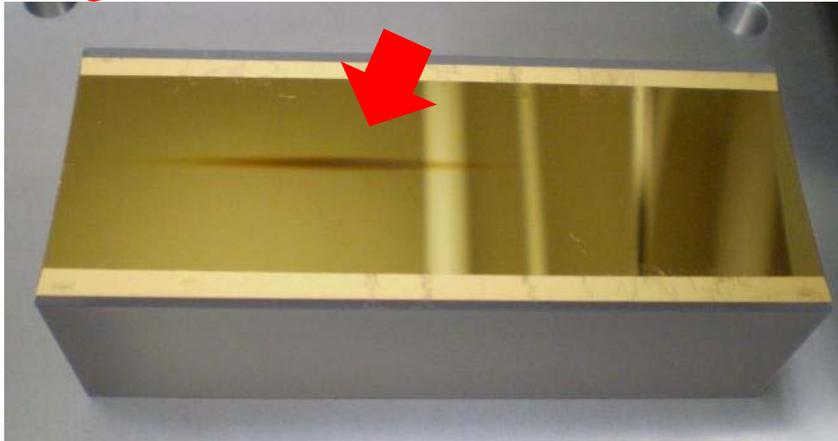
- ✓ Deformation by self-weight, coating and support ...
- ✓ Figure error of adaptive mechanism
- ✓ Misalignment of mirror
- ✓ Stability of mirror's position (angle)
- ✓ Deposition of contamination by use
- ✓ Decomposition of substrate by use

- Reflectivity
- Beam size
- Distortion
- Deformation ...

- Environment
- Manipulator
- Cooling system ...

Contamination and removal

before



After cleaning



Advantage of UV/ozone cleaning

1. Low Damage
2. Contamination-free
3. Non-contact

UV / ozone cleaning

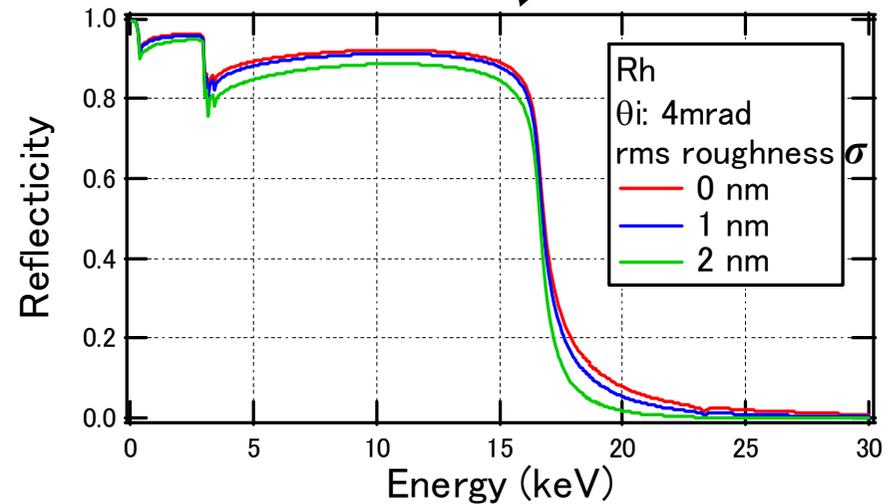
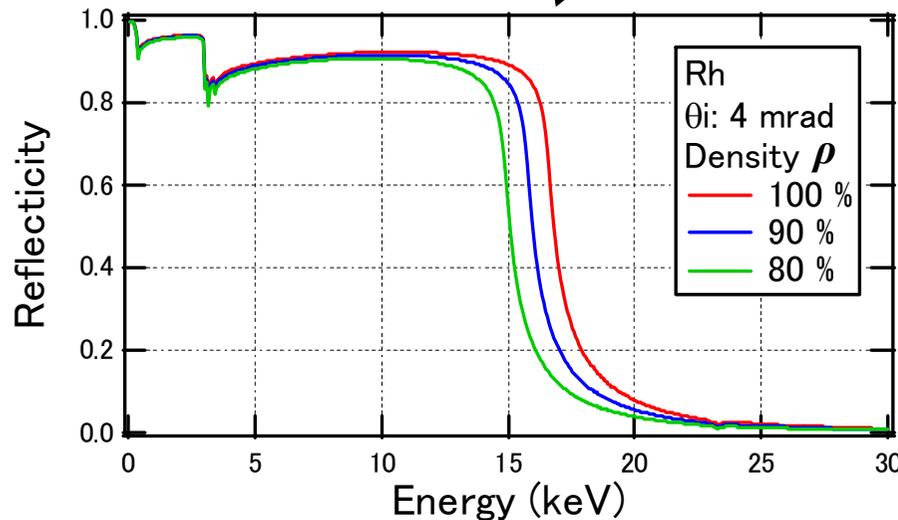
It takes from 10 min to a few hours.

Errors (1)

“Density ρ and surface roughness σ ”

$$E_c \approx 20 \sqrt{\rho} / \theta_i$$

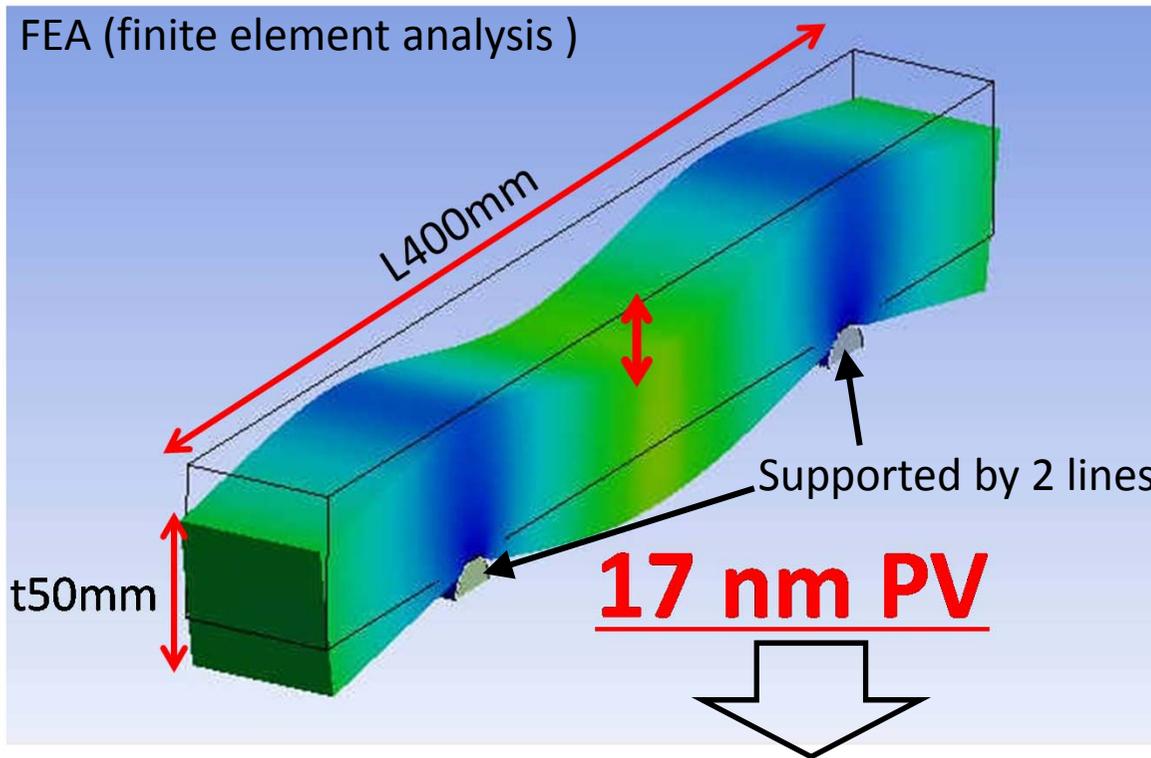
$$R = R_0 e^{-\left(\frac{4\pi\sigma \sin(\theta_i)}{\lambda}\right)^2}$$



Coating on sample wafer at the same time is helpful to evaluate the density and roughness.

Errors (2)

“the self-weight deformation”



Material	SiO ₂
Density	2.2 g / cm ³
Poisson's ratio	0.22
Young's modulus	E = 70 Gpa

$$D \propto \frac{L^4}{E \times t^3}$$

This value for nano-focusing is larger than figure error by Rayleigh's rule.

(→See next page)

Improvement for nano-focusing

a) Substrate → Si (E ~ 190 GPa)

b) Optimization of supporting points and method

c) Figuring the surface in consideration of the deformation

Errors (3a)

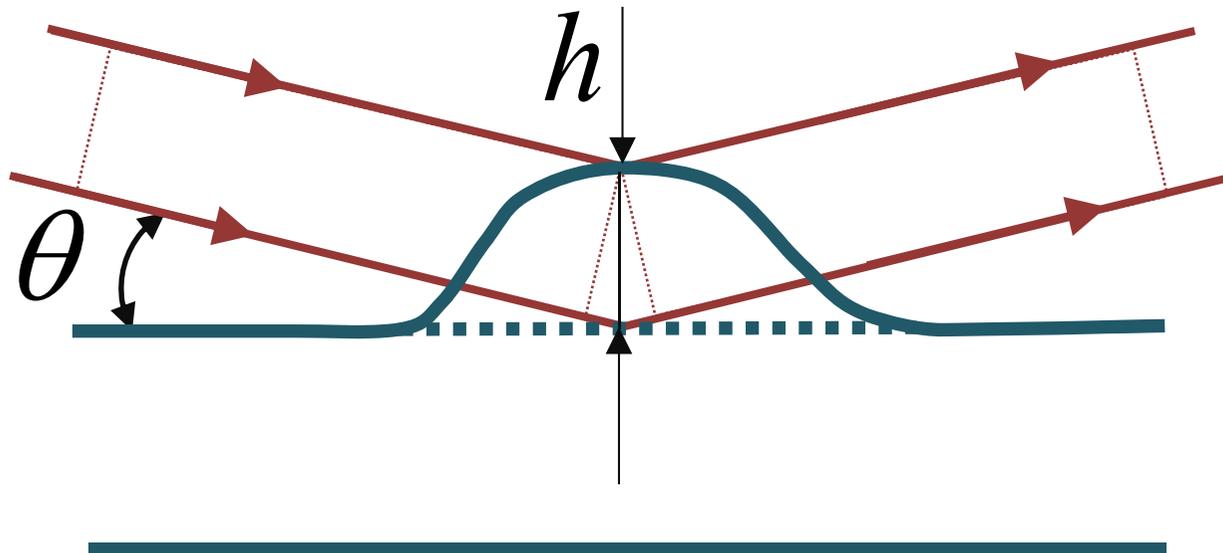
“figure error estimated by Rayleigh’s rule”

$$\phi = 2hk \sin(\theta) \rightarrow \pi/2 \quad h_{\lambda/4} = \lambda/8\theta$$

0.06nm (20keV)	3mrad	2nm
----------------	-------	-----

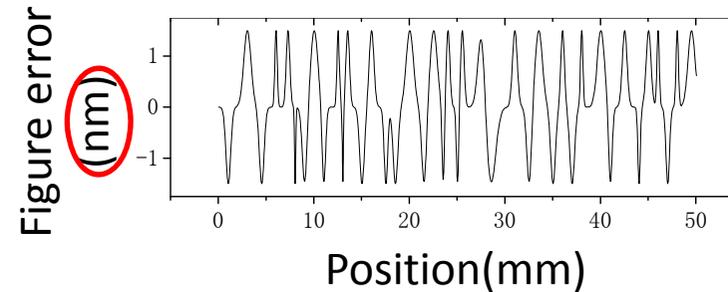
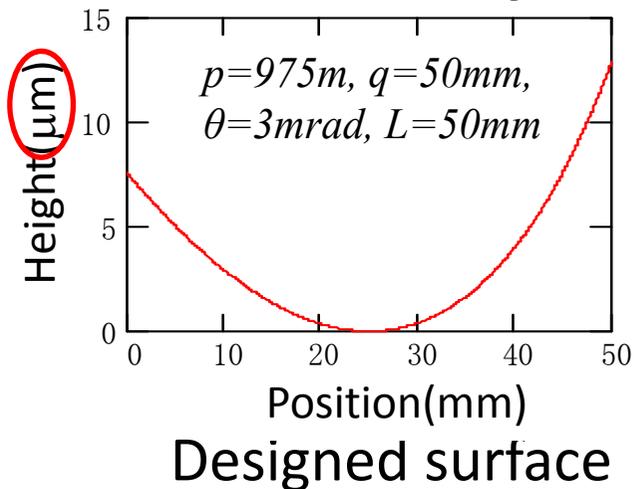
0.08nm (15keV)	3mrad	3nm
----------------	-------	-----

1 nm (1keV)	10mrad	12nm
--------------	--------	------



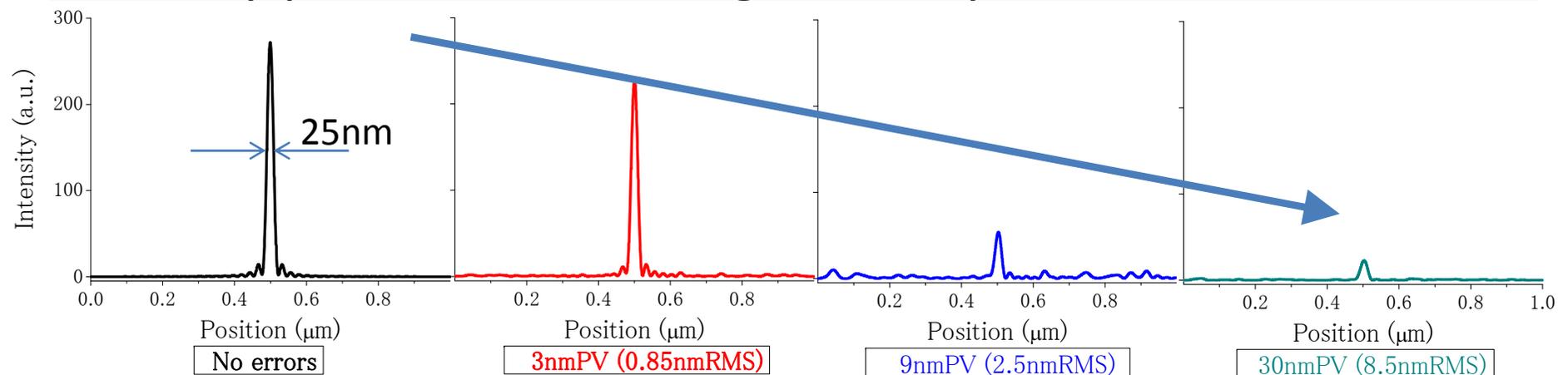
Errors (3b)

“*estimation by wavefront simulation*”



Errors of *short* range order

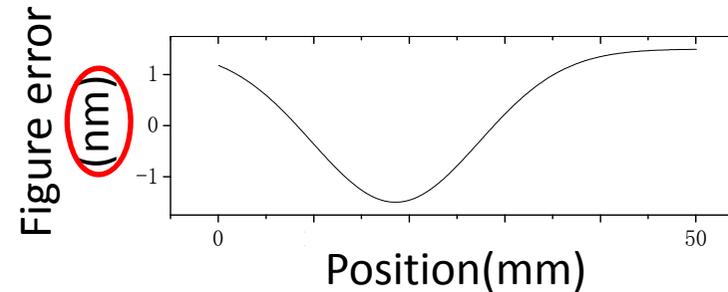
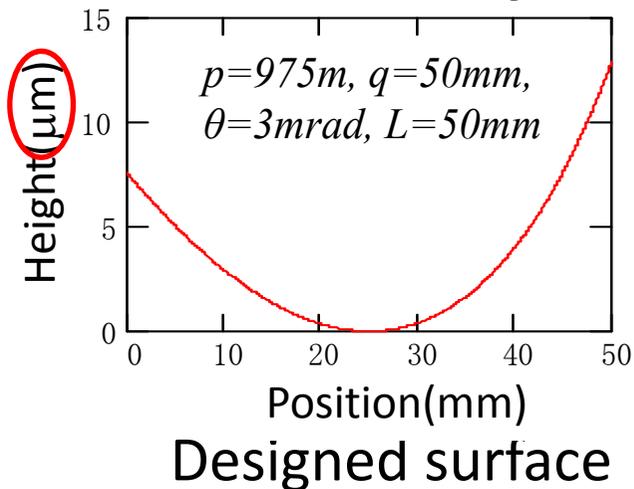
Intensity profiles of focusing beam by wavefront simulation



Errors of *short* range order *decreases intensity*. \rightarrow Roughness

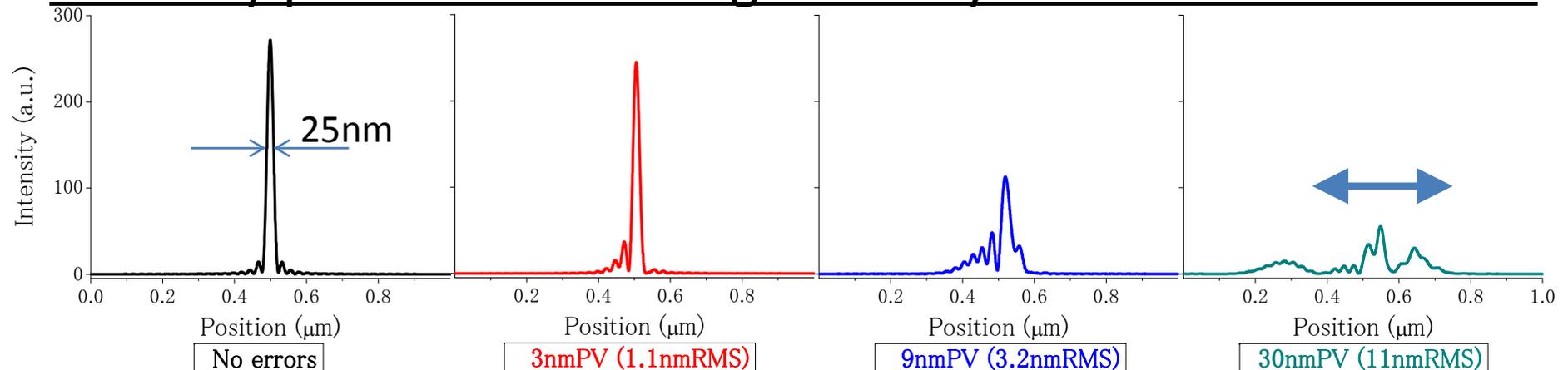
Errors (3c)

“ *estimation by wavefront simulation* ”



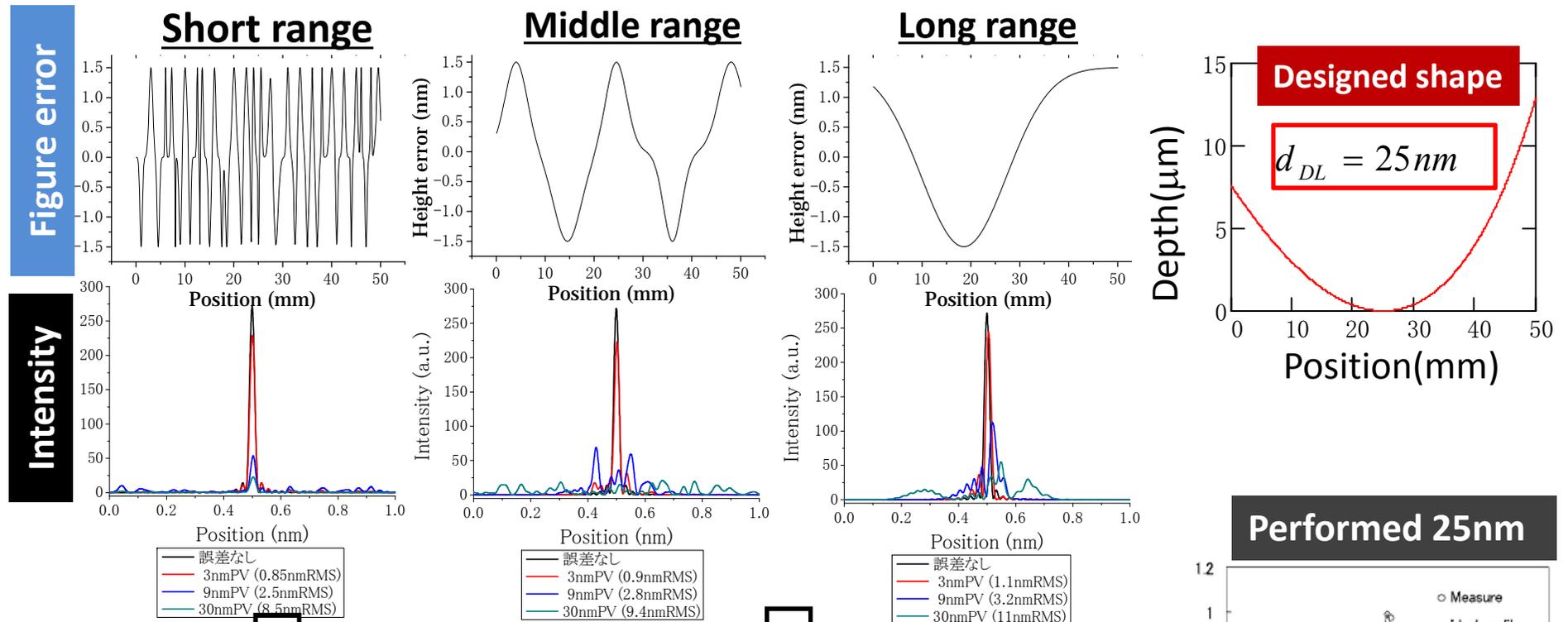
Errors of *long* range order

Intensity profiles of focusing beam by wavefront simulation



Errors of *long* range order *loses shape*. \rightarrow Figure

“ estimation by wavefront simulation ”



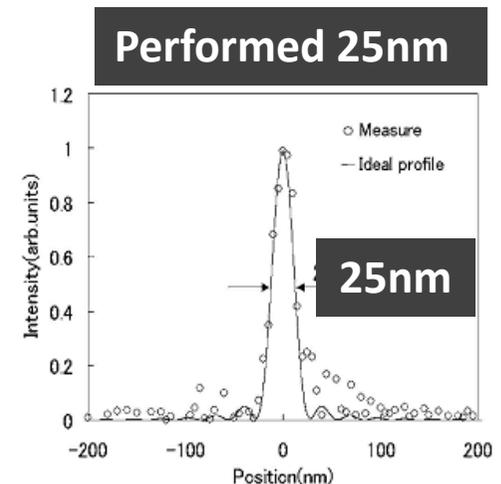
Intensity reduced

Shape loses

If the **figure error < 3nmPV for all spatial range**,

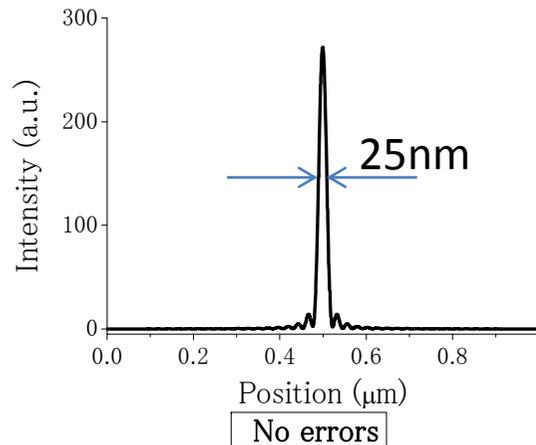
the estimated focusing size performs 25 nm.

The value corresponds to the result of Rayleigh's rule.



The focusing beam of 25 nm was realized using high precision mirror with figure error of 3 nm PV

*H. Mimura, H. Yumoto, K. Yamauchi et.al, Appl. Phys. Lett. **90**, 051903 (2007).



*Tailoring x-rays
to application*



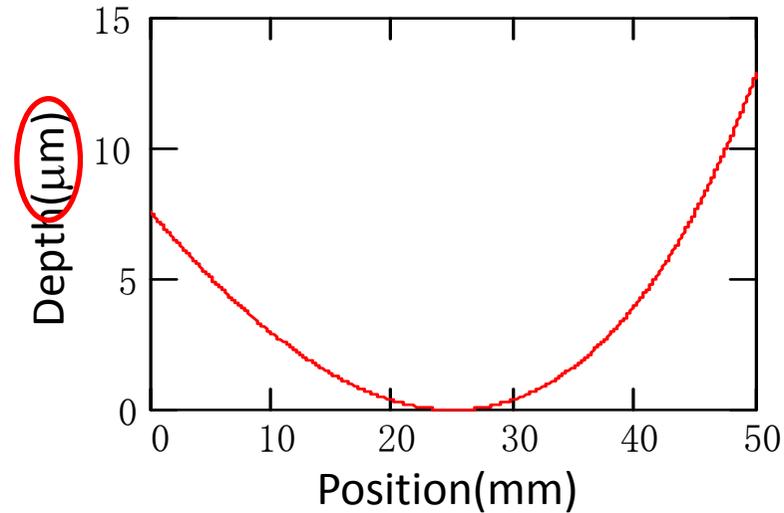
X-ray mirrors

design, errors, **metrology**
& alignment

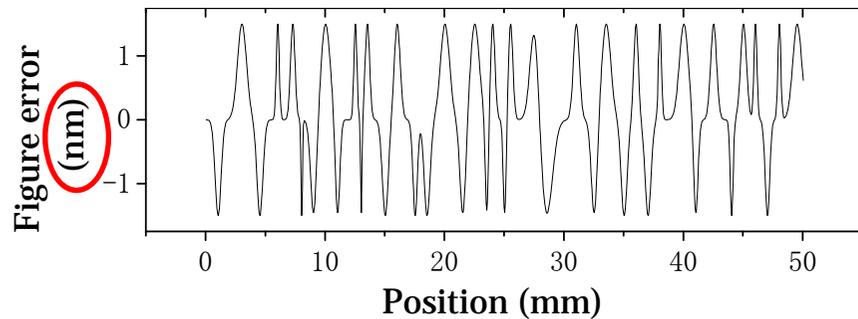


How to evaluate the errors ?

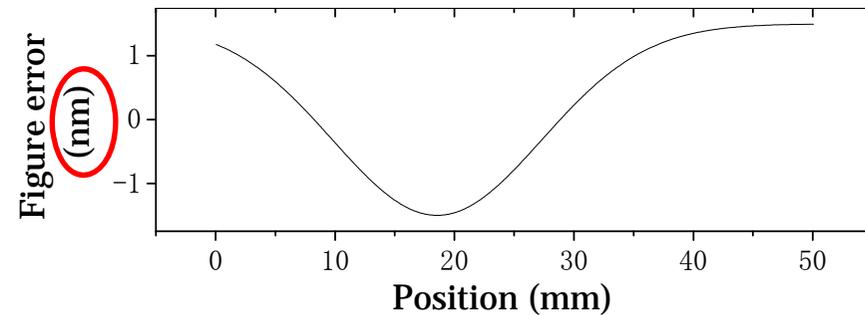
Designed surface



Errors (short range)



Errors (long range)



Metrology instruments for x-ray optics

Field of view, lateral resolution

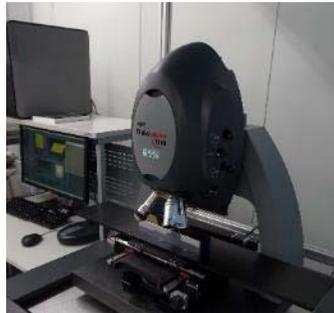
Short
 $\sim 10 \mu\text{m}$,
 0.1 nm
 Roughness



Scanning probe microscope

$z (0.1\text{nm})$

Short / middle
 $\sim 10 \text{ mm}$,
 $1 \mu\text{m}$
 Roughness, figure



Scanning white light interferometer

$z (0.1\text{nm})$

Long / middle
 $\sim 0.1 \text{ m}$,
 0.1 mm
 Figure



Fizeau interferometer

$z (0.1\text{nm})$

Long / middle
 $\sim 1\text{m}$,
 1 mm Slope



Long Trace Profiler (LTP)

slope
 $(0.1\mu\text{rad})$

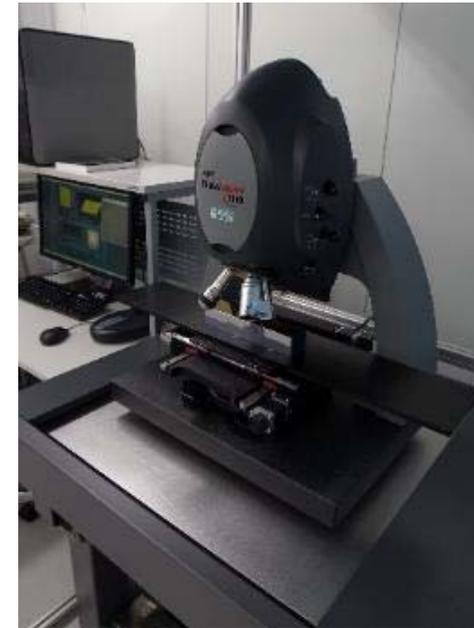
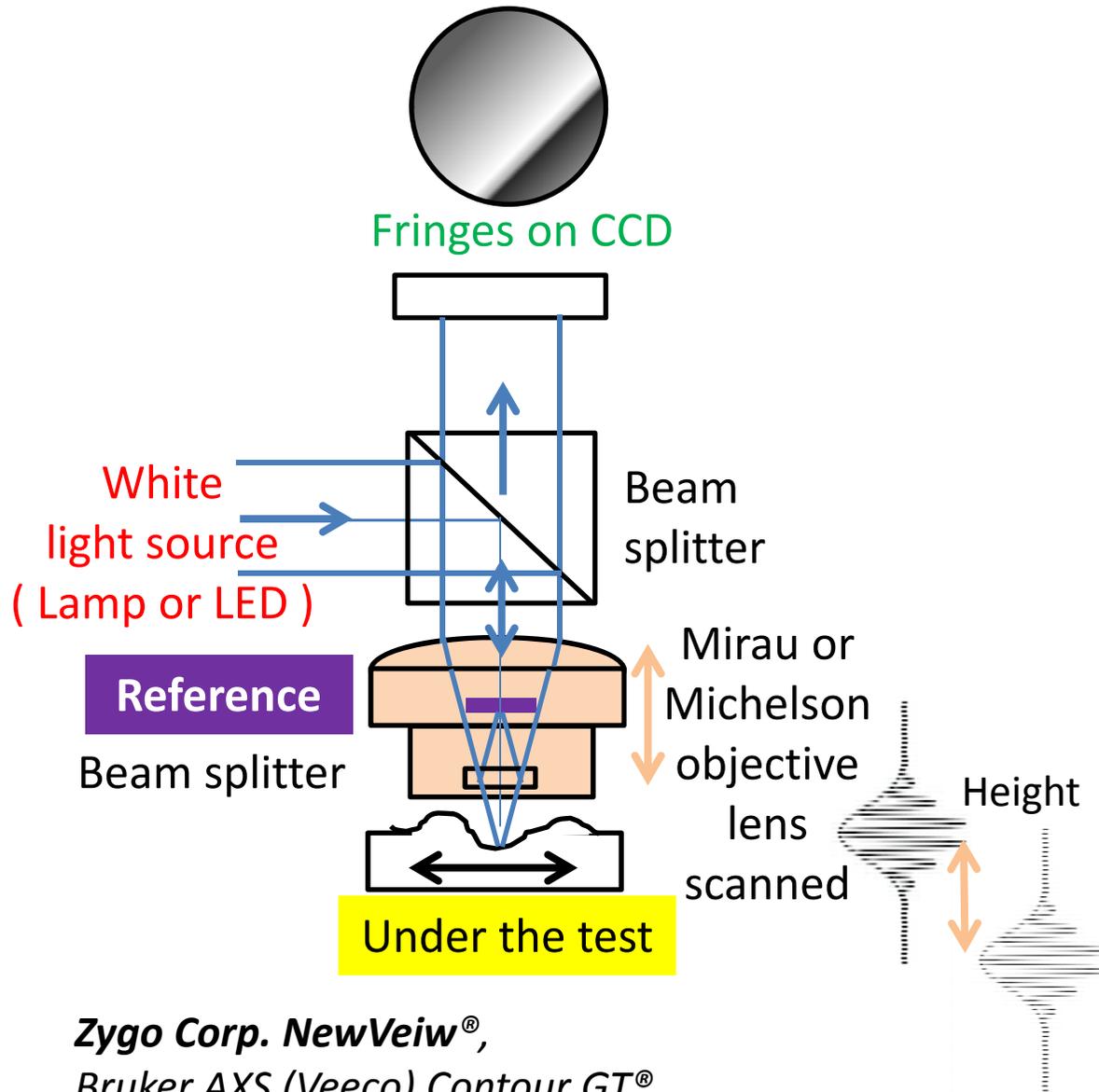
Vertical resolution (rms)

Scanning white light interferometer

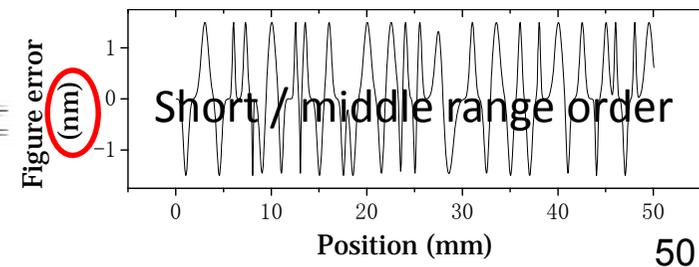
Short range

Interference fringe \rightarrow Height

Commercially available



FOV (=lens) 50 μ m ~ 10 mm
Lateral resolution 1 μ m ~
Vertical resolution 0.1 nm



Zygo Corp. NewView[®],
Bruker AXS (Veeco) Contour GT[®]

Fizeau interferometer

Long / mid range

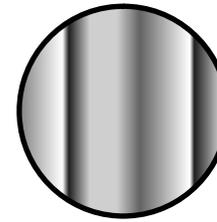
Interference pattern → Height

Commercially available

Monochromatic point light source

Zygo Corp. VeriFire®,
4DS technologies,
FujiFILM

Beam splitter



Fizeau fringes on CCD



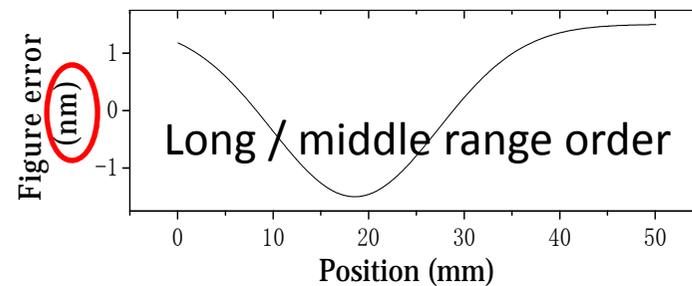
FOV (=reference) ~0.1 m
Lateral resolution ~0.1 mm
Vertical resolution 0.1 nm

Collimator

Reference

Cavity

Under the test



*Not easy to measure large mirror*⁵¹

Long trace profiler (LTP)

Long / mid range

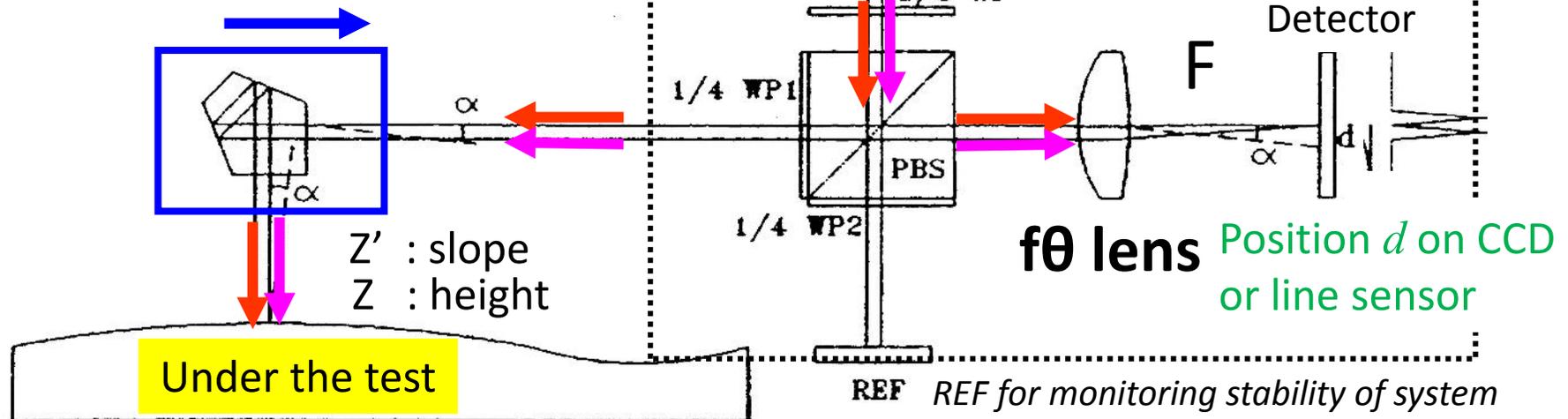
Homemade

Direction of laser reflected on the surface → **Slope**

$$Z' = \frac{d}{2F}$$

$d \quad \mu m$
 $F \quad 1m$
 $Z' < sub-\mu rad$

Scanning penta prism



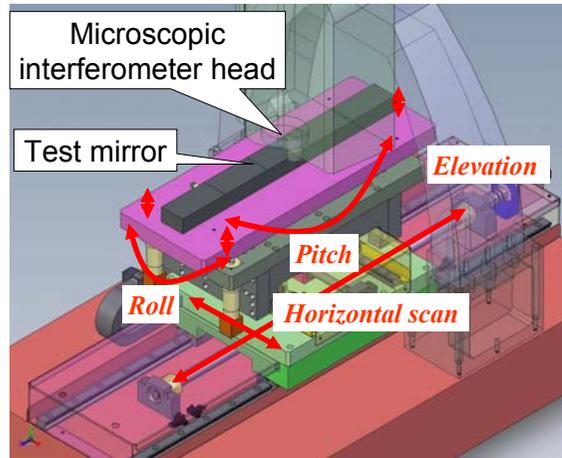
Easy to measure slope of sub- μrad on large mirror by *NO reference*
 Many kinds of LTPs are developing among SR facilities.

Stitching interferometer for large mirror

Homemade

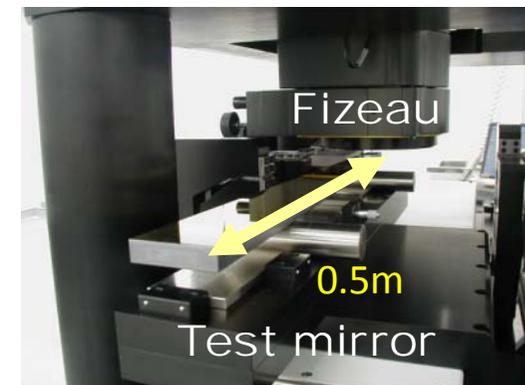
MSI

(micro-stitching interferometer)



RADSI

(relative angle determinable stitching interferometer)

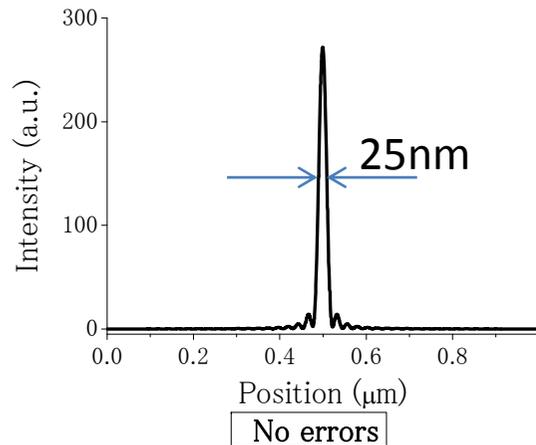


Collaboration with Osaka Univ., JTEC and SPring-8

H. Ohashi et al., Proc. Of SPIE **6704**, 670405-1 (2007).

Height error of wide range order for a long and aspherical mirror with $1\mu\text{m}$ of lateral and 0.1 nm of vertical resolution.

Necessity is the mother of invention.



*Tailoring x-rays
to application*

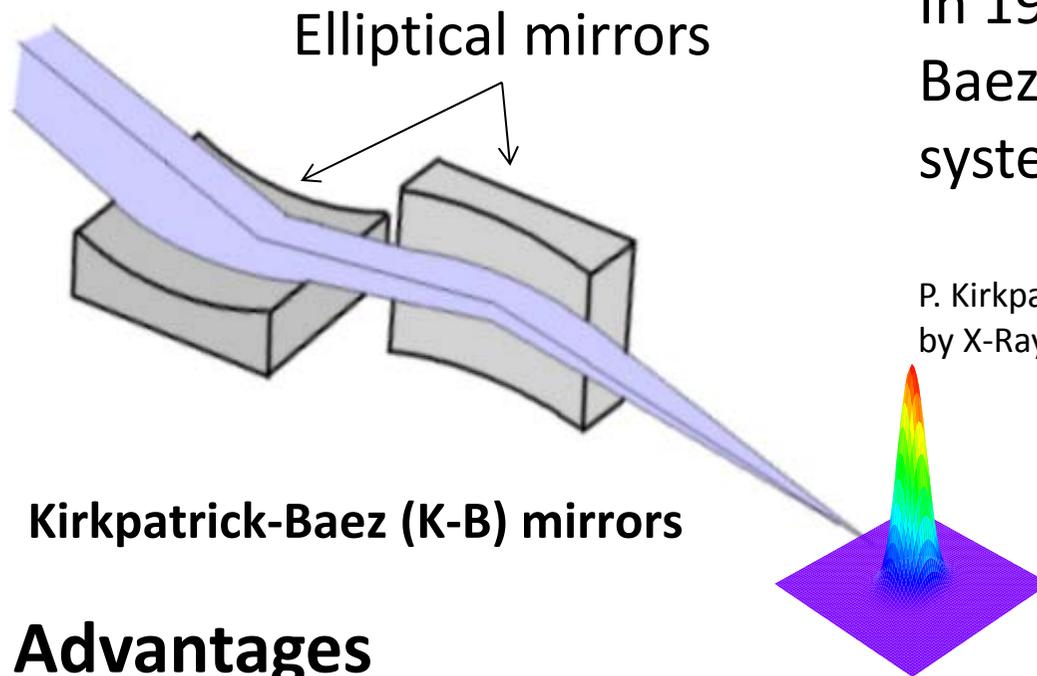


X-ray mirrors

design, errors, metrology
& alignment



Introduction of KB mirrors



In 1948, P. Kirkpatrick and A. V. Baez proposed the focusing optical system.

P. Kirkpatrick and A. V. Baez, "Formation of Optical Images by X-Rays", J. Opt. Soc. Am. **38**, 766 (1948).

Advantages

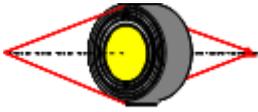
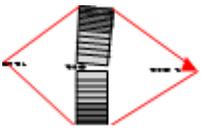
- Large acceptable aperture and High efficiency
- No chromatic aberration
- Long working distance

Disadvantages

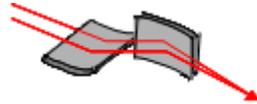
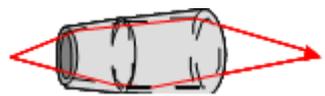
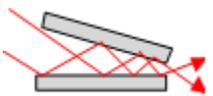
- Difficulty in mirror alignments
- Difficulty in mirror fabrications
- Large system

} *Suitable for
x-ray
nano-probe*

Overview of x-ray focusing devices

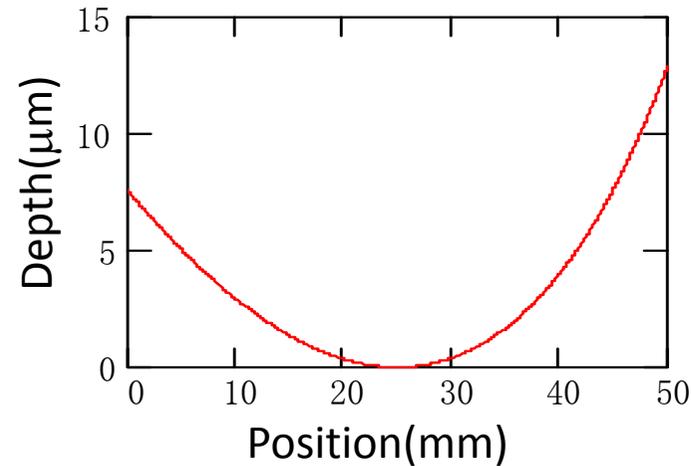
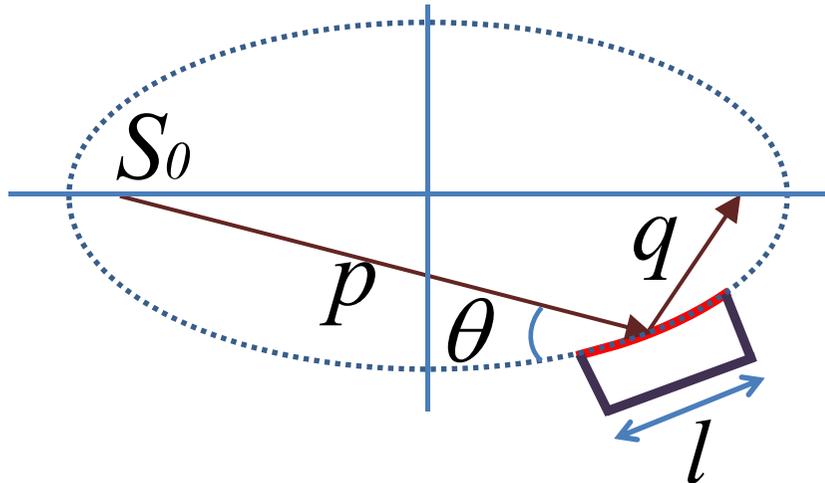
Diffraction	focus size, focal length [energy]	energy range	aberration -coma -chromatic -figure error
 Fresnel Zone Plate	12 nm, f = 0.16 mm [0.7 keV], 30 nm, f = 8 cm [8 keV]	soft x-ray hard x-ray	-coma small -chromatic exist -figure error small
 Sputter sliced FZP	0.3 μm, f = 22 cm [12.4 keV], 0.5 μm, f = 90 cm [100 keV]	8-100 keV	-coma small -chromatic exist -figure error large → small
 Bragg FZP	2.4 μm, f = 70 cm [13.3 keV]	mainly hard x-ray	-coma small -chromatic exist -figure error small
 Multilayer Laue Lens	16 nm(1D), f = 2.6 mm [19.5 keV], 25nm × 40nm, f=2.6mm,4.7mm [19.5 keV]	mainly hard x-ray	-coma large -chromatic exist -figure error small

Refraction	focus size, focal length [energy]	energy range	aberration -coma -chromatic -figure error
 Pressed Lens	1.5 μm, f = 80 cm [18.4 keV], 1.6 μm, f = 1.3 m [15 keV]	mainly hard x-ray	-coma small -chromatic exist -figure error large
 Etching Lens	47nm × 55nm, f = 1cm, 2cm [21 keV]	mainly hard x-ray	-coma small -chromatic exist -figure error small

Reflection	focus size, focal length [energy]	energy range	aberration -coma -chromatic -figure error
 Kirkpatrick-Baez Mirror	7 nm × 8nm, f=7.5cm [20 keV]	soft x-ray hard x-ray	-coma large -chromatic not exist -figure error small
 Wolter Mirror	0.7 μm, f = 35 cm [9 keV]	<10 keV	-coma small -chromatic not exist -figure error large
 X-ray Waveguide	95 nm, [10 keV]	soft x-ray hard x-ray	-coma large -chromatic not exist -figure error large

How small is x-ray focused ?

For example, by elliptical mirror



Geometrical size

$$d_G = \frac{q}{p} \times S_0$$

Diffraction limited size(FWHM)

$$d_{DL} = \lambda \times \frac{0.88q}{l \sin(\theta)}$$

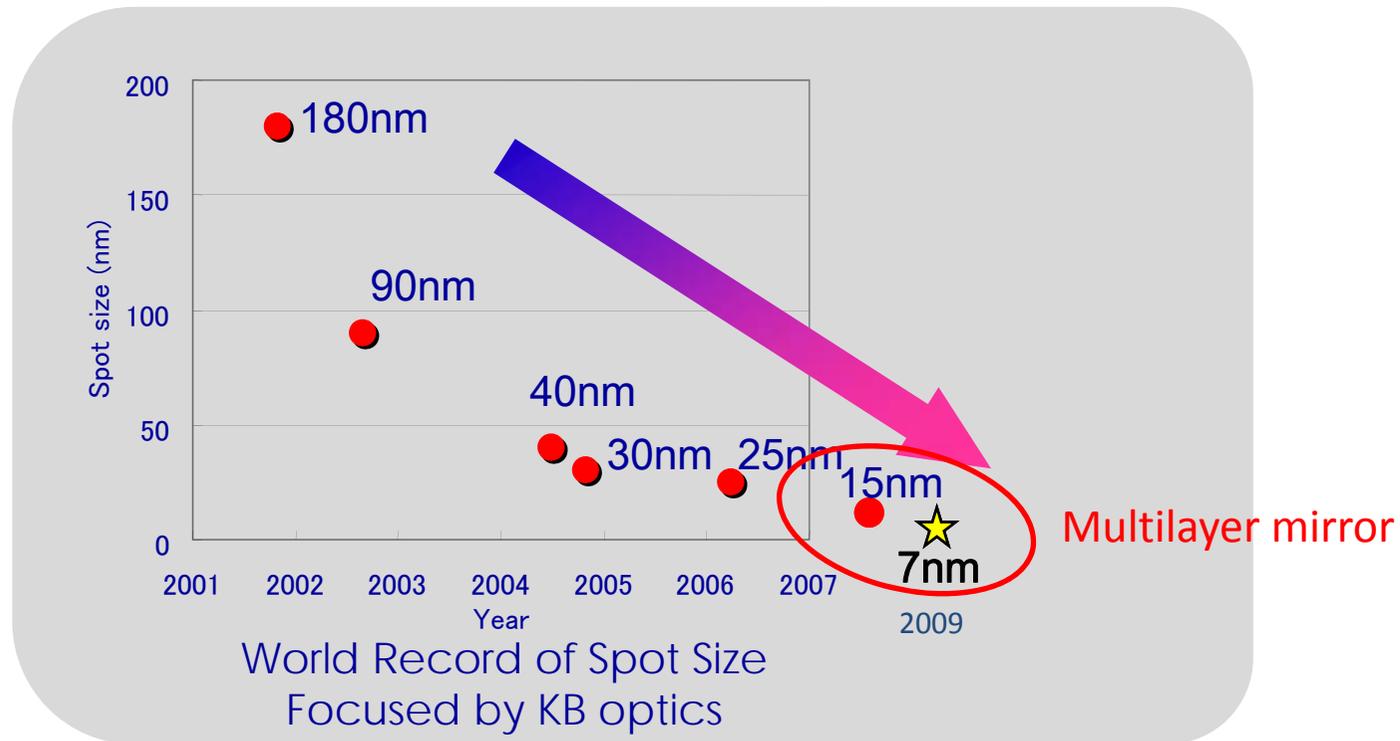
$$p = 975 \text{ m}, q = 50 \text{ mm}, \theta = 3 \text{ mrad}, l = 50 \text{ mm}, \lambda = 0.083 \text{ nm}, S_0 = 100 \mu\text{m} \text{ (15keV)}$$

$$\text{Mag.} = 1 / 19500 !$$

$$d_G = 5 \text{ nm} < d_{DL} = 25 \text{ nm}$$

The opening of the mirror restricts the focused size even if magnification is large. 58

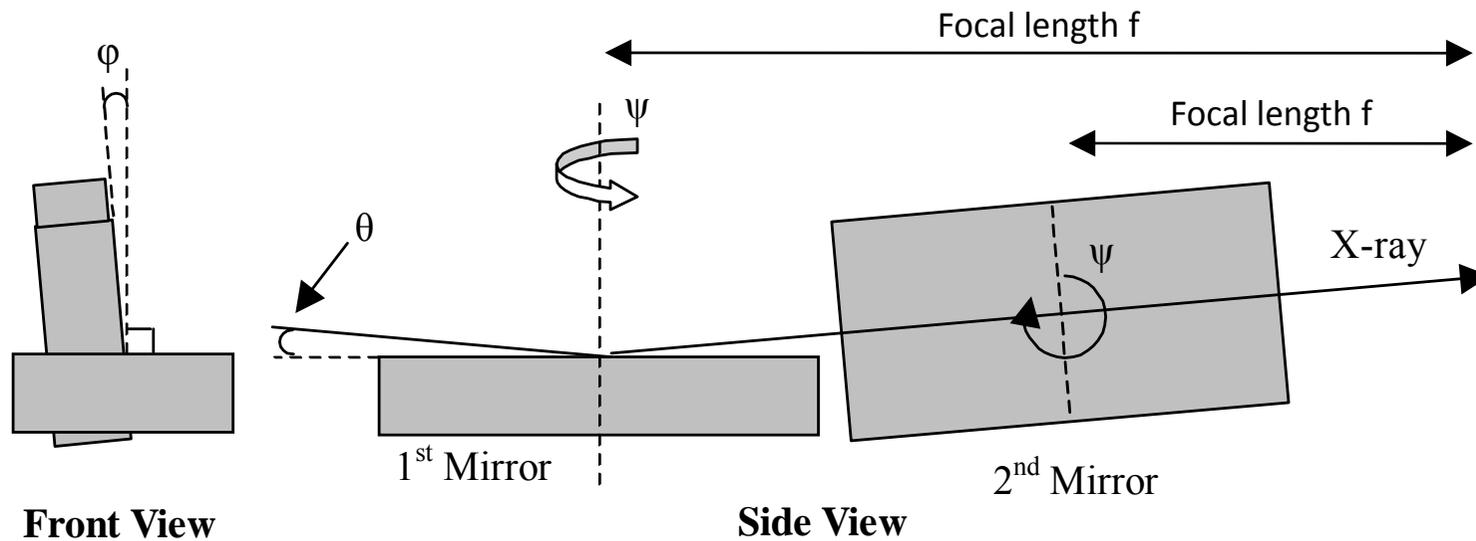
Nano-focusing by KB mirror History since the century



World Record of spot size is **7 nm** (by Osaka Univ., in 2009 *).

Routinely obtained spot size is up to **30 nm**.

Difficulty in mirror alignments



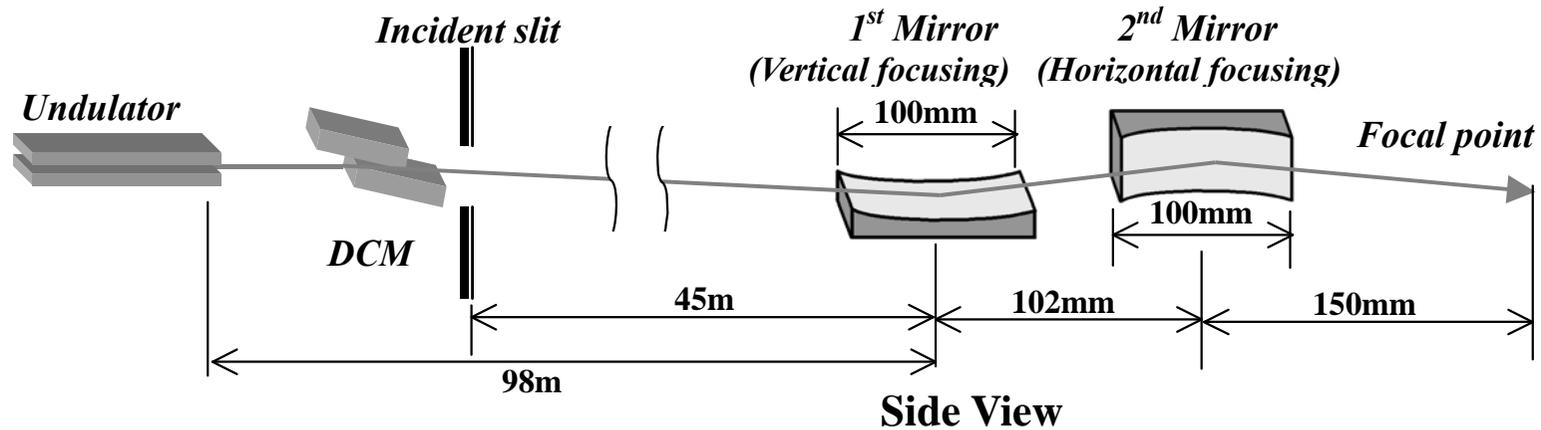
Positioning two mirrors is difficult because there are at least 7 degree of freedom.



It is difficult to use KB mirrors.

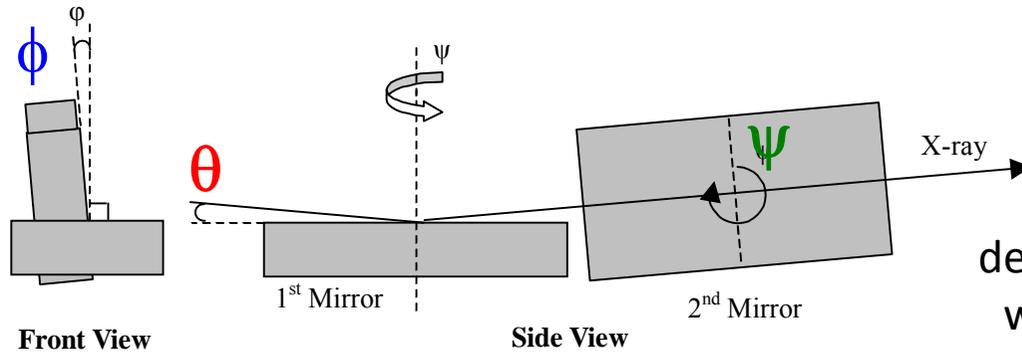
Pitching	θ_1, θ_2
Yawing	ψ_1, ψ_2
Orthogonality	Φ
Focal length	f_1, f_2

KB optics installed in BL29XU-L

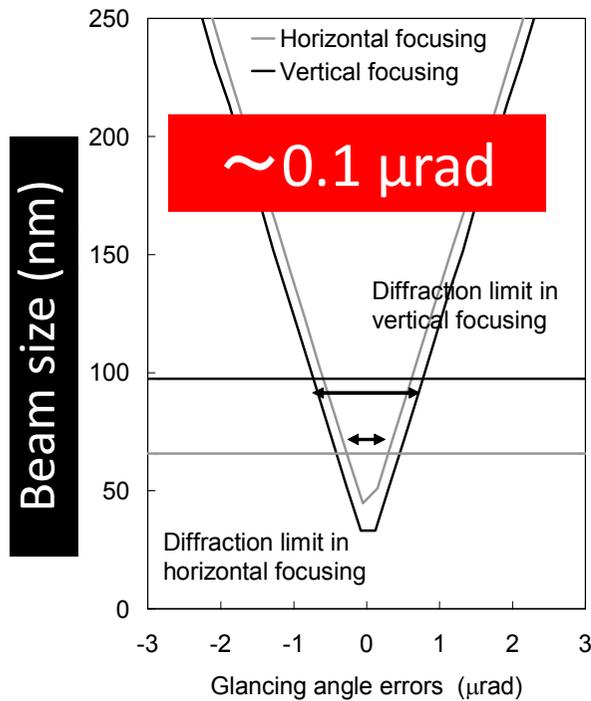


	1 st Mirror	2 nd Mirror
Glancing angle (mrad)	3.80	3.60
Mirror length (mm)	100	100
Mirror aperture (μm)	382	365
Focal length (mm)	252	150
Demagnification	189	318
Numerical aperture	0.75×10^{-3}	1.20×10^{-3}
Coefficient a of elliptic function (mm)	23.876×10^3	23.825×10^3
Coefficient b of elliptic function (mm)	13.147	9.609
Diffraction limited focal size (nm, FWHM)	48	29

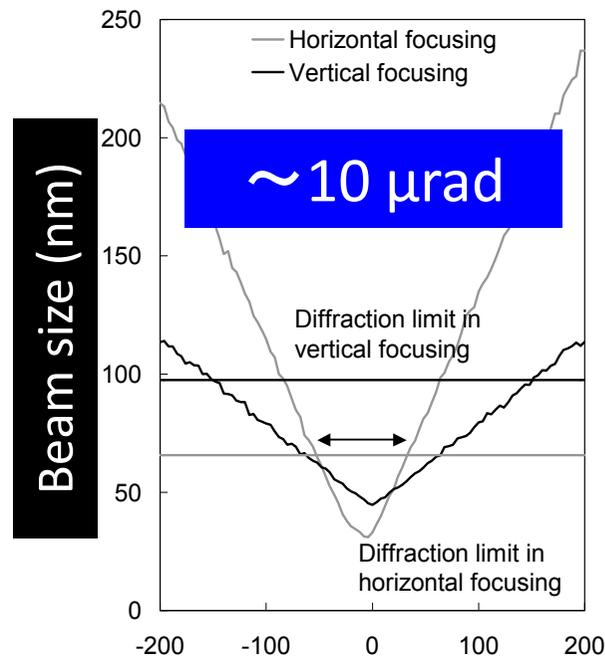
Tolerance limits of mirror alignments



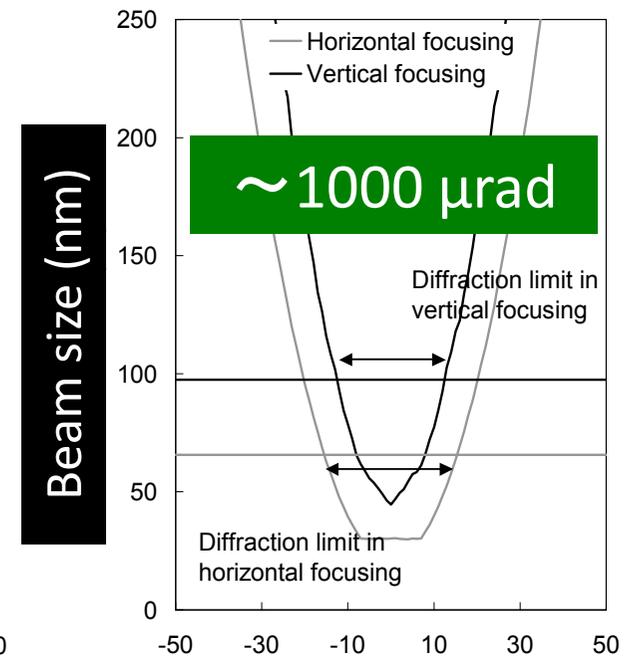
Severe positioning of two mirrors is required. The manipulator should be designed for these freedom of axis with the resolution & the range.



Errors of θ



Perpendicularity errors $\Delta\phi$ (μrad)

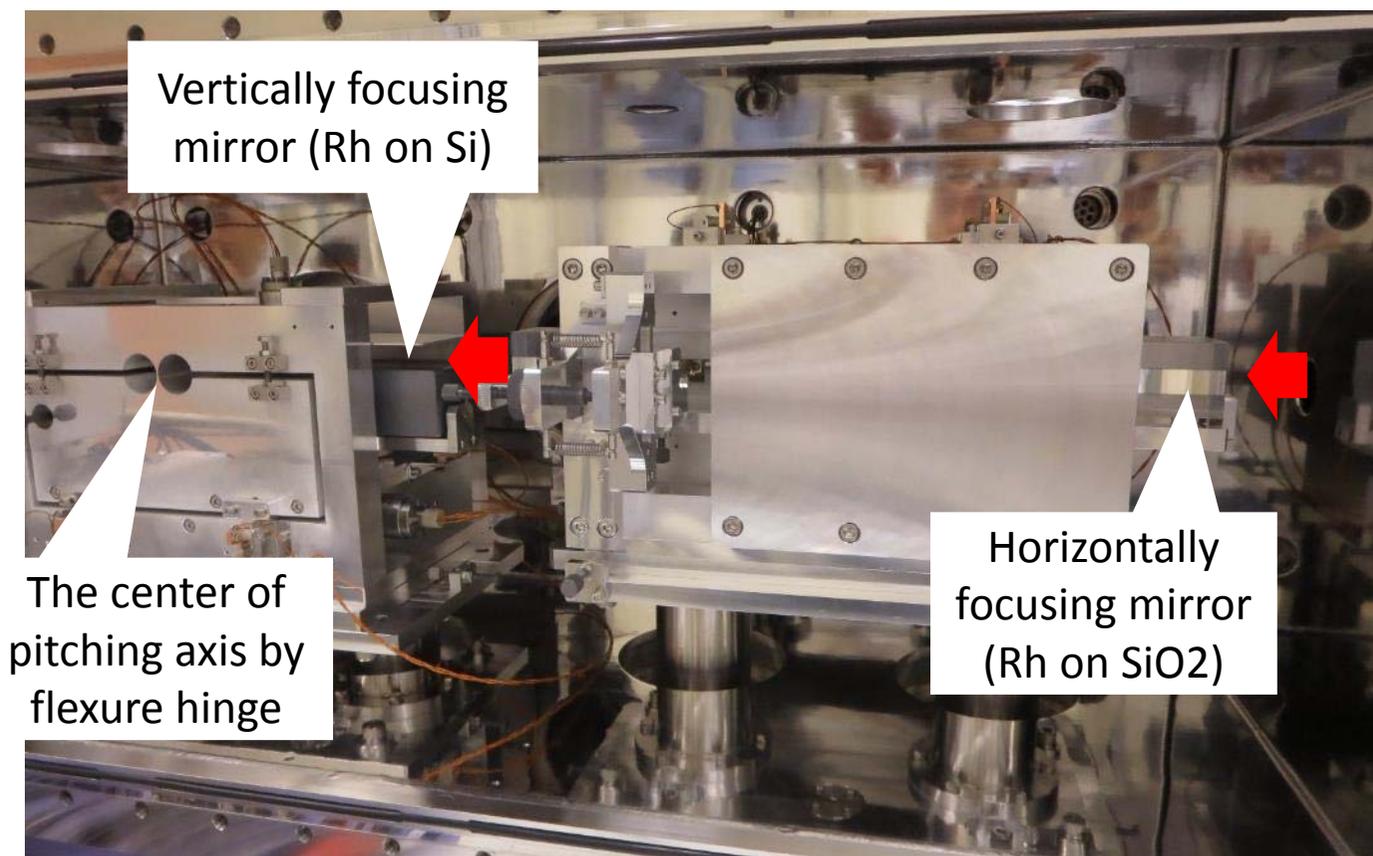


In-plane rotation errors $\Delta\psi$ (mrad)

Freedom of axis, Resolution, range

Ref: S. Matsuyama, H. Mimura, H. Yumoto et al., "Development of mirror manipulator for hard-x-ray nanofocusing at sub-50-nm level", Rev. Sci. Instrum. **77**, 093107 (2006).

A typical manipulator of KB optics

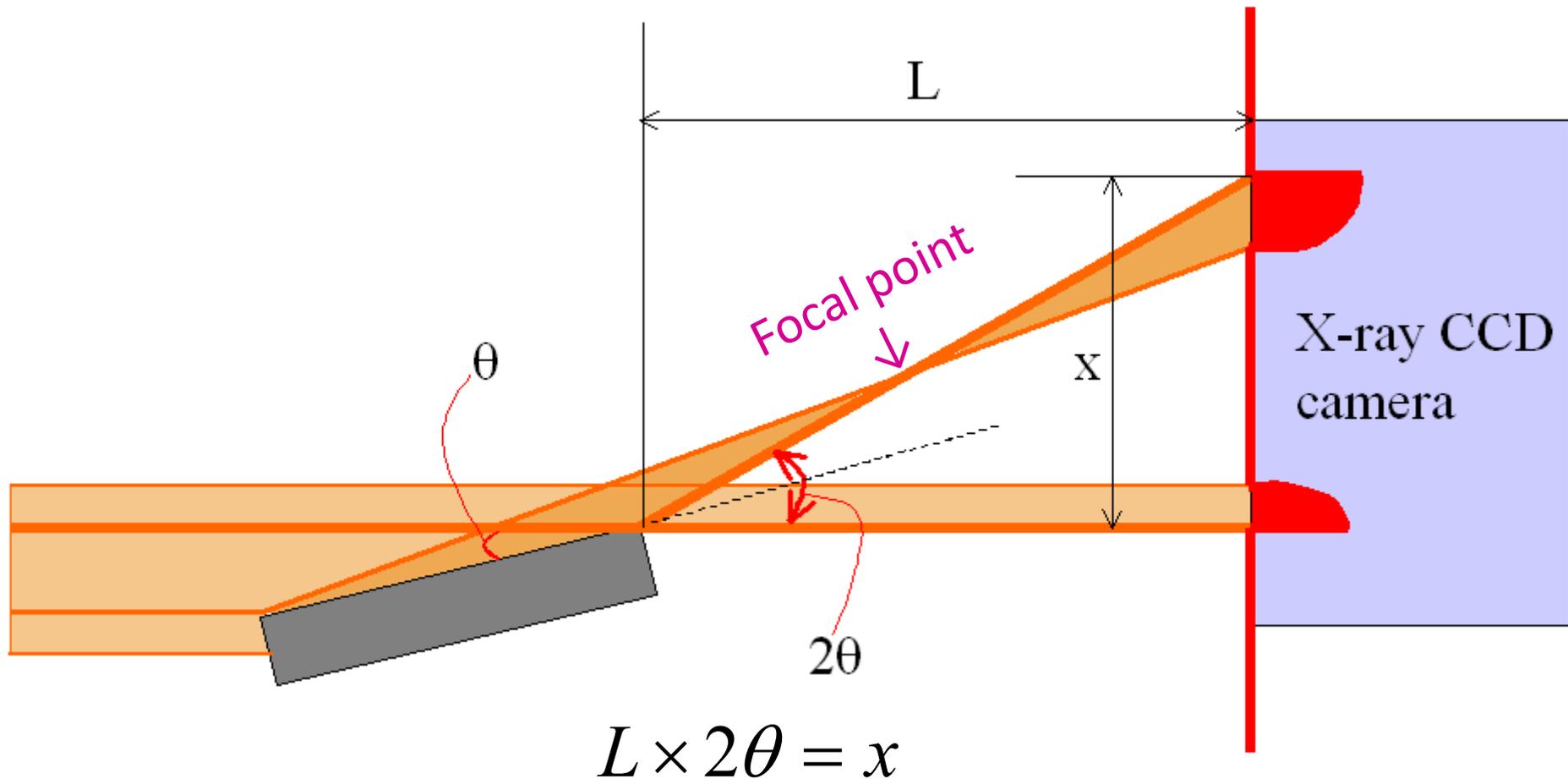


- ✓ Precise manipulation of mirrors
- ✓ Highly stable system
- ✓ Ultra-high vacuum (or He environment)

For example,

- *Resolution of pitching axis = 0.1 μ rad*
→ *Res. of the actuator at 100 mm = 10 nm*
- *The focal length = 1 m and beam size = 1 μ m*
→ *Angular stability of the mirror \sim 0.1 μ rad*

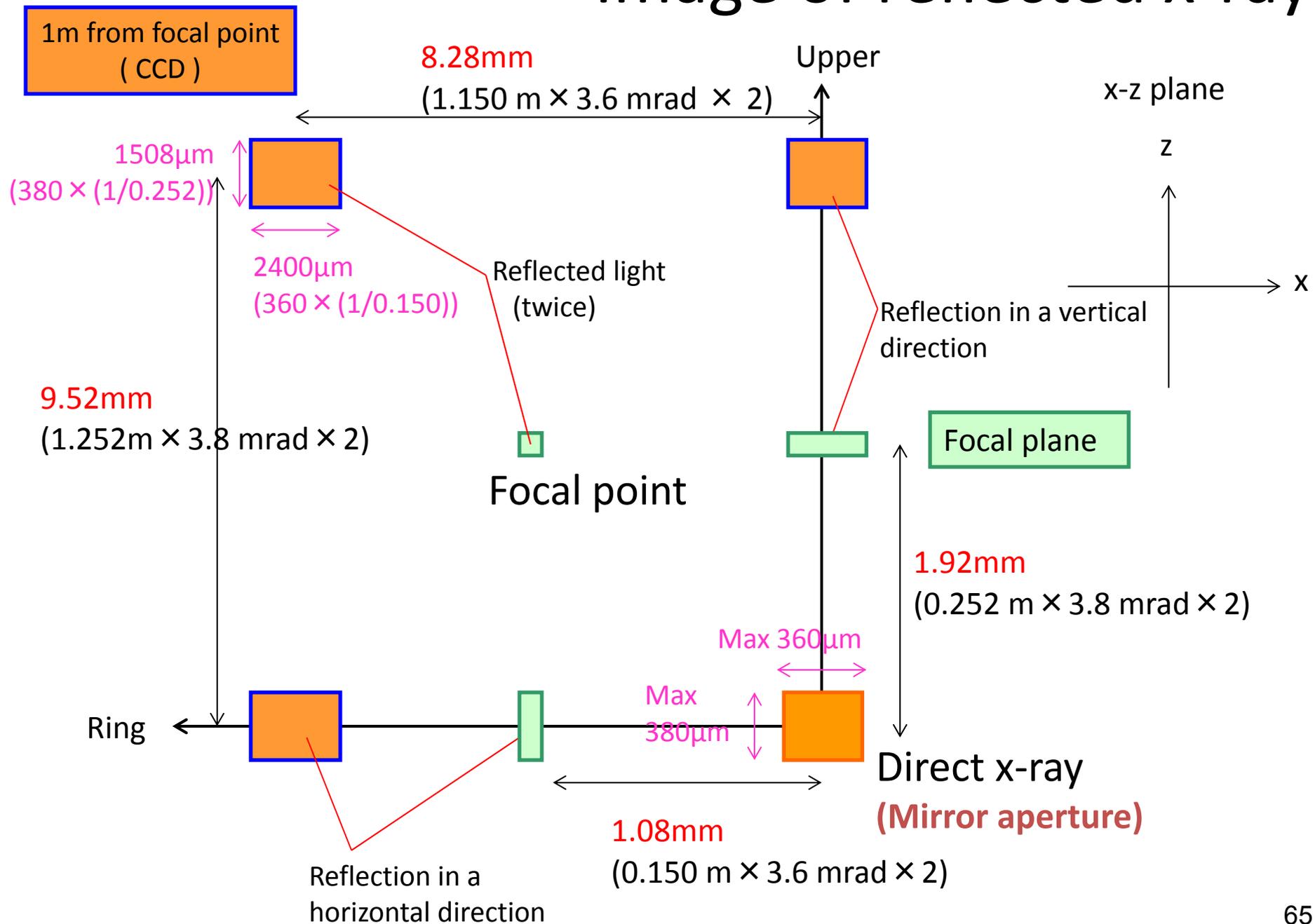
Image on X-ray CCD camera



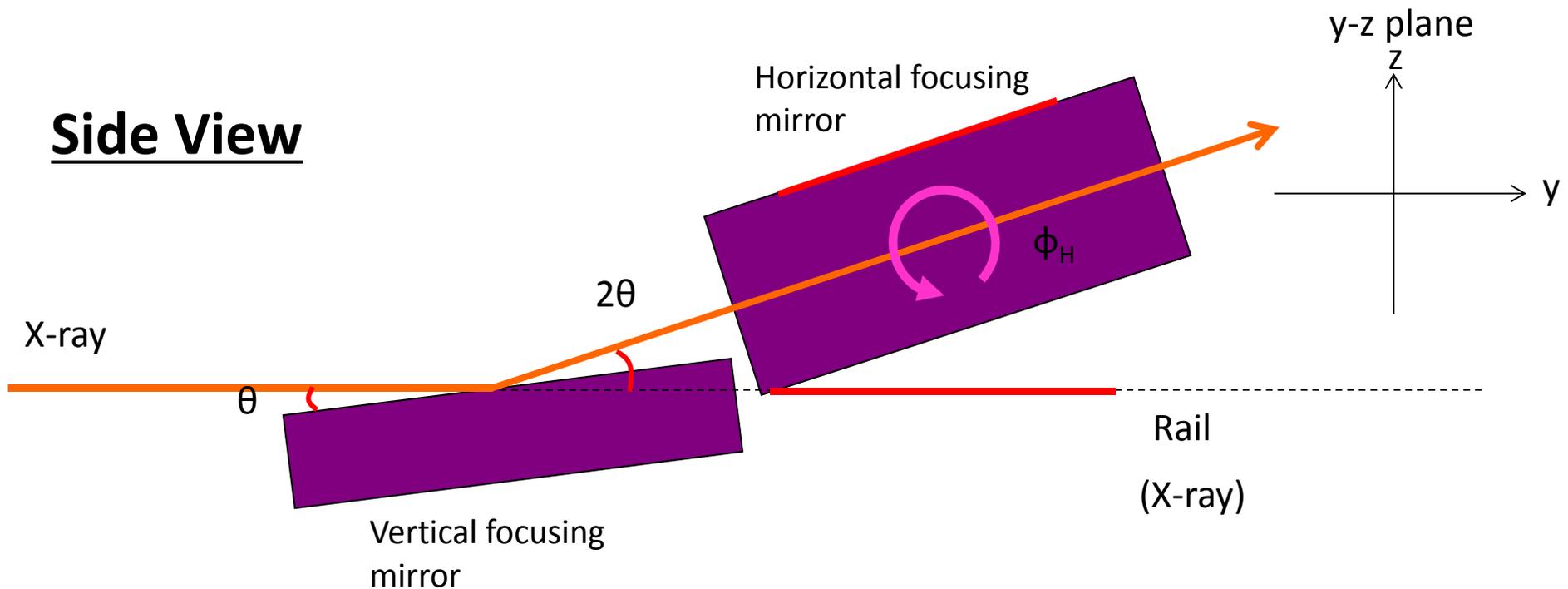
$$\theta = \frac{x}{2L}$$

Alignment

Image of reflected x-ray



Alignment of in-plane rotation (Horizontal focusing mirror)



$$\theta: 3.8\text{mrad} \rightarrow 2\theta: 7.6\text{mrad}$$

Reflected angle of vertical-focusing mirror needs to be considered, in the alignment of in-plane rotation of horizontal-focusing mirror.

Alignment of incident angle

- **Foucault test**

Rough assessment of focusing beam profile.

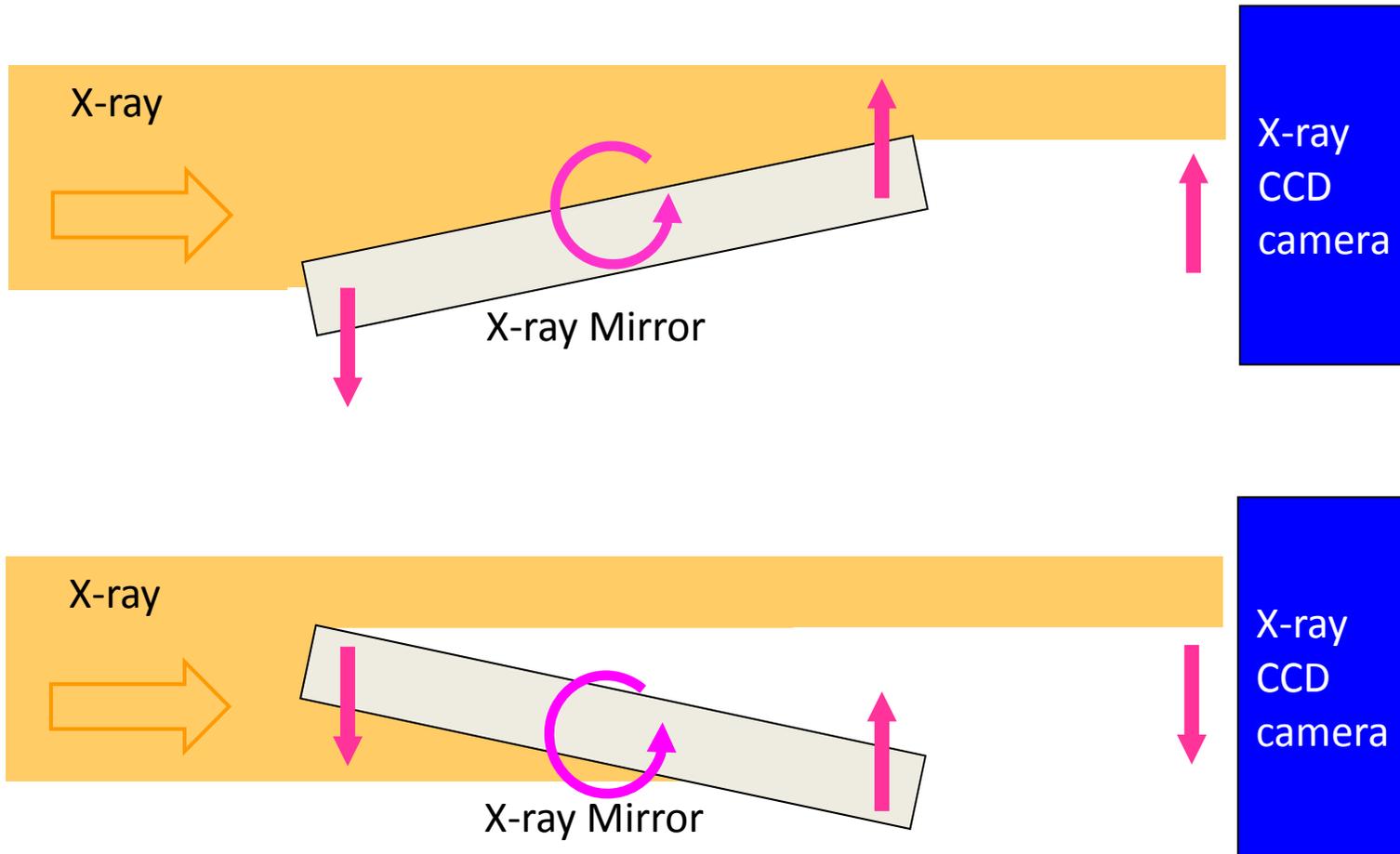
This method is used for *seeking focal point*.

- **Wire (Knife-edge) scan method**

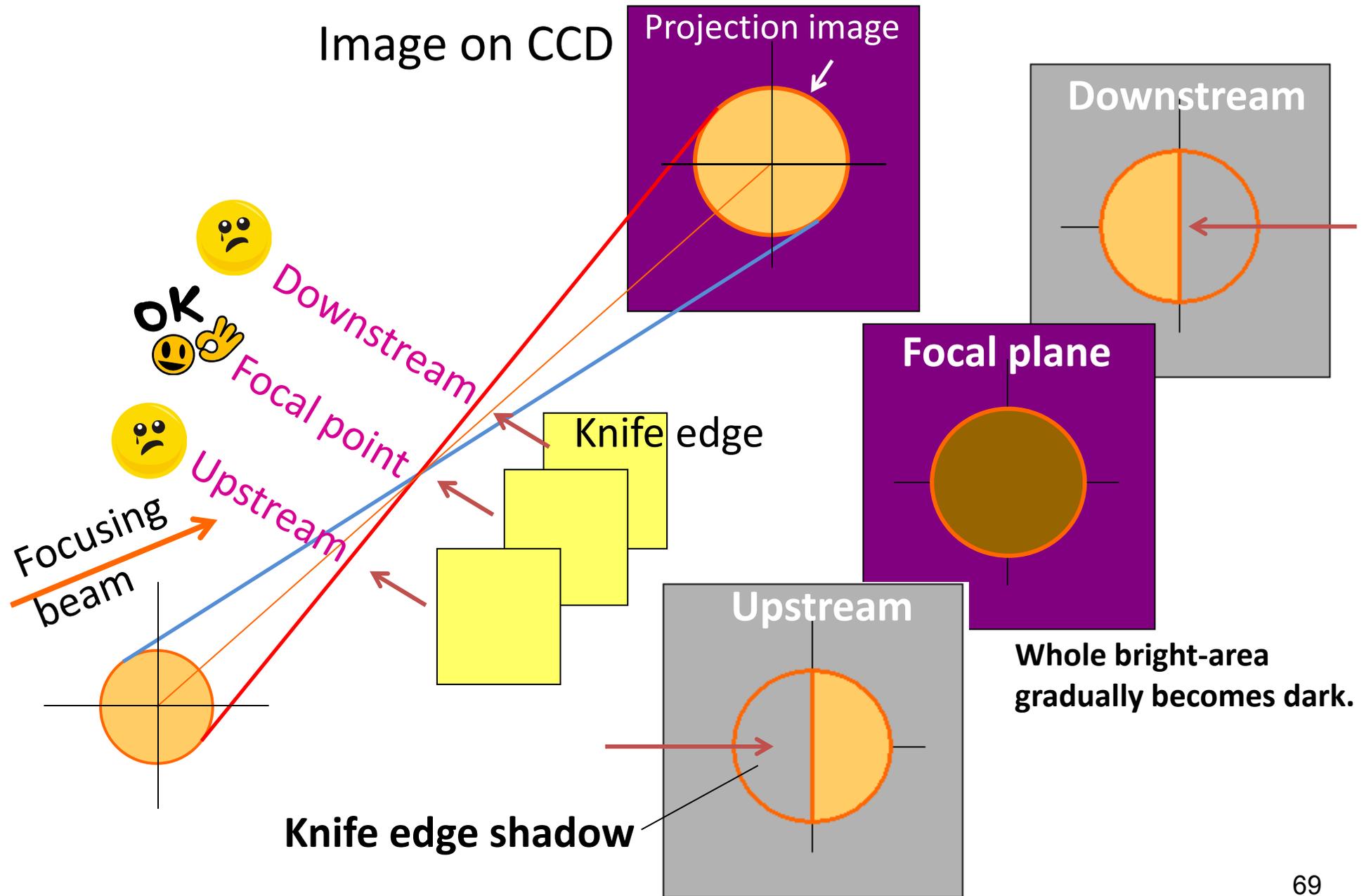
Final assessment of *focusing beam profile*.

Precise adjustment of the glancing angle and focal distance is performed until the best focusing is achieved, while monitoring the intensity profile.

Alignment of incident angle



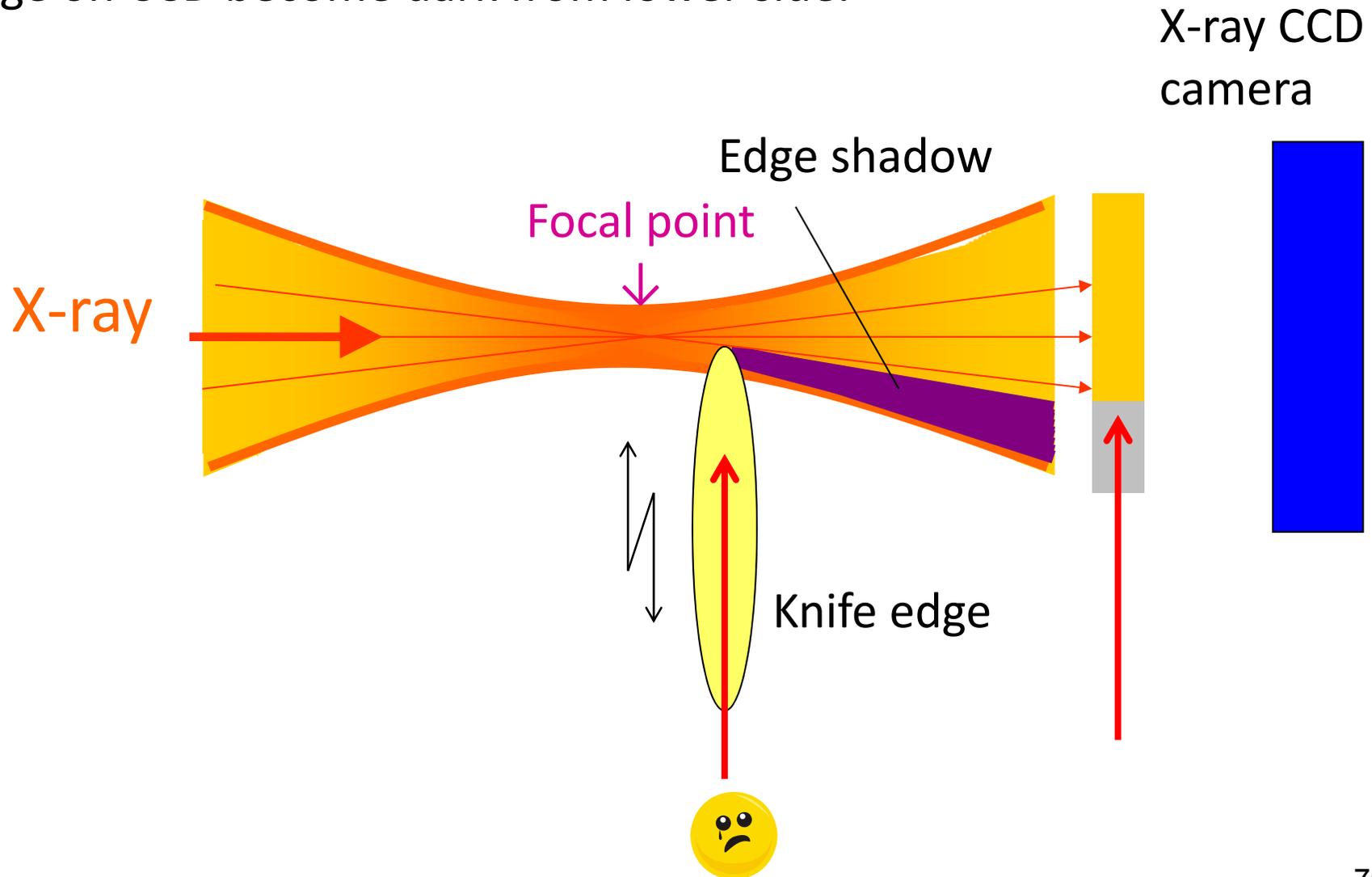
Foucault test



Foucault test 1

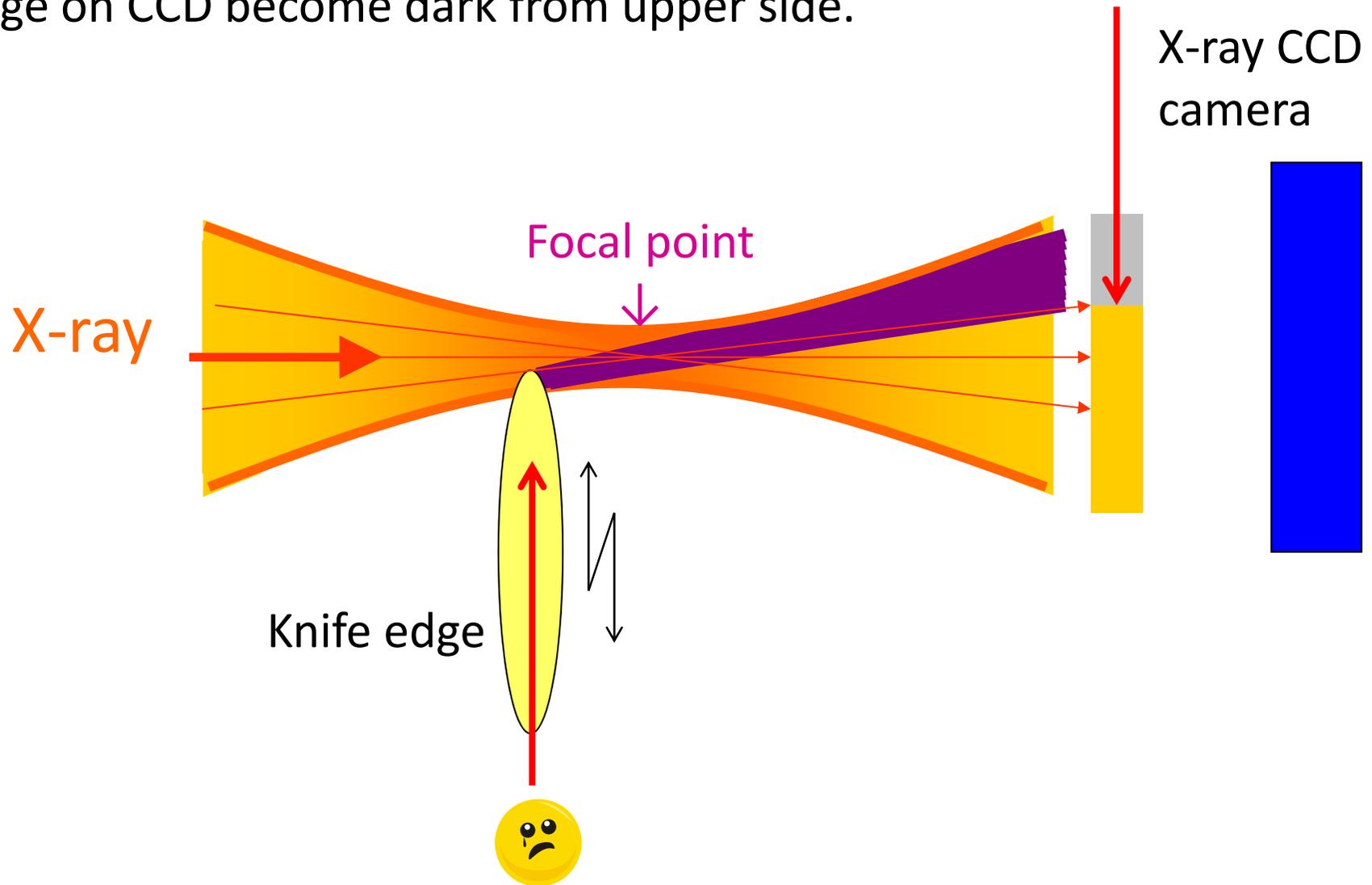
Wire is at downstream of focal point.

Image on CCD become dark from lower side.



Foucault test 2

Wire is at upstream of focal point.
Image on CCD become dark from upper side.

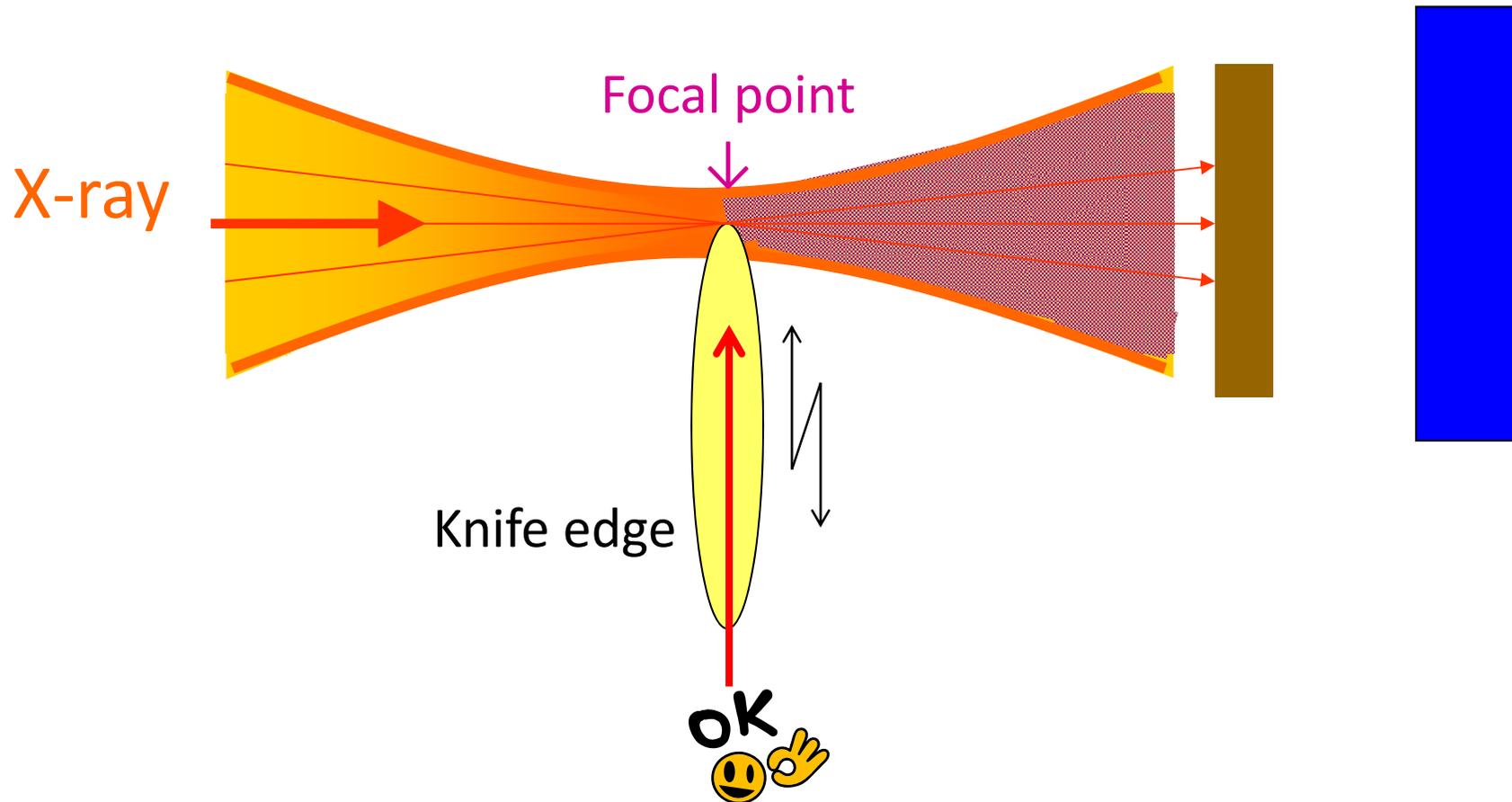


Foucault test 3

Wire is at the focal point.

Whole bright-area gradually becomes dark.

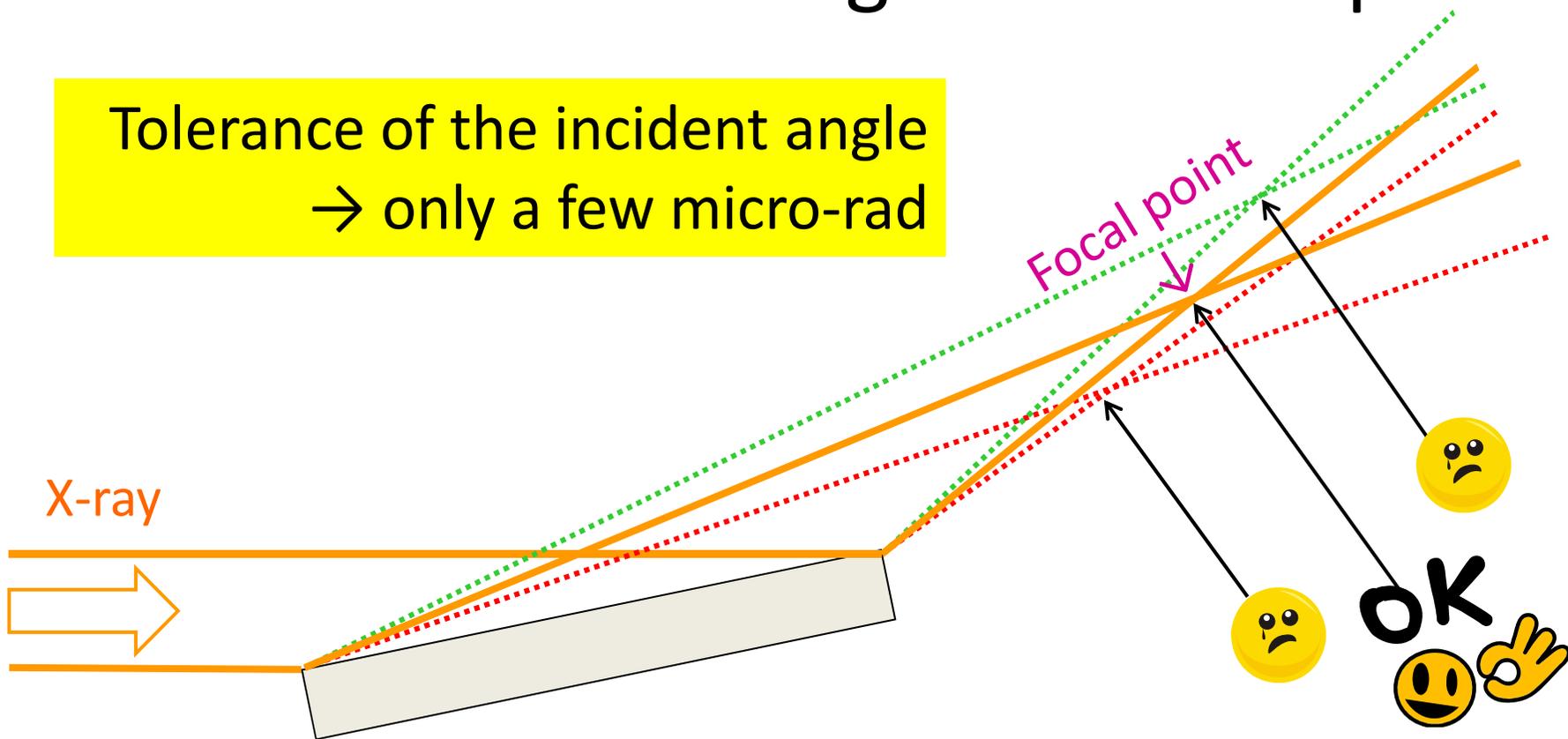
X-ray CCD camera



Relationship

between incident angle and focal position

Tolerance of the incident angle
→ only a few micro-rad

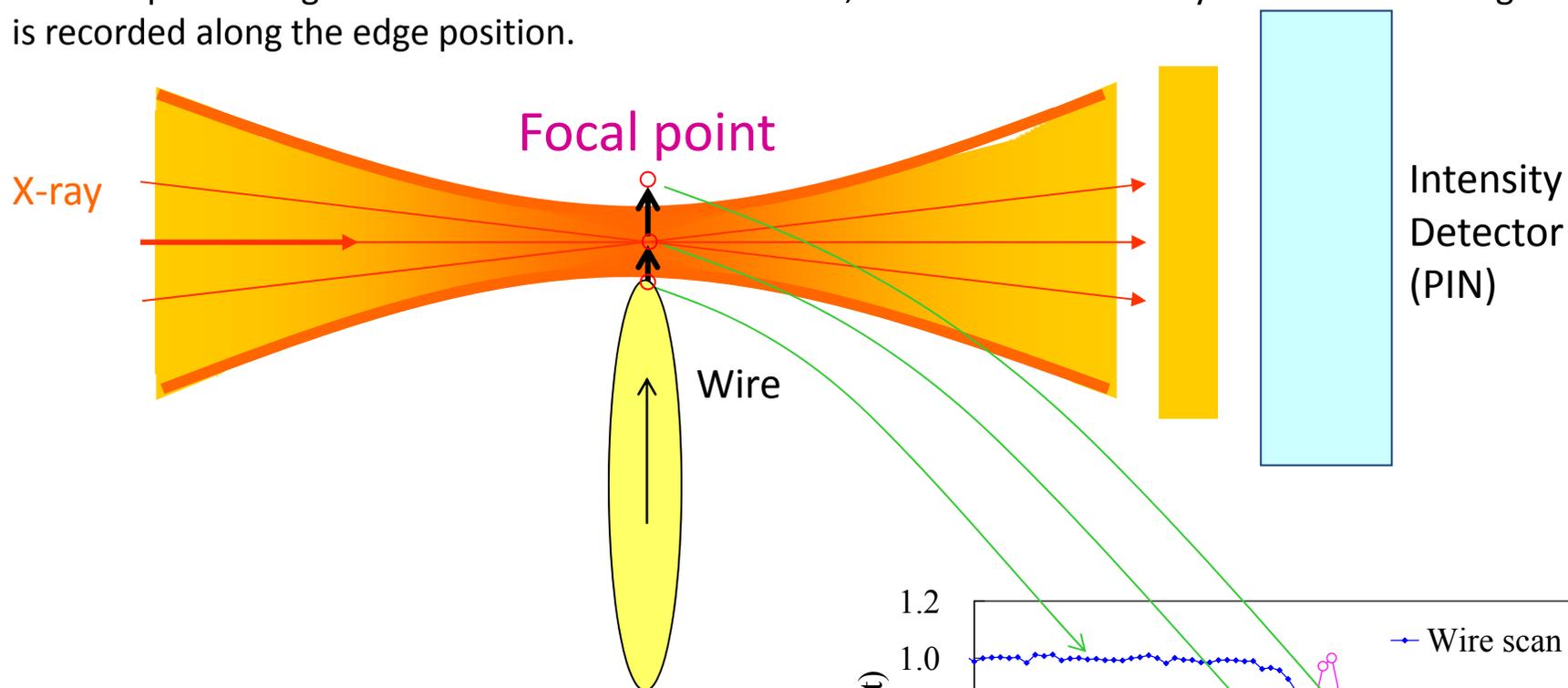


Incident angle → Large ⇒ Focal point → downstream

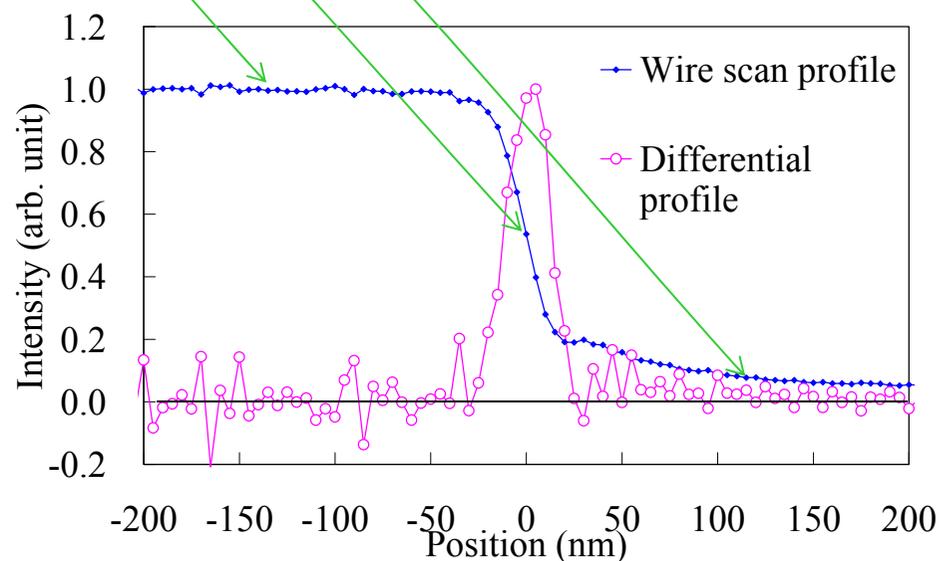
Incident angle → Small ⇒ Focal point → upstream

Wire (Knife-edge) scan method for measuring beam profiles

The sharp knife edge is scanned across the beam axis, and the total intensity of the transmitting beam is recorded along the edge position.

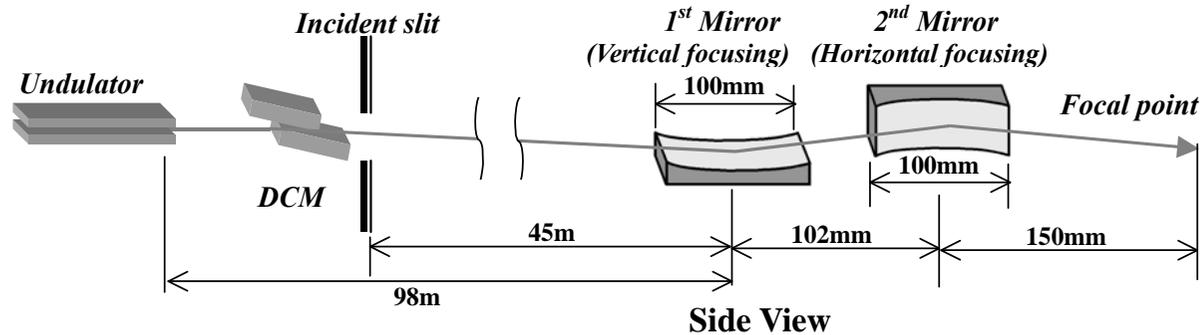


The line-spread function of the focused beam was derived from the numerical differential of the measured knife-edge scan profiles.



Relationship between Beam size and Source size

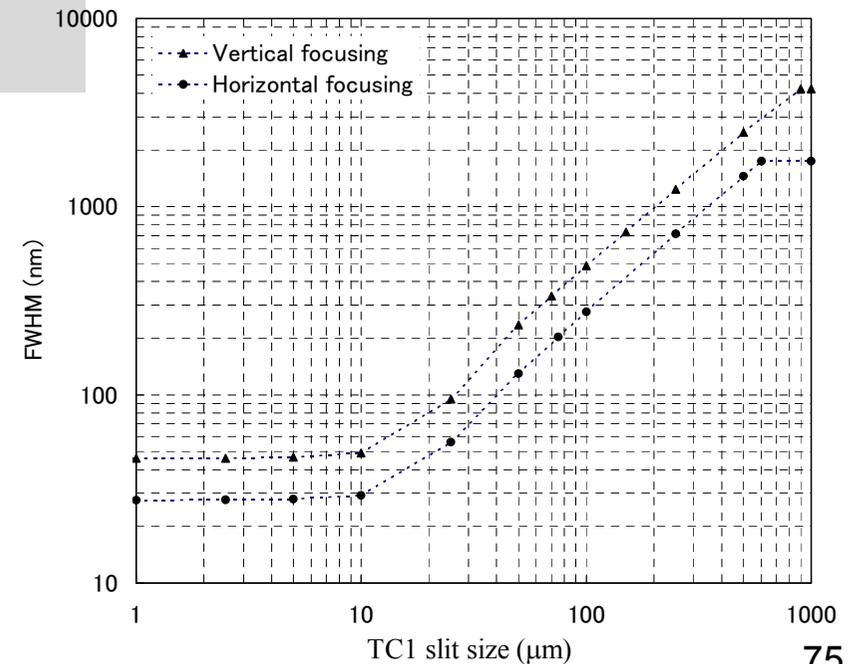
Beam size changes depending on source size (or virtual source size).



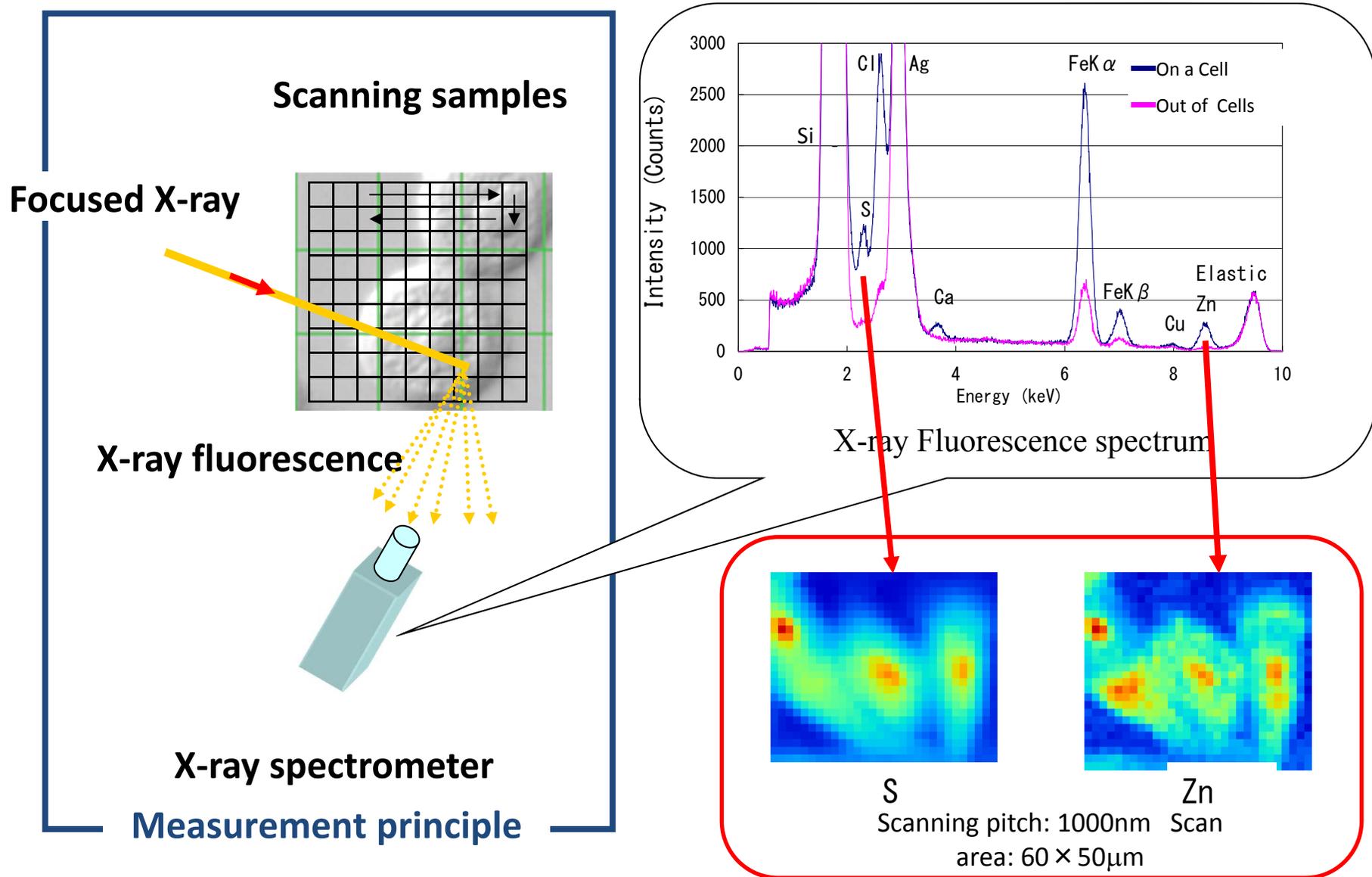
Beam size = Source size / M (M: demagnification)
AND
Beam size \geq Diffraction limit



Beam size is selectable
for each application.



Scanning X-ray Fluorescence Microscope: SXFM



Ref: M. Shimura et al., "Element array by scanning X-ray fluorescence microscopy after cis-diamminedichloro-platinum(II) treatment", Cancer research **65**, 4998 (2005).

Key issues of x-ray mirror

1. *To select the functions of x-ray mirror*

Deflecting, low pass filtering, focusing and collimating → Shape of the mirror

2. *To specify the incident and reflected beam properties*

Energy range , flux

→ absorption, cut off energy → coating material → incident angle

The beam size and the power of incident beam

→ opening of the mirror, incident angle

→ absorbed power density on the mirror → w/o cooling, substrate

Angular divergence / convergence, the reflected beam size

→ incident angle, position of the mirror (source, image to mirror)

Direction of the beam

→ effect of polarization, self-weight deformation

4. *To specify the tolerance of designed parameters*

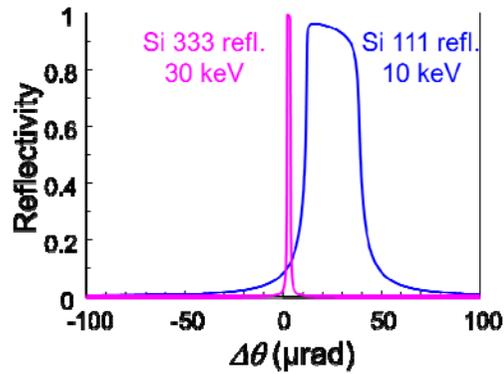
Roughness, density of coating material, radius error, figure error

The cost (price and lead time) depends entirely on the tolerance.

5. *To consider the alignment*

The freedom, resolution and range of the manipulator





Tailoring x-rays to application



X-ray monochromator

■ Principle

- ✓ Introduction of diffraction theory
- ✓ Dynamical theory
- ✓ DuMond diagram

■ Engineering



X-ray Monochromator

X-ray monochromator is key component for SR experiments:

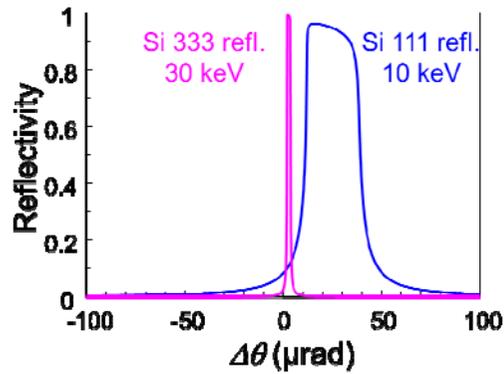
- ✓ length gauge for structure analysis,
- ✓ energy gauge for spectroscopy,...

Principle of x-ray monochromator

- ✓ Photon energy tuning ← Bragg's law
- ✓ Energy resolution ← source divergence, *Darwin width*,...
- ✓ Flux (throughput) ← related to *Darwin width*
- ➔ Understanding *the dynamical theory* for large & perfect crystal

Practical of the monochromator

- ✓ Double-crystal monochromator for fixed-exit
- ✓ Crystal cooling to manage high heat load
- ➔ *Mechanical engineering* issues



Tailoring x-rays to application



X-ray monochromator

■ Principle

- ✓ Introduction of diffraction theory
- ✓ Dynamical theory
- ✓ DuMond diagram

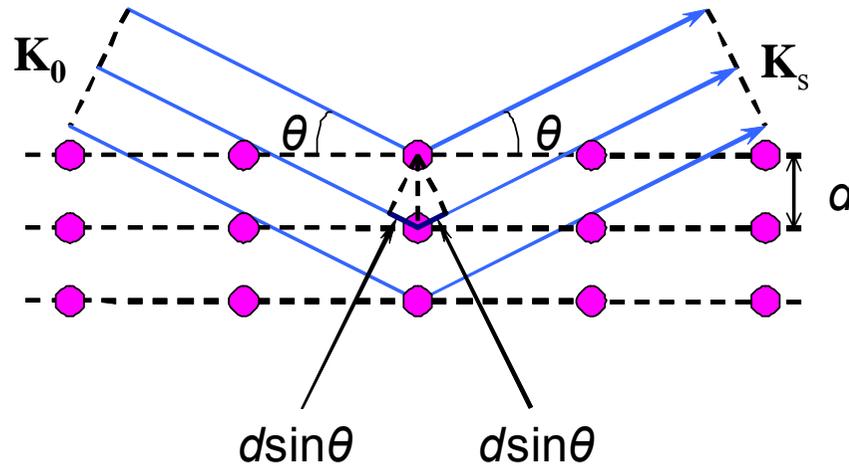
■ Engineering



Bragg reflection (*kinematical*)

Bragg's law
in real space

$$2d \sin \theta = m\lambda$$

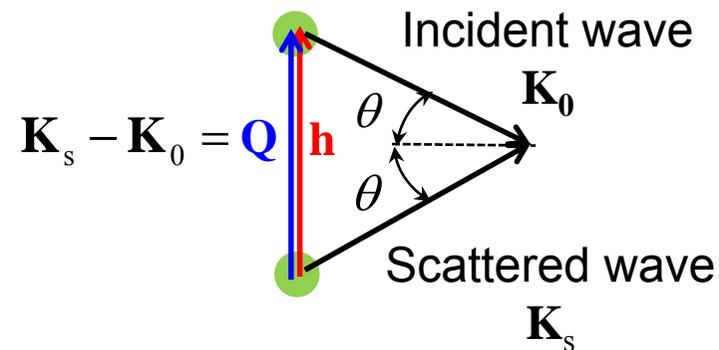


- 1) Phase matching on the single net plane by mirror-reflection condition.
- 2) Phase matching between net planes.

Laue condition
in reciprocal space

$$\mathbf{Q} = \mathbf{h}$$

Scattering vector \mathbf{Q} = Reciprocal lattice vector \mathbf{h}



Reciprocal lattice vector \mathbf{h}

- Normal to net plane
- Length = $1/d$

$$|\mathbf{K}_s| = |\mathbf{K}_0| = k = 1/\lambda$$

$$|\mathbf{Q}| = 2k \sin \theta = |\mathbf{h}| = 1/d$$

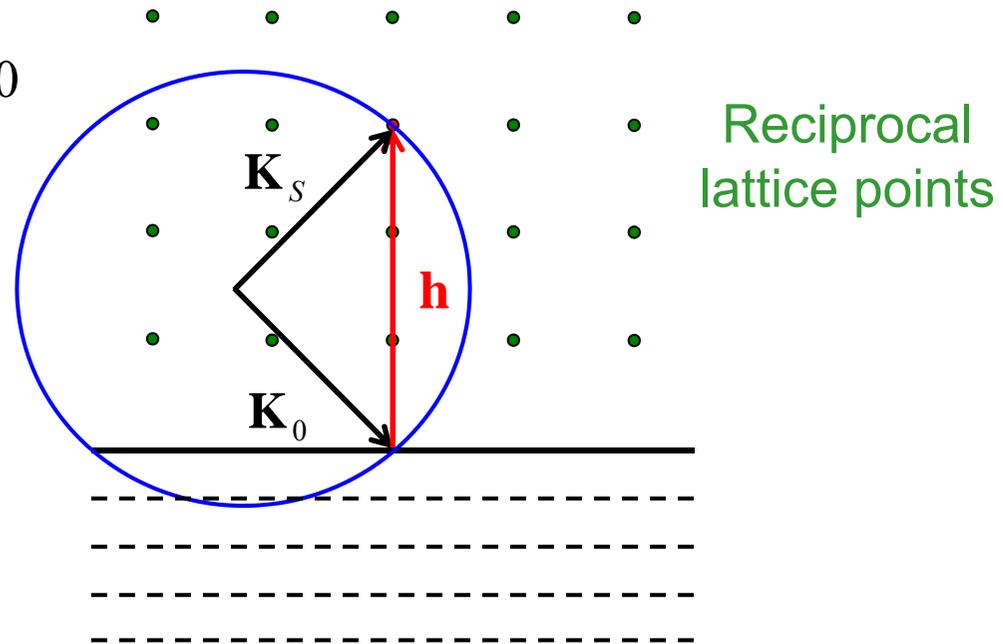
Laue condition equivalent to Bragg's law

Ewald sphere

Ewald sphere:

$$\text{Radius} = 1/\lambda = K_0$$

$$\mathbf{K}_s - \mathbf{K}_0 = \mathbf{h}$$

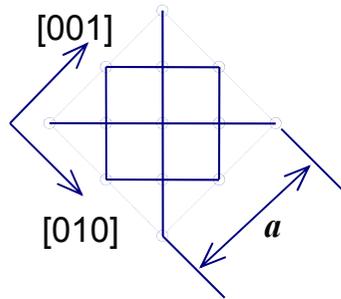


*When a reciprocal lattice point is **on the Ewald sphere**, Bragg reflection occurs.*

Miller indices and d -spacing for silicon

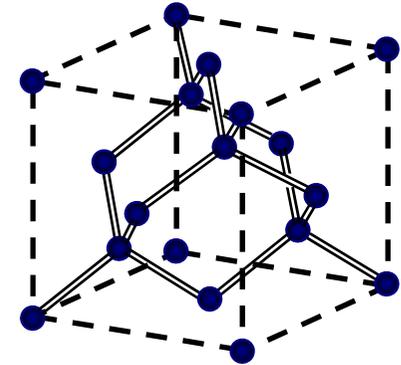
$$d = \frac{a}{\sqrt{h^2 + k^2 + l^2}}$$

Top view

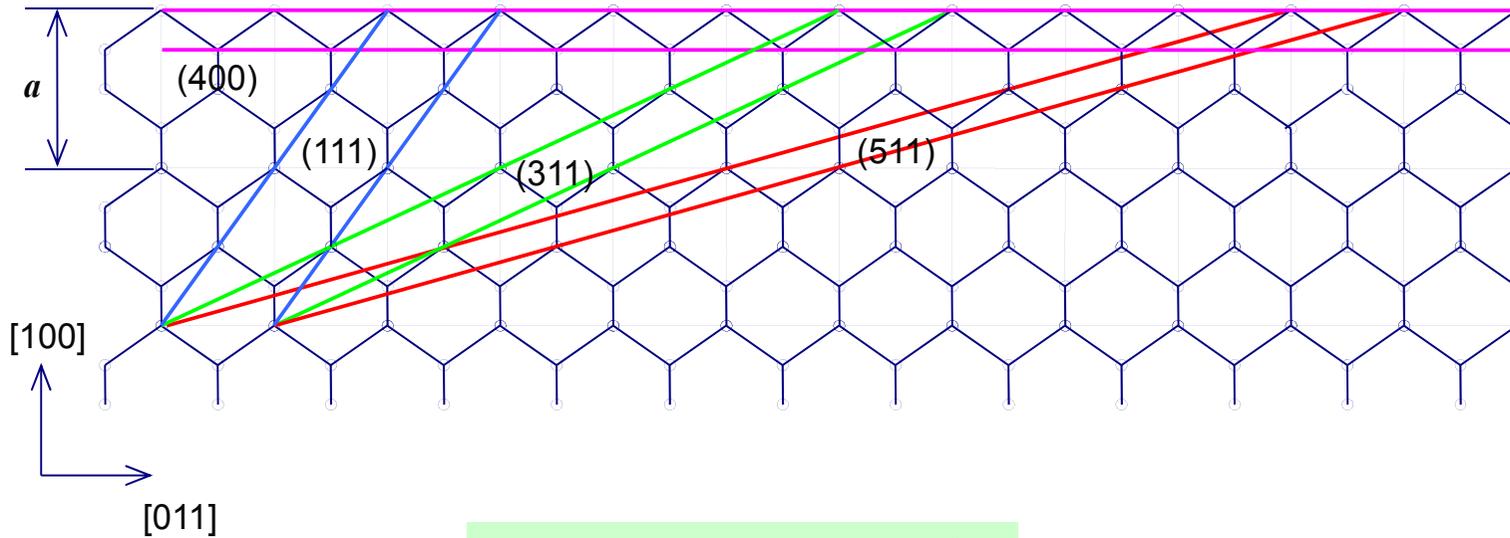


Silicon: $a = 5.431 \text{ \AA}$

- d -spacing
- (400) : 1.3578 \AA
 - (111) : 3.1356 \AA
 - (311) : 1.6375 \AA
 - (511) : 1.0452 \AA



Side view



Diamond : $a = 3.567 \text{ \AA}$

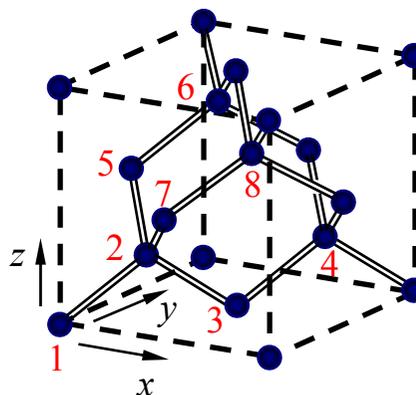
Crystal structure factor for diamond structure

Structure factor → Sum of atomic scattering with phase shift in the unit cell

$$F(\mathbf{h}) = \sum_j \underline{f_j(\mathbf{h}, E)} \exp(2\pi i \mathbf{h} \cdot \mathbf{r}_j)$$

Atomic scattering factor

$$F(\mathbf{h}) = \sum_j f_j(\mathbf{h}, E) \exp\{2\pi i (hx_j + ky_j + lz_j)\}$$



Position of atoms in the unit cell for diamond structure

$$(x_j, y_j, z_j) =$$

$$(0, 0, 0)_1, (1/4, 1/4, 1/4)_2,$$

$$(1/2, 1/2, 0)_3, (3/4, 3/4, 1/4)_4,$$

$$(0, 1/2, 1/2)_5, (1/4, 3/4, 3/4)_6,$$

$$(1/2, 0, 1/2)_7, (3/4, 1/4, 3/4)_8$$

For diamond structure

$$\left\{ \begin{array}{l} h, k, l \text{ Mixture of odd and even numbers} \\ F = 0 \end{array} \right.$$

$$\left\{ \begin{array}{l} h, k, l \text{ All odd, or, all even numbers, and } m: \text{ integer,} \end{array} \right.$$

$$\left\{ \begin{array}{lll} h + k + l = 4m & F = 8f & \leftarrow 8 \text{ atoms in phase} \end{array} \right.$$

$$\left\{ \begin{array}{lll} h + k + l = 4m \pm 1 & F = 4(1 \pm i)f & \leftarrow \text{Half contribute with phase shift } \pm \pi/2 \end{array} \right.$$

$$\left\{ \begin{array}{lll} h + k + l = 4m \pm 2 & F = 0 & \leftarrow \text{Half cancel with } \pi \end{array} \right.$$

Crystal structure factor for diamond structure

(400), (220),...

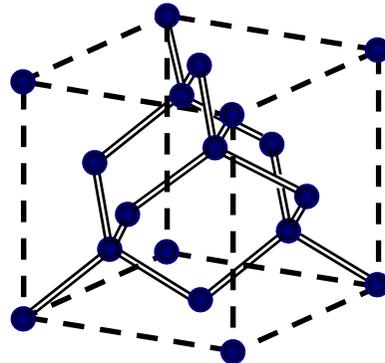
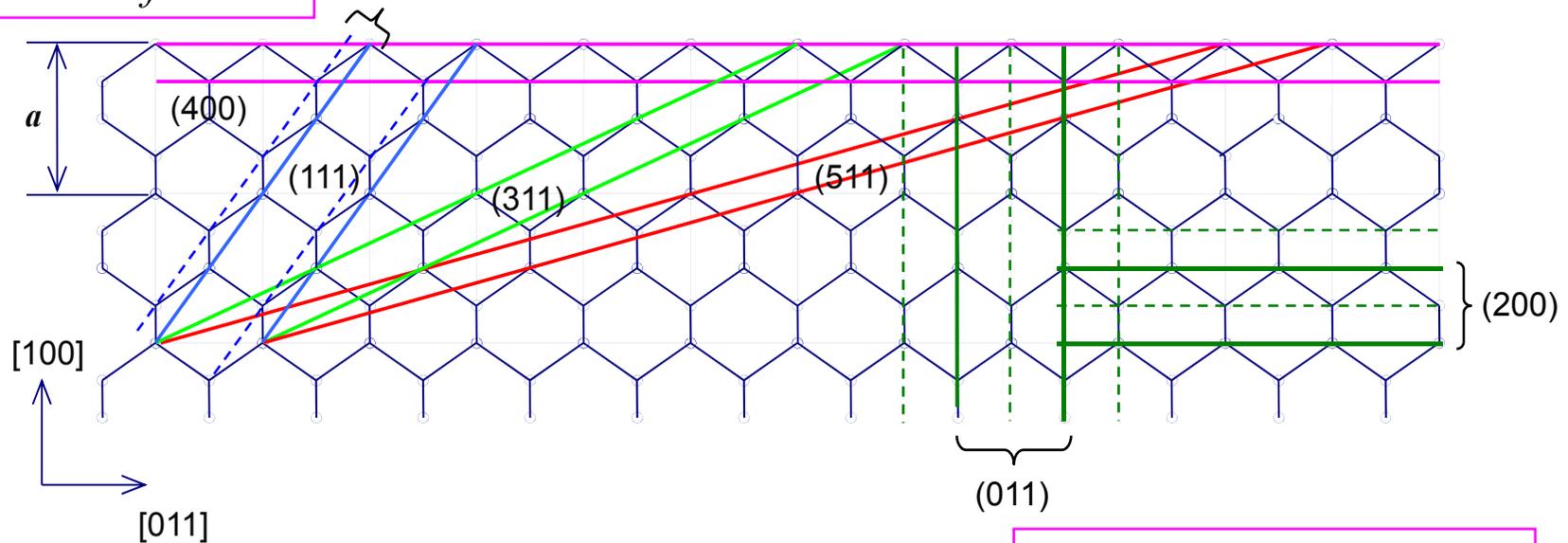
All in phase

$$\rightarrow F = 8f$$

(111), (311),...

Half contribute with phase shift $\pm \pi/2$

$$\rightarrow F = 4(1 \pm i)f$$



(011), (200),...

Half cancel with π

\rightarrow Forbidden reflection

$$F = 0$$

Total intensity in *kinematical* approximation

3-dimensional periodic structure of unit cell with number N_x, N_y, N_z

Total scattering intensity becomes:

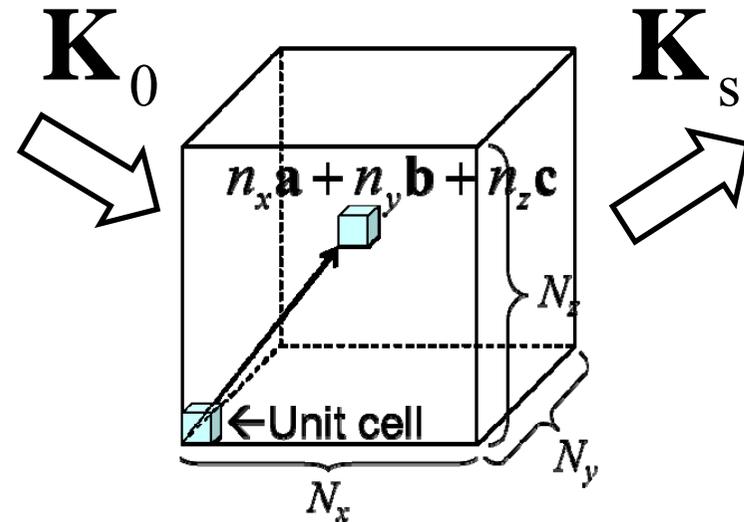
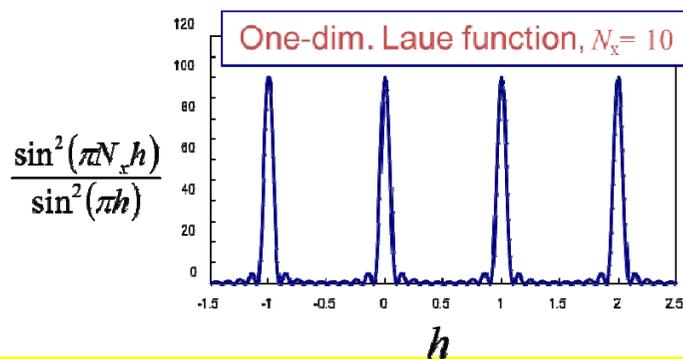
$$I = I_e |F(\mathbf{Q})|^2 \cdot |G(\mathbf{Q})|^2$$

Laue function:

$$|G(\mathbf{Q})|^2 = \frac{\sin^2(\pi N_x h)}{\sin^2(\pi h)} \cdot \frac{\sin^2(\pi N_y k)}{\sin^2(\pi k)} \cdot \frac{\sin^2(\pi N_z l)}{\sin^2(\pi l)}$$

h, k, l : integer \rightarrow Intense peaks

\rightarrow (hkl) reflection



Peak intensity N_x^2

FWHM $\Delta h \approx 0.8858/N_x \sim 1/N_x$

Crystal size (N) becomes larger

\rightarrow *narrower & higher, approaching delta function*

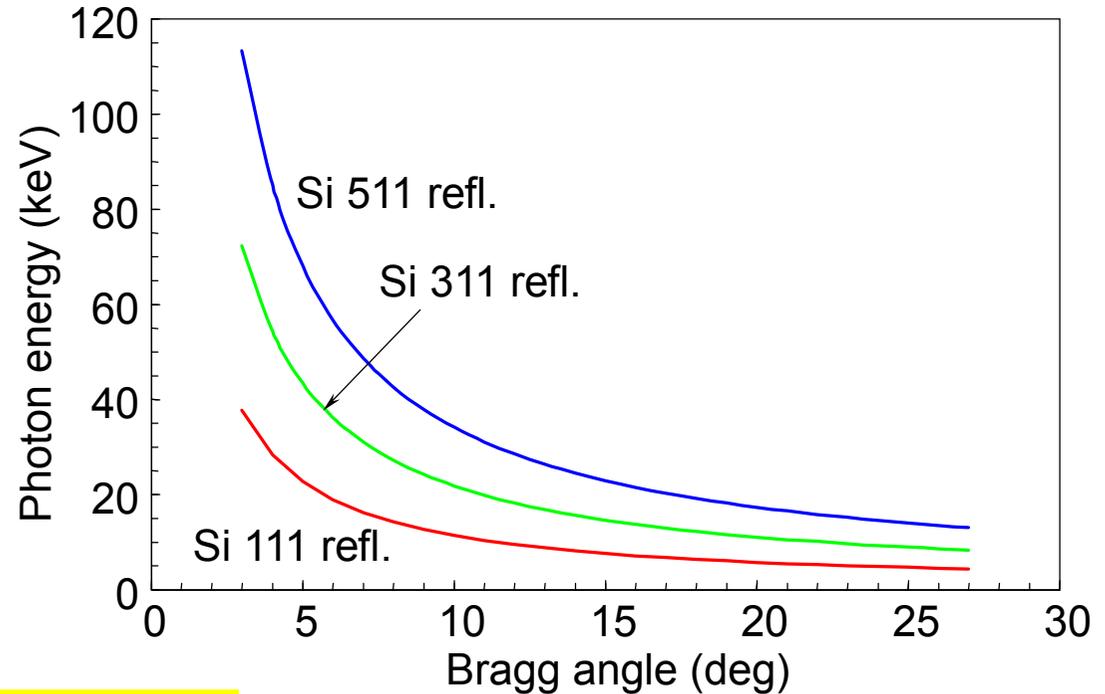
X-ray monochromator using *perfect crystal*

→ Perfect single crystal: **silicon, diamond**,...

Photon energy tuning:

✓ Crystal & lattice plane

✓ Bragg angle range



$$E \text{ [keV]} = \frac{12.3984}{2d_{hkl} \text{ [\AA]} \sin \theta_B}$$

ex) for SPring-8 standard DCM

Bragg angle: 3~27°

Total intensity in *kinematical* approximation

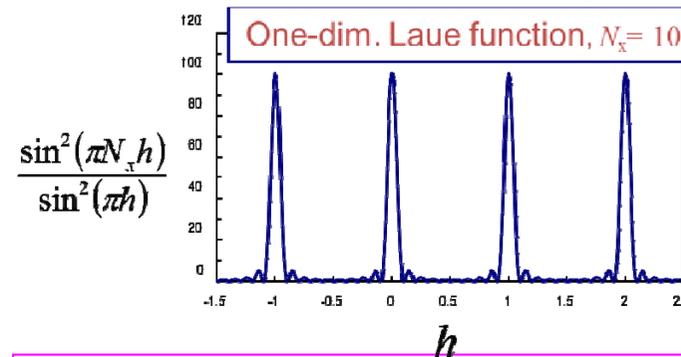
3-dimensional periodic structure of unit cell with number N_x, N_y, N_z

Total scattering intensity becomes:

$$I = I_e |F(\mathbf{Q})|^2 \cdot |G(\mathbf{Q})|^2$$

Laue function:

$$|G(\mathbf{Q})|^2 = \frac{\sin^2(\pi N_x h)}{\sin^2(\pi h)} \cdot \frac{\sin^2(\pi N_y k)}{\sin^2(\pi k)} \cdot \frac{\sin^2(\pi N_z l)}{\sin^2(\pi l)}$$



Peak intensity N_x^2
FWHM $\Delta h \approx 0.8858/N_x \sim 1/N_x$

Crystal size (N) becomes larger

→ narrower & higher, approaching delta function

$N \uparrow$

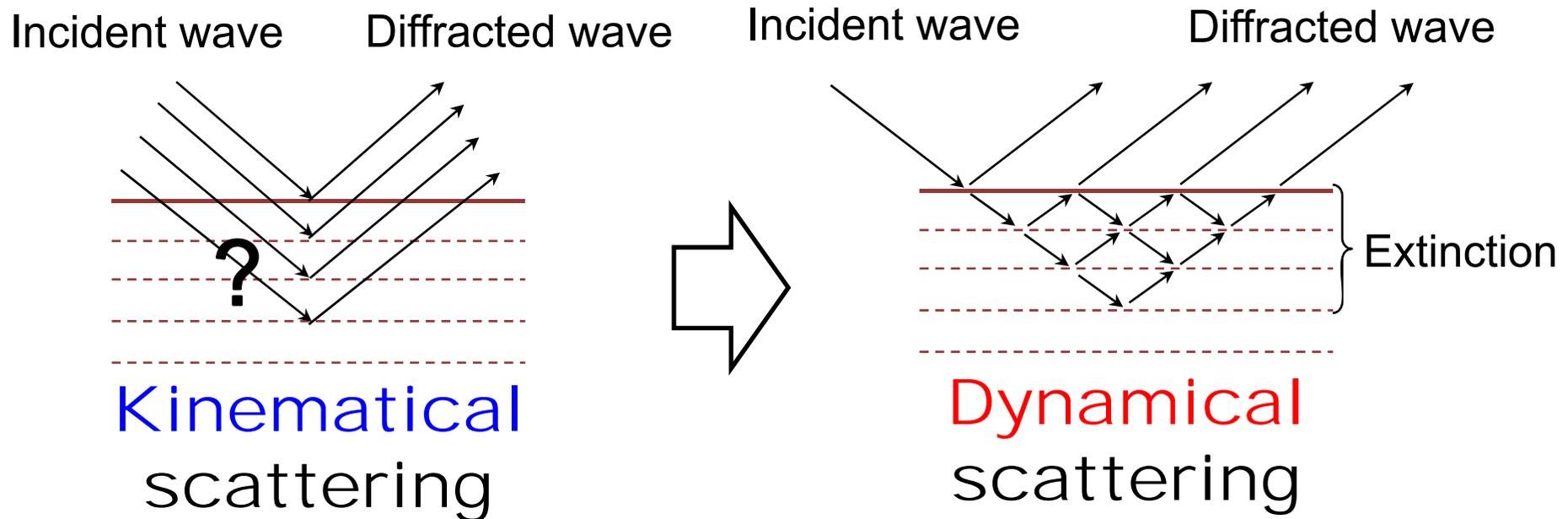
$FWHM \rightarrow 0, I \rightarrow \infty$



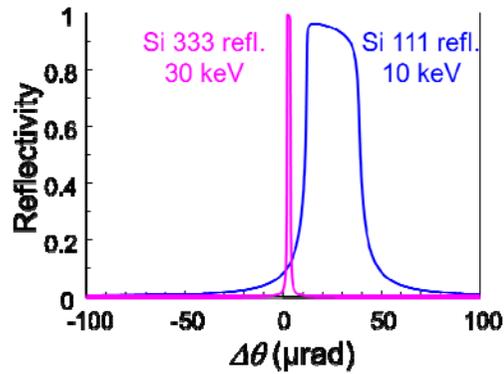
Diffraction theory *for large and perfect crystal* kinematical to dynamical theory

“Large & perfect” single crystal:

- 1) Multiple scattering in crystal
- 2) Extinction (Diffraction by “finite” number of net planes)



*Kinematical diffraction is invalid for large and perfect crystal.
Dynamical theory must be applied.*



Tailoring x-rays to application



X-ray monochromator

■ Principle

- ✓ Introduction of diffraction theory
- ✓ Dynamical theory
- ✓ DuMond diagram

■ Engineering

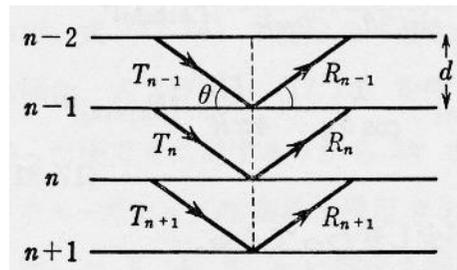
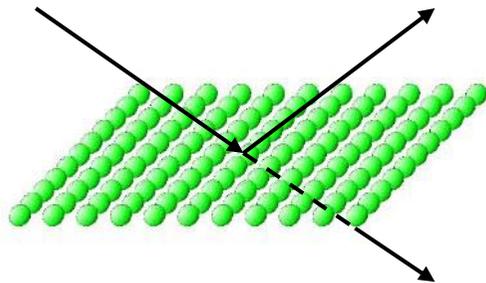


Dynamical theory

C. G. Darwin (1914)

the crystal as an finite stack of atomic planes

→ *difference equation*



$$T_n = tT_{n-1}e^{i\phi} + rR_n e^{2i\phi}$$

$$R_n = rT_n + tR_n e^{i\phi}$$

$$T_0 = 1, R_{-1} = 0$$

$$\phi = Kd \sin \theta$$

P. P. Ewald (1917)

Max von Laue (1931)

the crystal as a periodic dielectric constant

→ *Maxwell's equation*



Dynamical theory by Laue

#1

Fundamental equation

Fundamental equation is derived

using **Maxwell's equations** and introducing **Bloch wave**

for 3-dimensional periodic medium (= perfect single crystal):

Maxwell's equations

$$\rightarrow \operatorname{rot}(\operatorname{rot}E) = K^2(1 + \chi)E$$

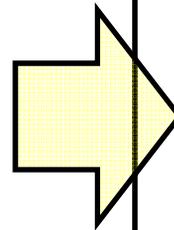
$$K = 2\pi/\lambda$$

$$E = \exp(-i\omega t) \sum_g E_g \exp(ik_g \cdot r)$$

$$k_g = k_0 + h$$

$$\chi(r) = \sum_g \chi_g \exp(ig \cdot r)$$

$$\chi_g \propto F(g)$$



$$\frac{k_h^2 - K^2}{K^2} E_h = \sum_g \chi_{h-g} P \cdot E_g$$

Fundamental equation

Fundamental equation is derived

$$\frac{k_h^2 - K^2}{K^2} E_h = \sum_g \chi_{h-g} P \cdot E_g$$

h, g, \dots : Reciprocal lattice points

E_h, E_g : Fourier components of electric field

K : Incident wave vector in vacuum

k_h : Wave vectors in the crystal

χ_h : **Fourier components of the polarizability** (Negative values, $10^{-6} \sim 10^{-5}$)

P : Polarization factor between h and g waves

$k_h = k_0 + h$: Momentum conservation

#2 When one wave E_0 in crystal

Fundamental equation

$$\frac{k_h^2 - K^2}{K^2} E_h = \sum_g \chi_{h-g} P \cdot E_g$$

Waves E in the crystal

$$E = \sum_g E_g \exp(ik_g \cdot r)$$

$$k_h = k_0 + h \rightarrow \text{Bloch wave}$$

When one wave E_0 in the crystal

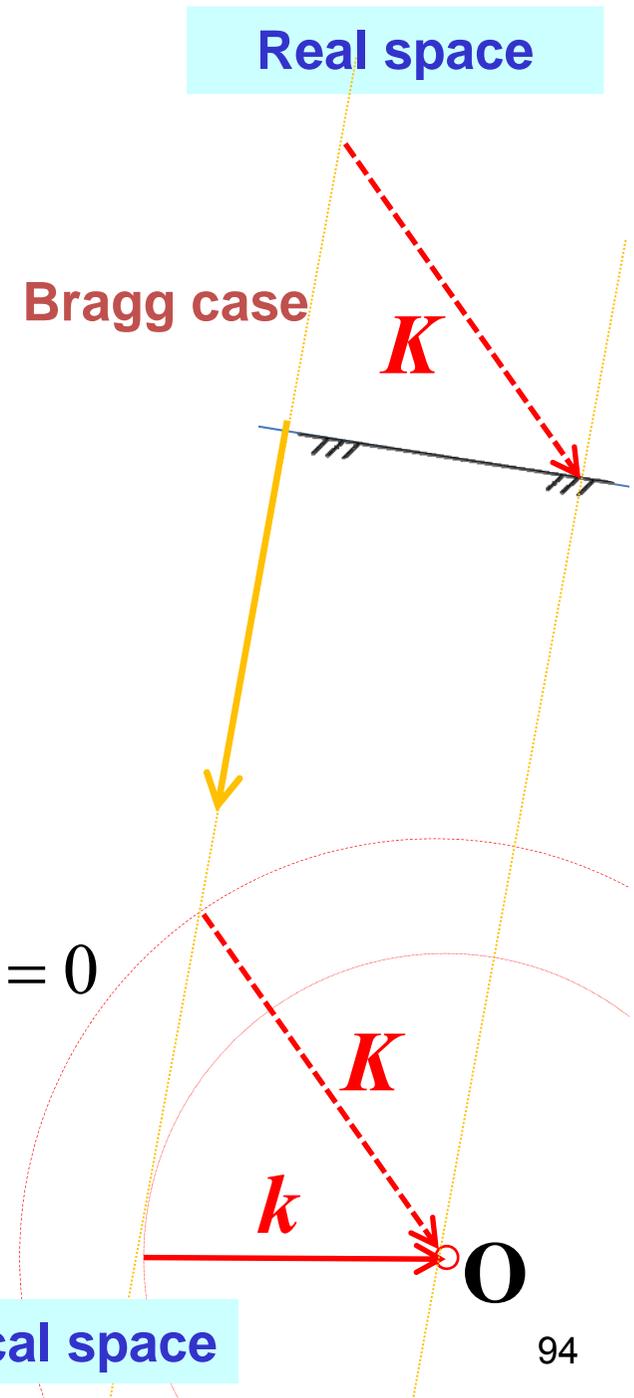
$$\frac{k_0^2 - K^2}{K^2} E_0 = \chi_0 E_0 \therefore \left\{ (1 + \chi_0) K^2 - k_0^2 \right\} E_0 = 0$$

$$k_0 = K \sqrt{1 + \chi_0} \equiv k$$

$$k \approx K(1 + \chi_0/2)$$

k : Mean wave number in the crystal

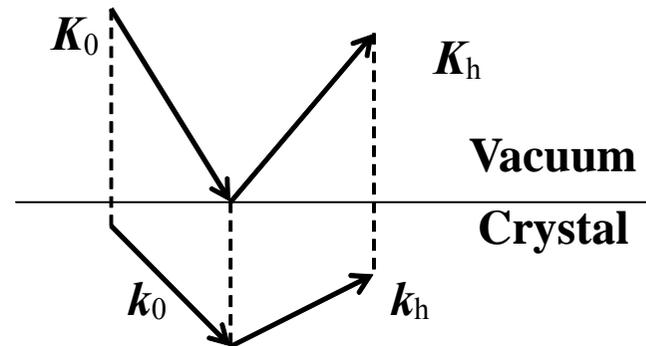
Reciprocal space



#3

Boundary condition of wave vector

We must consider connections of waves from vacuum into the crystal and from the crystal to vacuum, to solve the equations.



Incident wave in vacuum	K_0
→ Refracted wave in the crystal	k_0
→ Reflected wave in the crystal	k_h
→ Reflected wave in vacuum	K_h

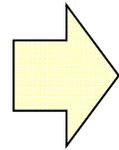
Tangential component of wave vector must be continuous

#4

Two-beam approximation

Fundamental equation is reduced to the equation for **two beams (waves)** of incidence E_0 and "one" intense diffraction E_h

$$\frac{k_h^2 - K^2}{K^2} E_h = \sum_g \chi_{h-g} P \cdot E_g$$



$$(A) \quad \frac{k_0^2 - K^2}{K^2} E_0 = \chi_0 E_0 + P \chi_{-h} E_h$$

$$(B) \quad \frac{k_h^2 - K^2}{K^2} E_h = P \chi_h E_0 + \chi_0 E_h$$

$$\chi_0, \chi_h, \chi_{-h}$$

Fourier components of the polarizability

Negative values, $10^{-6} \sim 10^{-5}$

$$\chi_h = \chi_{-h} \quad \text{for Si}$$

P

Polarization factor

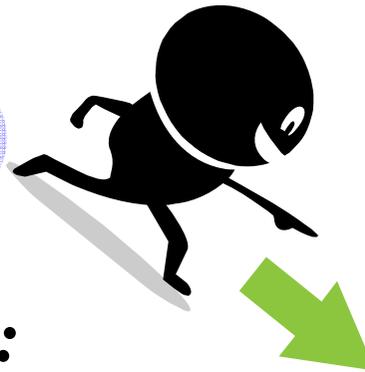
$$\sigma : P = 1, \quad \pi : P = \cos 2\theta_B$$

Two-beam approximation

Two beams (waves) of incidence E_0 and "one" intense diffraction E_h

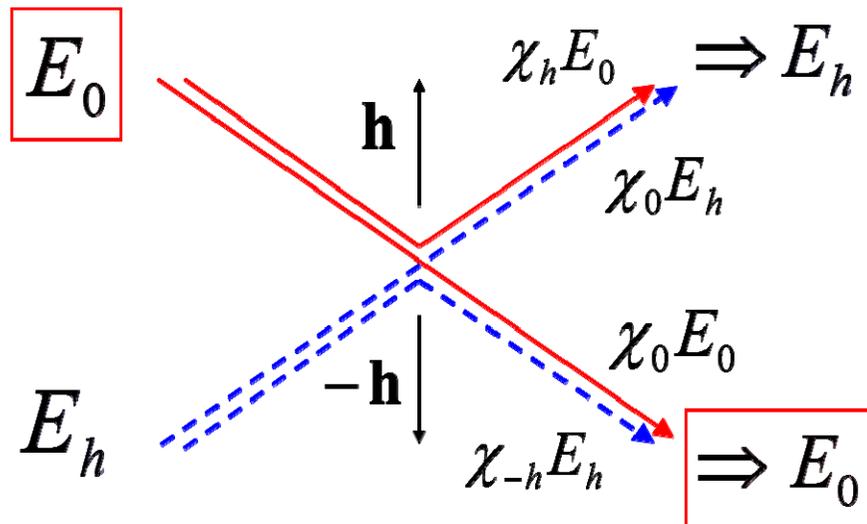
$$(A) \quad \frac{k_0^2 - K_0^2}{K_0^2} E_0 = \chi_0 E_0 + P \chi_{-h} E_h$$

$$(B) \quad \frac{k_h^2 - K^2}{K^2} E_h = P \chi_h E_0 + \chi_0 E_h$$



Goal

What means these equations:



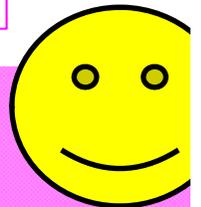
Scheme of **self-consistent wave field**

$$R = r^2 = \left(\frac{E_h}{E_0} \right)^2$$

$$FWHM = \Delta\theta_{\text{Darwin}}$$

Reflectivity curve

Effective band width 97



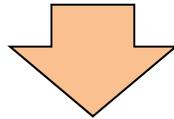
#5

Dispersion surface

Real space

Using two equations, we obtain following secular equation:

$$(A) \quad \frac{k_0^2 - K_0^2}{K_0^2} E_0 = \chi_0 E_0 + P \chi_{-h} E_h$$
$$(B) \quad \frac{k_h^2 - K^2}{K^2} E_h = P \chi_h E_0 + \chi_0 E_h$$



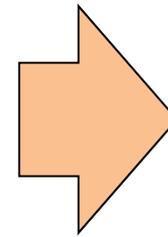
Secular equation

$$(k_0^2 - k^2)(k_h^2 - k^2) = \chi_h \chi_{-h} P^2 K^4$$

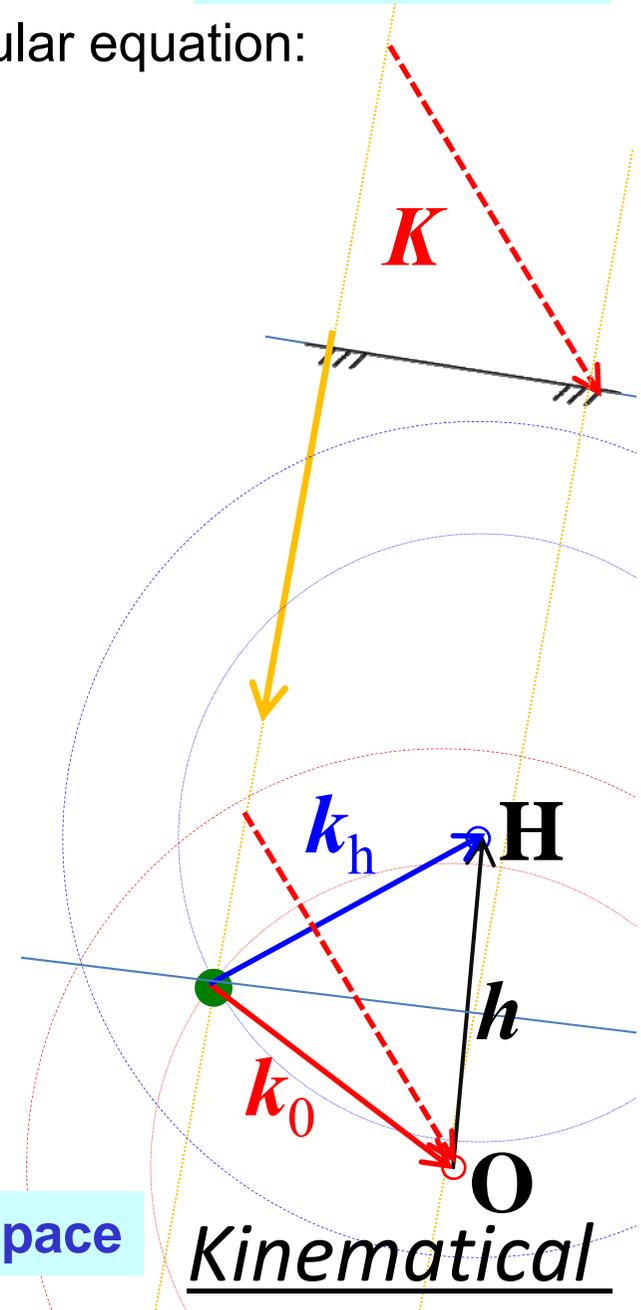
$$k_h = k_0 + h$$

$$\chi_h = \chi_{-h} = 0$$

Not our goal!



Reciprocal space

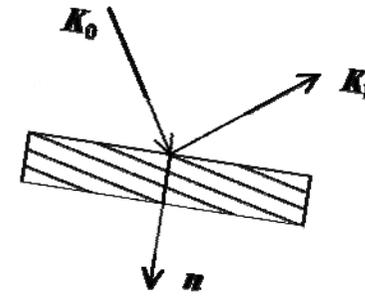


Dispersion surface

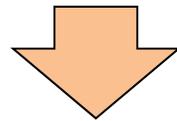
Real space

$$(A) \quad \frac{k_0^2 - K_0^2}{K_0^2} E_0 = \chi_0 E_0 + P \chi_{-h} E_h$$

$$(B) \quad \frac{k_h^2 - K^2}{K^2} E_h = P \chi_h E_0 + \chi_0 E_h$$



Bragg case



Secular equation

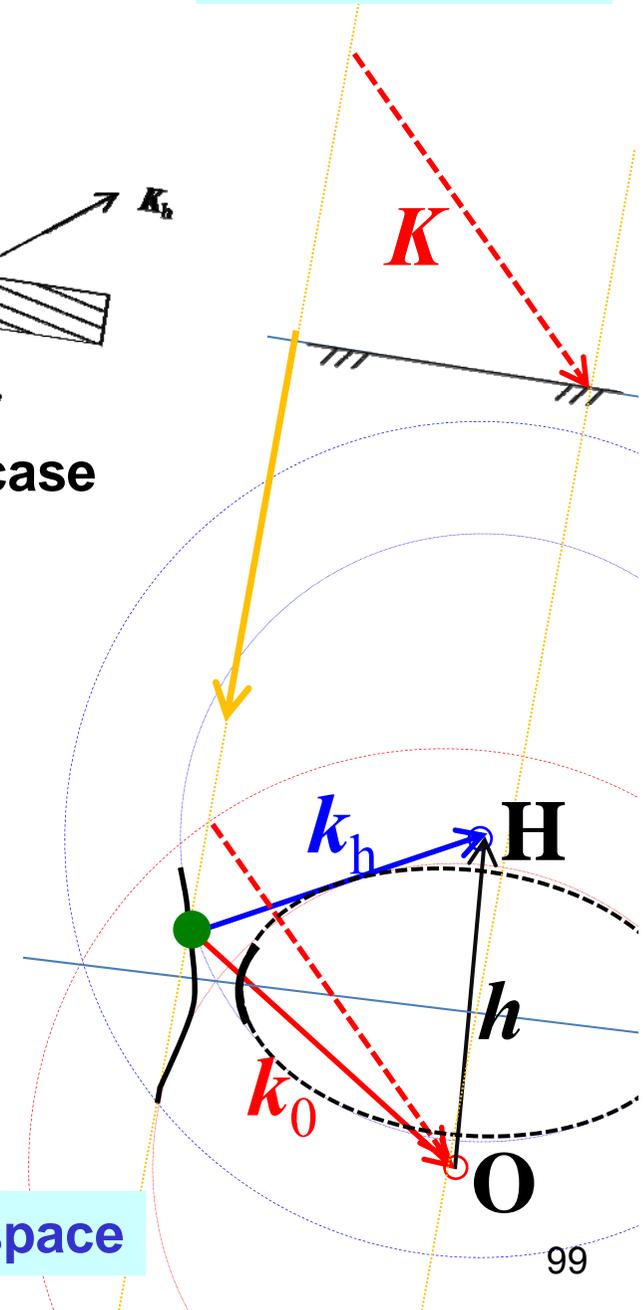
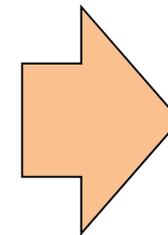
$$(k_0^2 - k^2)(k_h^2 - k^2) = \chi_h \chi_{-h} P^2 K^4$$

$$k_h = k_0 + h$$

$$\chi_h \neq 0 \neq \chi_{-h}$$

Secular equation can be reduced to quadratic equation near Brillouin zone boundary.

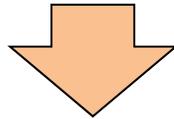
Reciprocal space



Dispersion surface

$$(A) \quad \frac{k_0^2 - K_0^2}{K_0^2} E_0 = \chi_0 E_0 + P \chi_{-h} E_h$$

$$(B) \quad \frac{k_h^2 - K^2}{K^2} E_h = P \chi_h E_0 + \chi_0 E_h$$



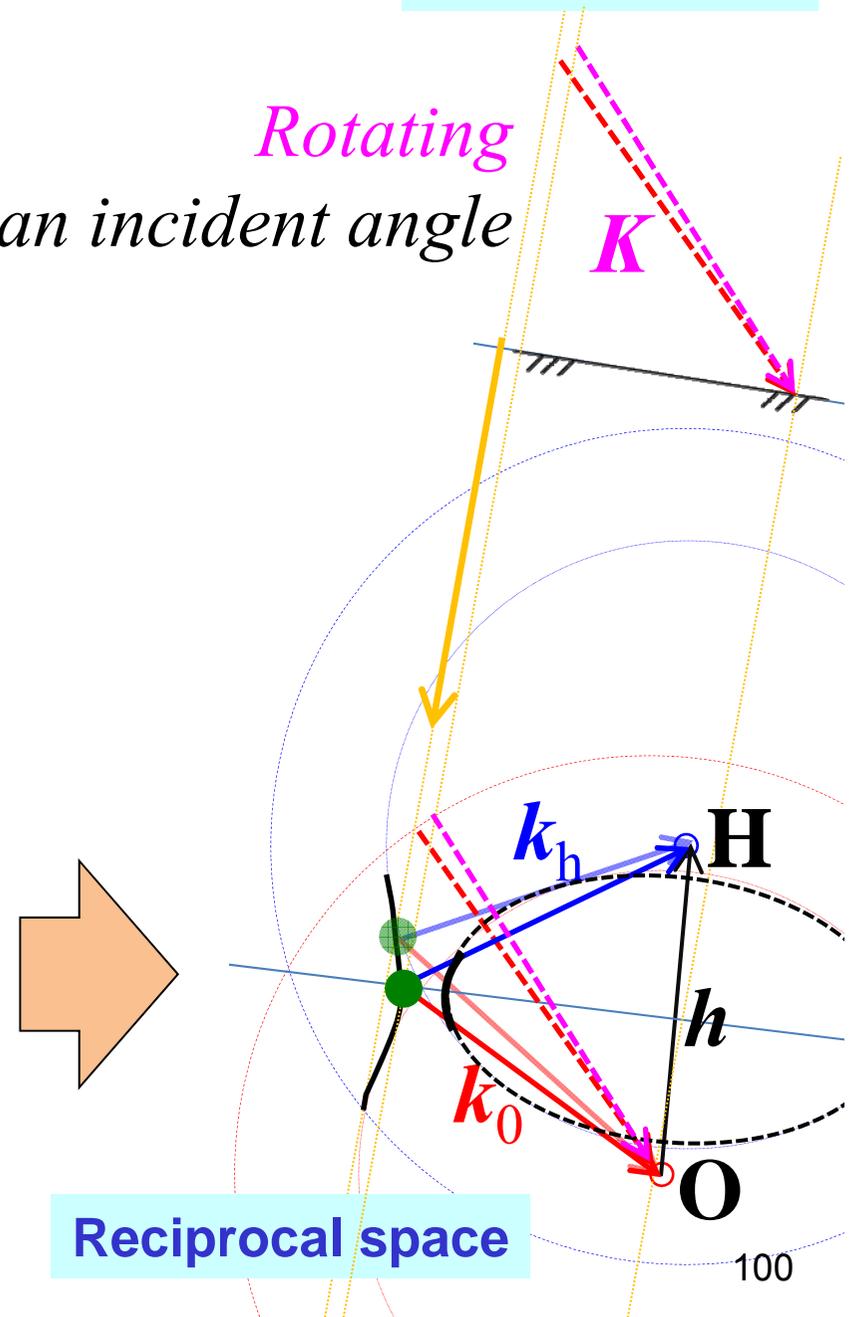
Secular equation

$$(k_0^2 - k^2)(k_h^2 - k^2) = \chi_h \chi_{-h} P^2 K^4$$

$$k_h = k_0 + h$$

$$\chi_h \neq 0 \neq \chi_{-h}$$

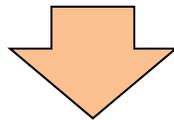
*Rotating
an incident angle*



Dispersion surface

$$(A) \quad \frac{k_0^2 - K_0^2}{K_0^2} E_0 = \chi_0 E_0 + P \chi_{-h} E_h$$

$$(B) \quad \frac{k_h^2 - K^2}{K^2} E_h = P \chi_h E_0 + \chi_0 E_h$$

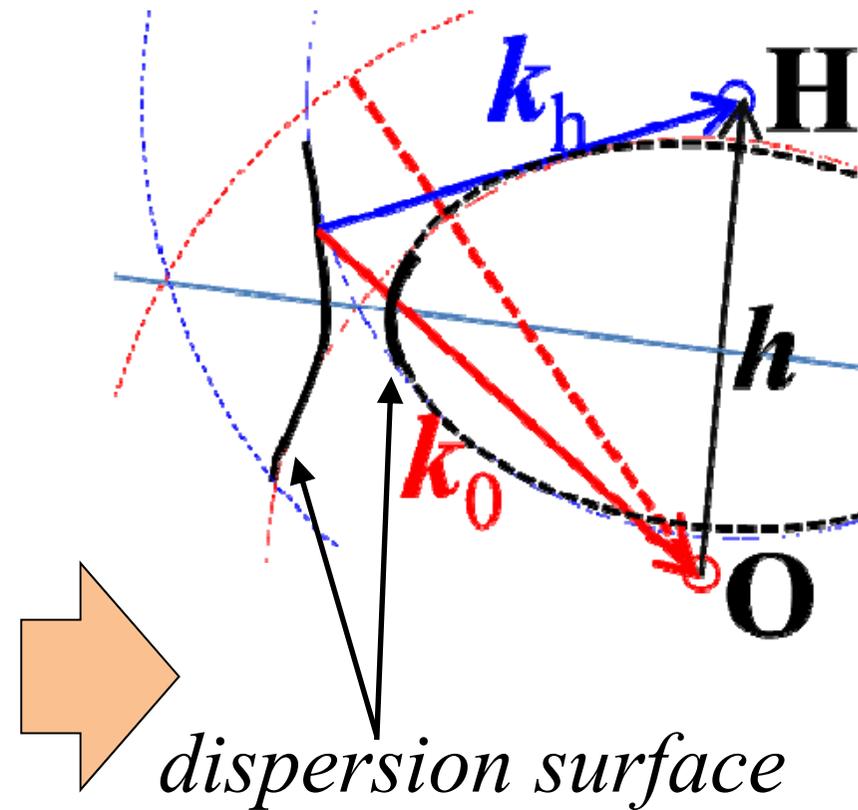


Secular equation

$$(k_0^2 - k^2)(k_h^2 - k^2) = \chi_h \chi_{-h} P^2 K^4$$

$$k_h = k_0 + h$$

$$\chi_h \neq 0 \neq \chi_{-h}$$



In the gap between two dispersion surfaces

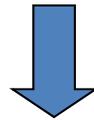
total reflection occurs for Bragg case.

#6

Normalized deviation parameter W

Parameter W is related to **the gap between two dispersion surfaces** and **total reflection occurs at $-1 < W < 1$** for Bragg case.

$$W = -\frac{2(\mathbf{K}_0 \cdot \mathbf{h}) + h^2}{2K_0^2} \sqrt{\frac{\gamma_0}{|\gamma_h|}} \frac{1}{|\chi_{hr}| \cdot |P|} + \frac{\chi_{0r}}{2|\chi_{hr}| \cdot |P|} \sqrt{\frac{\gamma_0}{|\gamma_h|}} \left(1 - \frac{\gamma_h}{\gamma_0}\right)$$



$\Delta\theta$: Angle deviation for fixed photon energy,

ΔE : Energy deviation for fixed incident angle

$$W = \left\{ \Delta\theta \sin 2\bar{\theta}_{BK} + 2 \frac{\Delta E}{E} \sin^2 \bar{\theta}_{BK} + \frac{\chi_{0r}}{2} \left(1 - \frac{\gamma_h}{\gamma_0}\right) \right\} \sqrt{\frac{\gamma_0}{|\gamma_h|}} \frac{1}{|\chi_{hr}| \cdot |P|}$$

For symmetric Bragg case, sigma polarization:

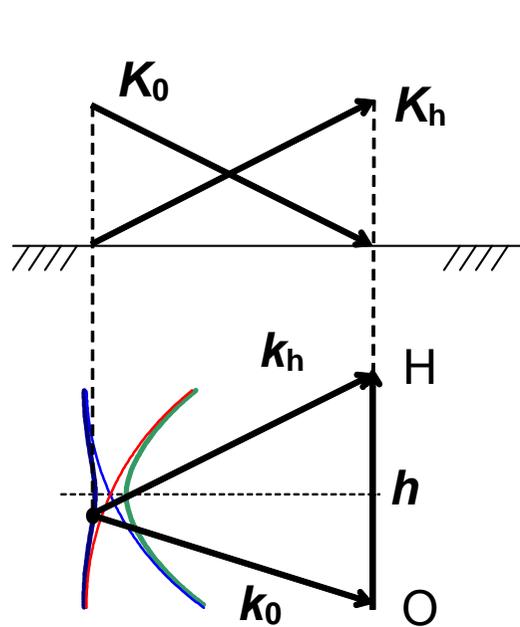
$$W = \left\{ \Delta\theta \sin 2\bar{\theta}_{BK} + 2 \frac{\Delta E}{E} \sin^2 \bar{\theta}_{BK} + \chi_{0r} \right\} \frac{1}{|\chi_{hr}|}$$

#7

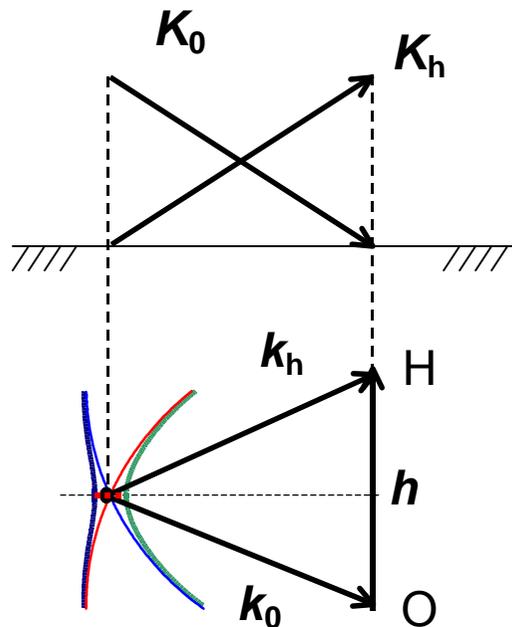
Movement of tie point

Tie point moves by *changing the incident angle*
at fixed photon energy (wavelength).

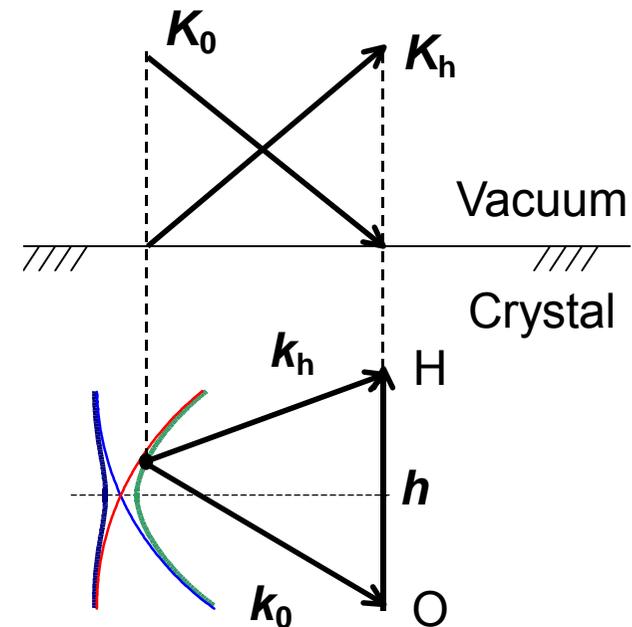
(1) Lower angle
 $W < -1$



(2) Near Bragg condition
 $-1 < W < 1$



(3) Higher angle
 $W > 1$



Total reflection

Dominant branch for thick Bragg-case crystal is close to **O-sphere**.

#8

Calculation of polarizability

χ_h : Fourier component of polarizability
 \rightarrow proportional to the structure factor

$$\chi_h = -\frac{r_e \lambda^2}{\pi v_c} F(\mathbf{h}, E)$$

v_c : unit cell volume

$$\chi_h = \chi_{hr} + i\chi_{hi}$$

$$\chi_{hr} \Leftrightarrow f^0(\mathbf{h}) + f'(E)$$

Atomic form factor
 + real part of anomalous factor

$$\chi_{hi} \Leftrightarrow f''(E)$$

Imaginary part of
 anomalous factor

For diamond structure

$$h + k + l = 4m$$

$$\chi_{hr} = -\frac{r_e \lambda^2}{\pi v_c} 8(f^0 + f')e^{-M}$$

$$\chi_{hi} = -\frac{r_e \lambda^2}{\pi v_c} 8f''e^{-M}$$

$$h + k + l = 4m \pm 1$$

$$\chi_{hr} = -\frac{r_e \lambda^2}{\pi v_c} 4(1+i)(f^0 + f')e^{-M}$$

$$\chi_{hi} = -\frac{r_e \lambda^2}{\pi v_c} 4(1+i)f''e^{-M}$$

$$h = k = l = 0$$

$$\chi_{0r} = -\frac{r_e \lambda^2}{\pi v_c} 8(Z + f')$$

$$\chi_{0i} = -\frac{r_e \lambda^2}{\pi v_c} 8f''$$

#9

Amplitude ratio

From **the solution** of the fundamental equations,
we obtain the ratio $r = E_h/E_0$ (\leftarrow reflection coefficient)
as a function of parameter W .

For Bragg case, no absorption, and thick crystal:

$$\left\{ \begin{array}{l} r = \frac{E_h}{E_0} = -\sqrt{\frac{\gamma_0}{|\gamma_h|}} \frac{|\chi_{hr}|}{\chi_{-h}} \frac{|P|}{P} \left(W + \sqrt{W^2 - 1} \right) \quad (W < -1) \\ r = \frac{E_h}{E_0} = -\sqrt{\frac{\gamma_0}{|\gamma_h|}} \frac{|\chi_{hr}|}{\chi_{-h}} \frac{|P|}{P} \left(W + i\sqrt{1 - W^2} \right) \quad (-1 \leq W \leq 1) \quad \leftarrow \text{Total reflection} \\ r = \frac{E_h}{E_0} = -\sqrt{\frac{\gamma_0}{|\gamma_h|}} \frac{|\chi_{hr}|}{\chi_{-h}} \frac{|P|}{P} \left(W - \sqrt{W^2 - 1} \right) \quad (W > 1) \end{array} \right.$$

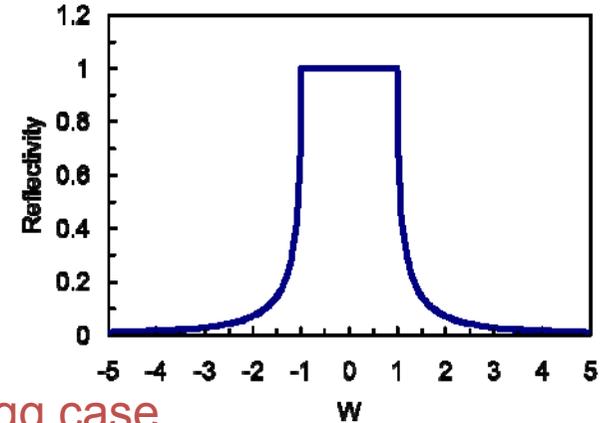
$$R = r^2$$

#10

Reflectivity (Darwin curve)

Darwin curve (intrinsic reflection curve for monochromatic plane wave) for Bragg case, no absorption, and thick crystal:

$$\begin{cases} R = \left(W + \sqrt{W^2 - 1}\right)^2 & (W < -1) \\ R = 1 & (-1 \leq W \leq 1) \leftarrow \text{Total reflection region} \\ R = \left(W - \sqrt{W^2 - 1}\right)^2 & (W > 1) \end{cases}$$



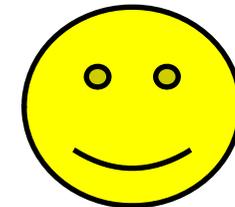
W : deviation parameter for s-polarization, symmetrical Bragg case

$$W = \left(\underbrace{\Delta\theta \sin 2\theta_B}_{\text{Angular deviation}} + \underbrace{2 \sin^2 \theta_B \frac{\Delta E}{E}}_{\text{Energy deviation}} + \underbrace{\chi_0}_{\text{Refraction}} \right) \frac{1}{|\chi_h|}$$

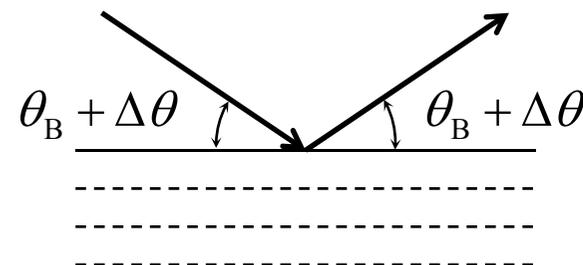
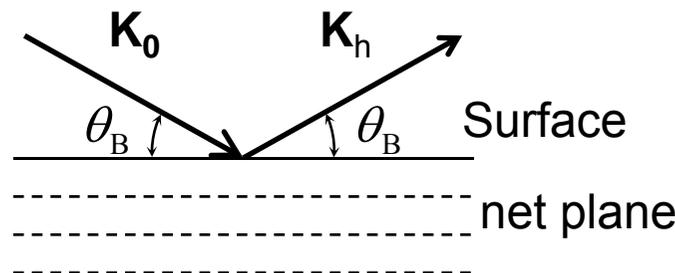
Angular deviation

Energy deviation

Refraction



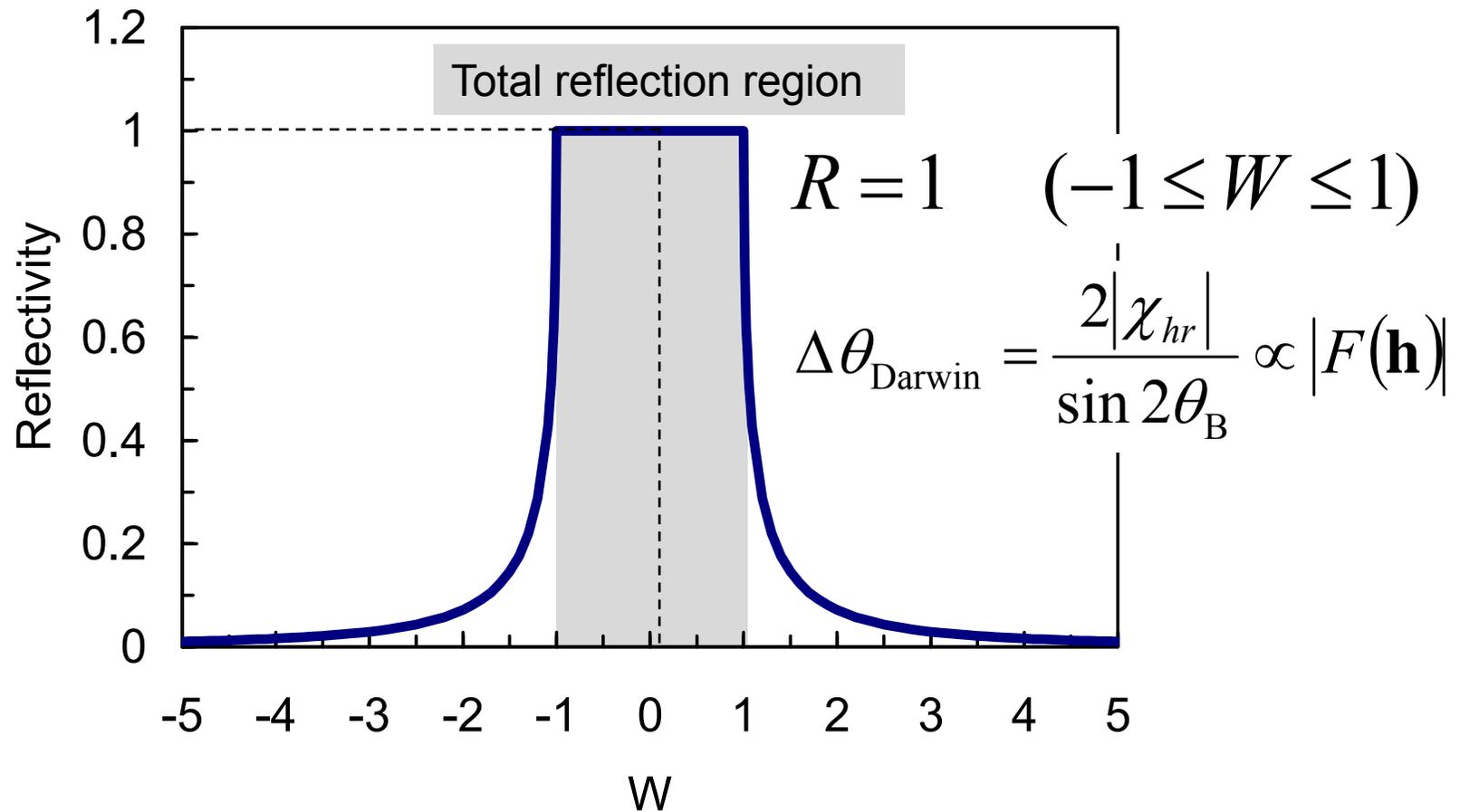
Geometry for symmetrical Bragg case



Darwin curve



For Bragg case, **no absorption**, and thick crystal:



Reflectivity with absorption

Reflectivity

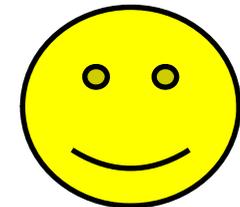
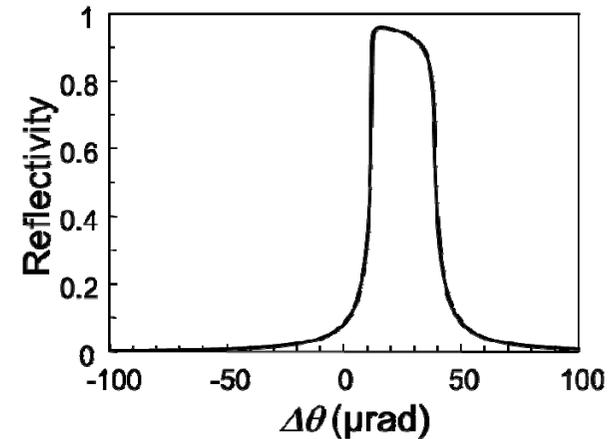
- symmetrical Bragg case,
- s-polarization,
- thick crystal

$$R = L - \sqrt{L^2 - 1}$$

$$L = \frac{\left\{ W^2 + g^2 + \sqrt{(W^2 - g^2 - 1 + \kappa^2)^2 + 4(gW - \kappa)^2} \right\}}{1 + \kappa^2}$$

$$W = \left(\Delta\theta \sin 2\bar{\theta}_B + 2 \sin^2 \bar{\theta}_B \frac{\Delta E}{E} + \chi_{0r} \right) \frac{1}{|\chi_{hr}|}$$

$$g = \frac{\chi_{0i}}{|\chi_{hr}|}, \quad \kappa = \frac{|\chi_{hi}|}{|\chi_{hr}|}$$



Note: No absorption $g = 0, \kappa = 0 \Rightarrow R \rightarrow \text{Darwin curve}$

Reflectivity curve for silicon



Examples for symmetrical Bragg case, **with absorption**,
s-polarization and thick crystal:

Si 111 refl., 10 keV

$$\chi_{0r} = -9.78 \times 10^{-6}$$

$$\chi_{0i} = -1.48 \times 10^{-7}$$

$$\chi_{111_r} = -3.66 \times 10^{-6}(1+i)$$

$$\chi_{111_i} = -7.30 \times 10^{-8}(1+i)$$

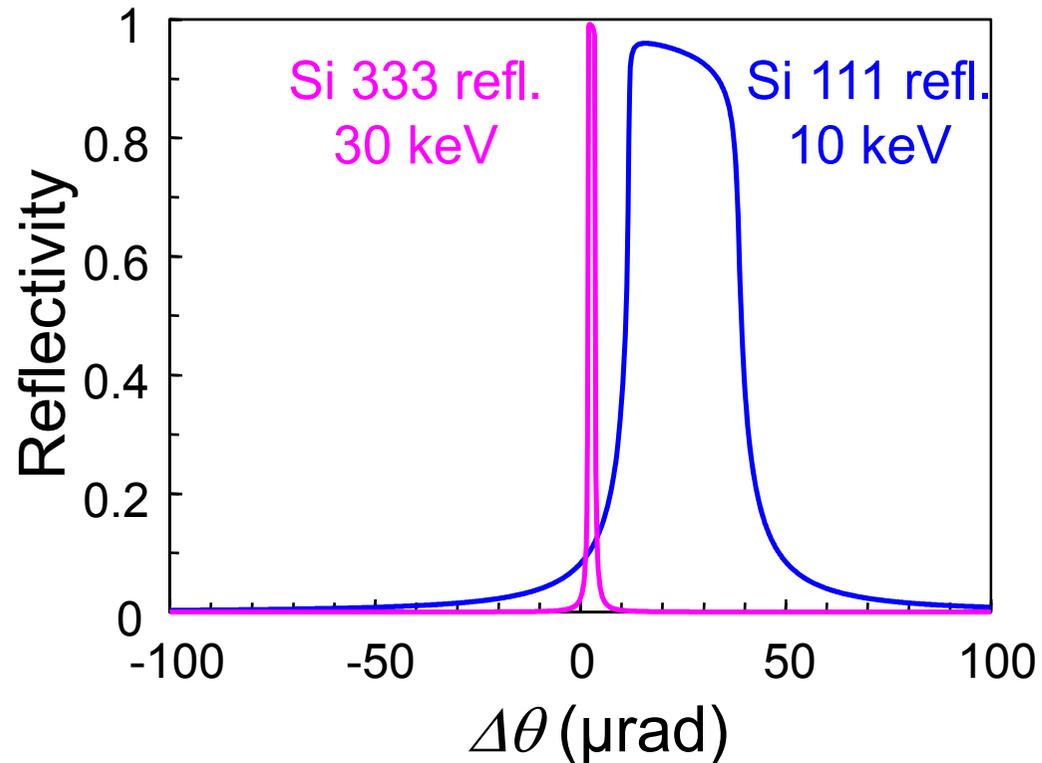
Si 333 refl., 30 keV

$$\chi_{0r} = -1.07 \times 10^{-6}$$

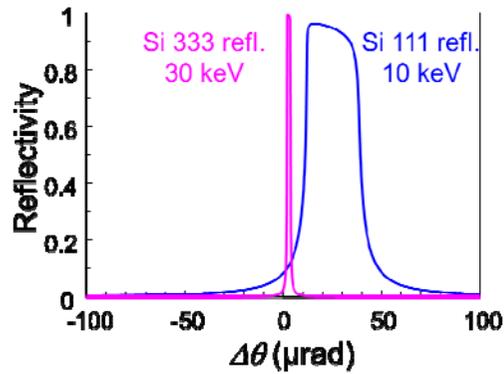
$$\chi_{0i} = -1.75 \times 10^{-9}$$

$$\chi_{333_r} = -2.24 \times 10^{-7}(1+i)$$

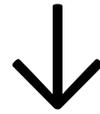
$$\chi_{333_i} = -7.87 \times 10^{-10}(1+i)$$



- Width of 0.1 ~ 100 μrad
- Peak ~1 with small absorption



Tailoring x-rays to application



X-ray monochromator

■ Principle

- ✓ Introduction of diffraction theory
- ✓ Dynamical theory
- ✓ DuMond diagram

■ Engineering





DuMond (angle-energy) diagram

The diagram helps to understand how we can extract x-rays from SR source.

Angular width
(Darwin width)

$$\Delta\theta_{\text{Darwin}} = \frac{2|\chi_{hr}|}{\sin 2\theta_B} \propto |F(\mathbf{h})| \quad \leftarrow \Delta W = 2$$

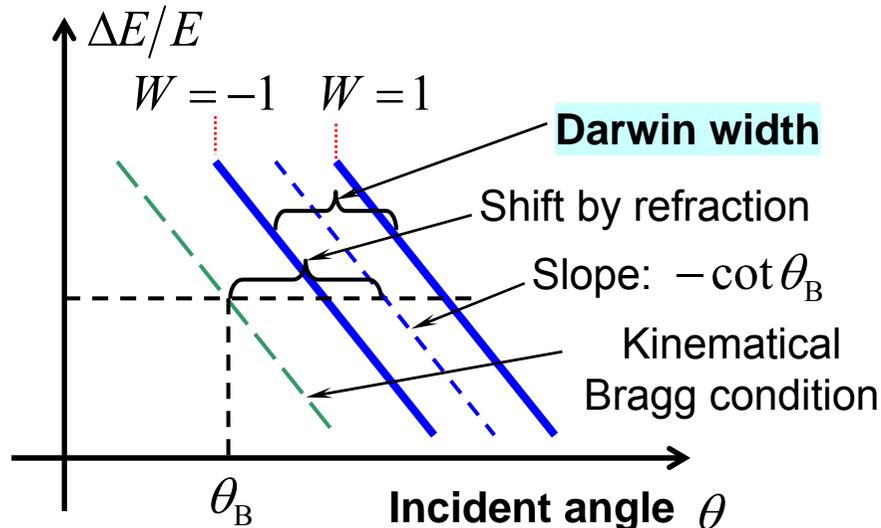
Energy resolution

$$\frac{\Delta E}{E} = \cot \theta_B \sqrt{\Omega^2 + \Delta\theta_{\text{Darwin}}^2} \quad \leftarrow \text{Gaussian approximation for both light source and reflection curve}$$

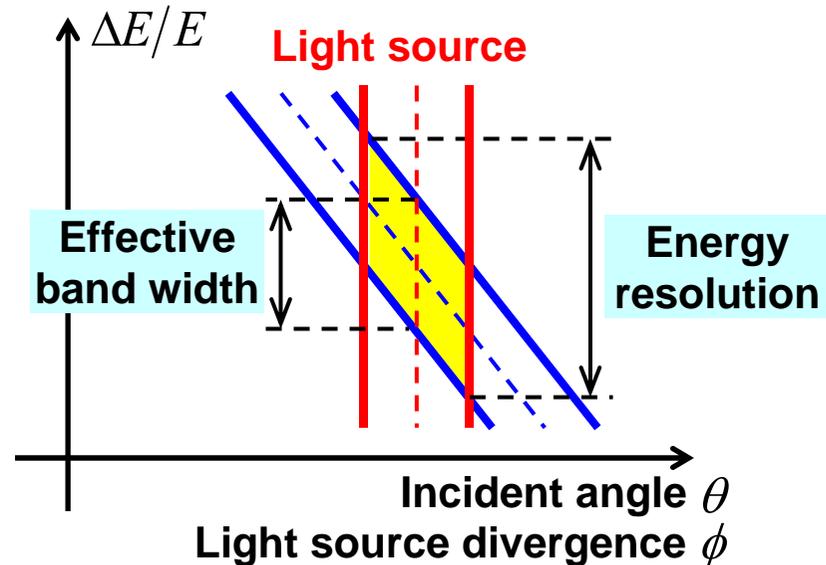
Effective band width

$$\frac{\Delta E}{E} \approx \frac{|\chi_{hr}|}{\sin^2 \theta_B}$$

Relative energy

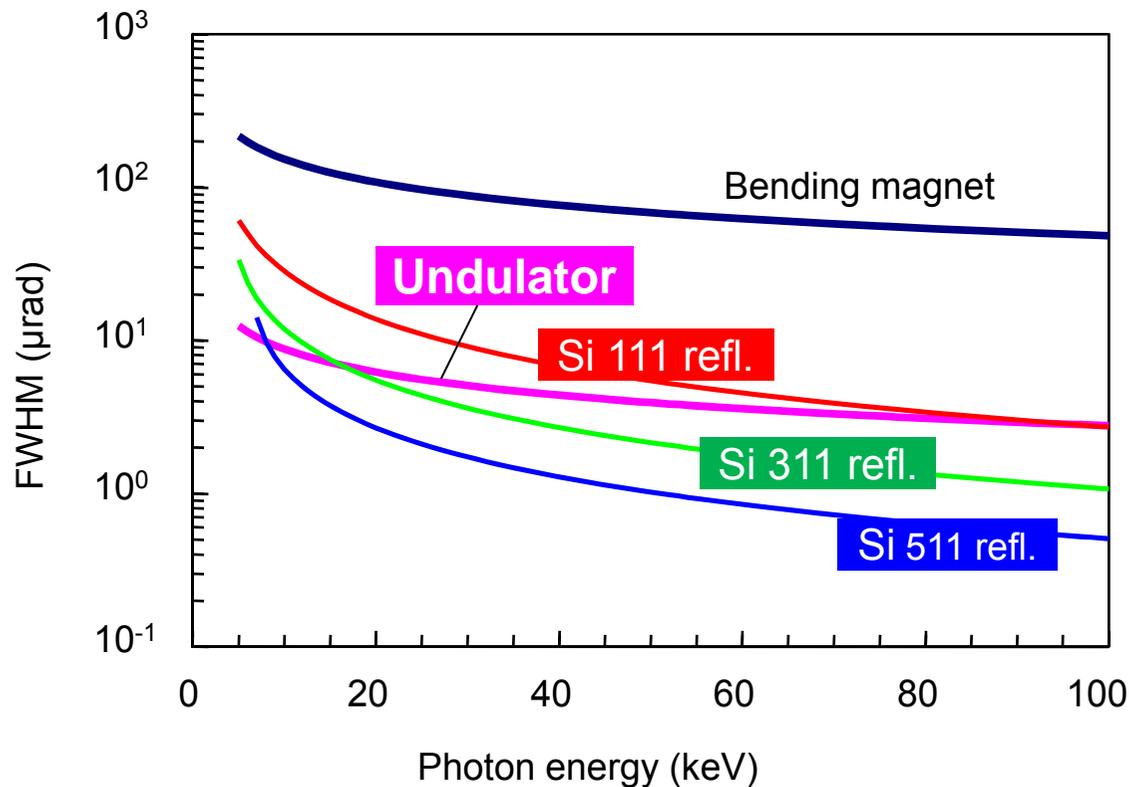


Relative energy





Source divergence and diffraction width



Natural divergence

- Bending magnet

$$\sigma_{r'} \approx 0.597 \frac{1}{\gamma} \sqrt{\frac{\lambda}{\lambda_c}} \propto \sqrt{\frac{1}{h\omega}}$$

- Undulator

$$\sigma_{r'} \approx \sqrt{\frac{\lambda}{2N\lambda_u}} \propto \sqrt{\frac{1}{h\omega}}$$

For SPring-8 case:

- Bending magnet

$$\sigma_{r'} \approx 60 \mu\text{rad}$$

- Undulator (N= 140)

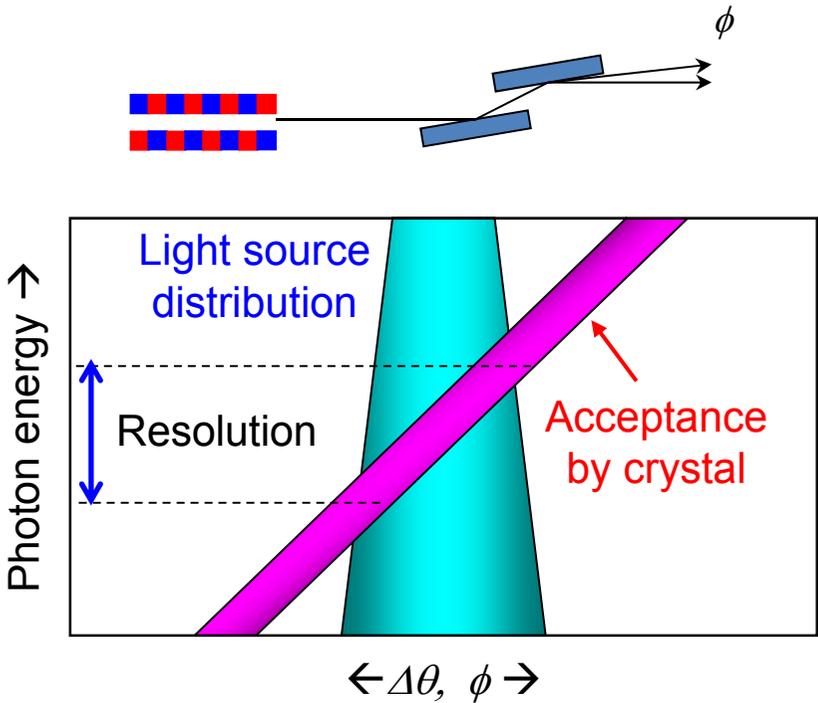
$$\sigma_{r'} \approx 5 \mu\text{rad}$$

Divergence of undulator radiation ~ diffraction width

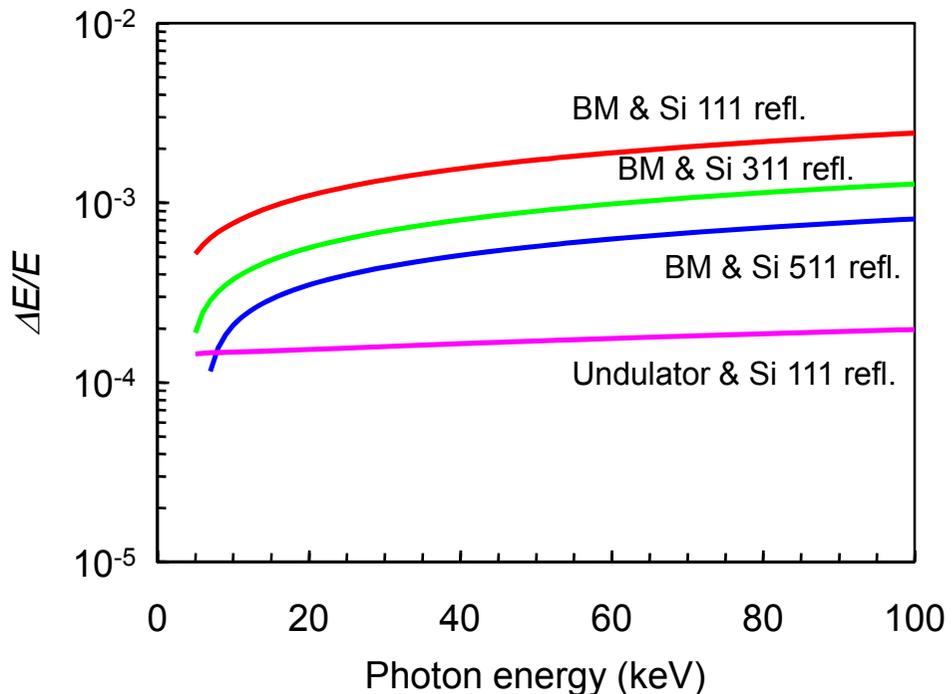
Energy resolution

$$\frac{\Delta E}{E} = \cot \theta_B \sqrt{\Omega^2 + \omega^2}$$

Ω : source divergence,
 ω : diffraction width

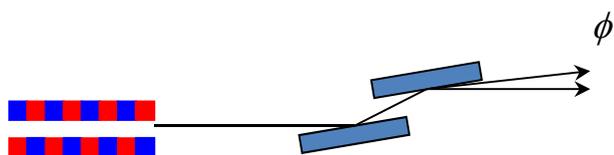


Angle-energy diagram
 (DuMond diagram)



For usual beamline : $\Delta E/E = 10^{-5} \sim 10^{-3}$

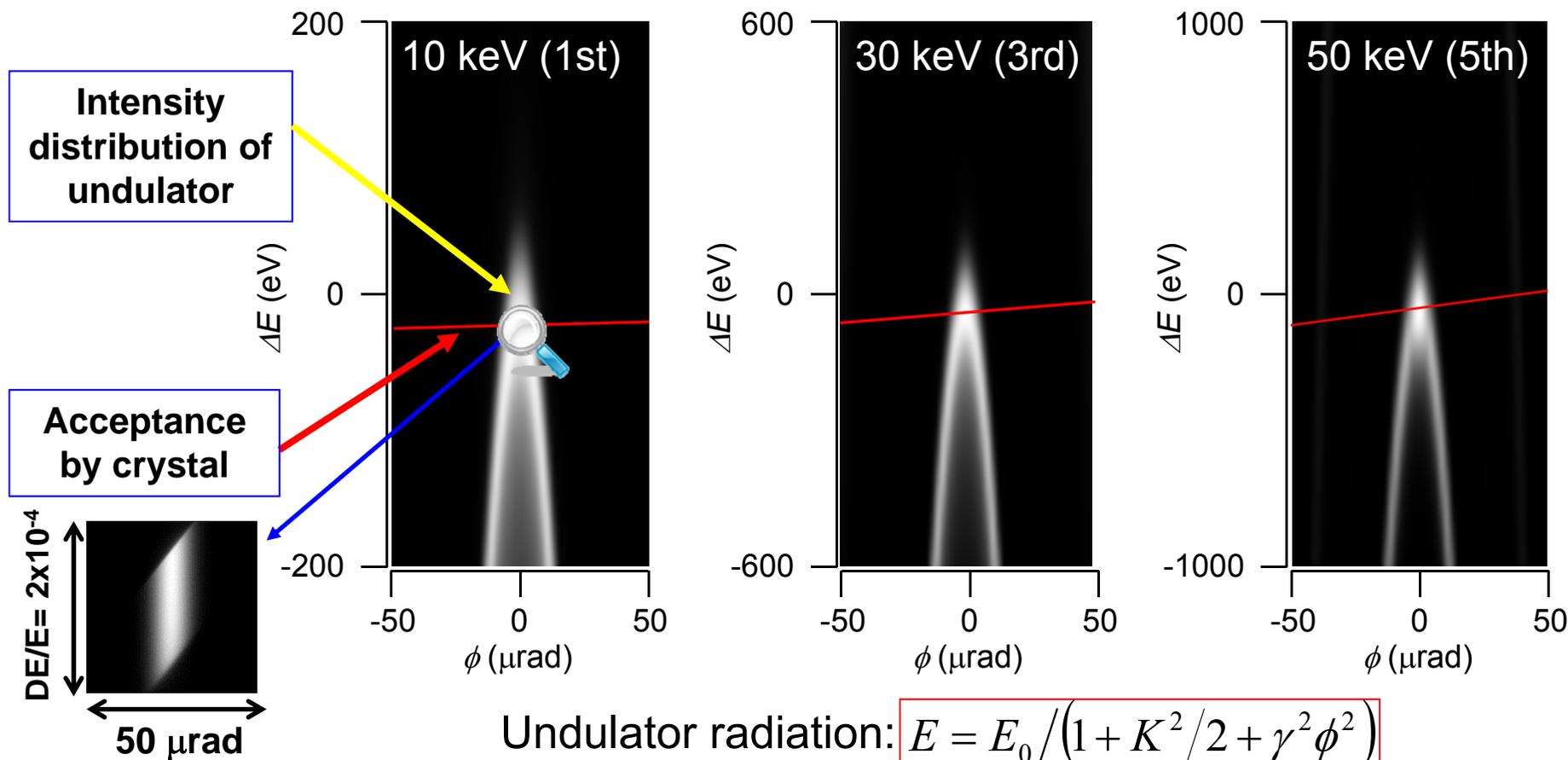
DuMond diagram: undulator & DCM



SPring-8 standard undulator

($\lambda_u = 32$ mm, $N = 140$, $K = 1.34$, $E_{1st} = 10$ keV)

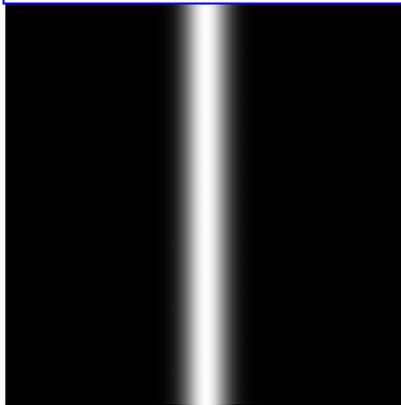
+ DCM (Si 111 refl.)



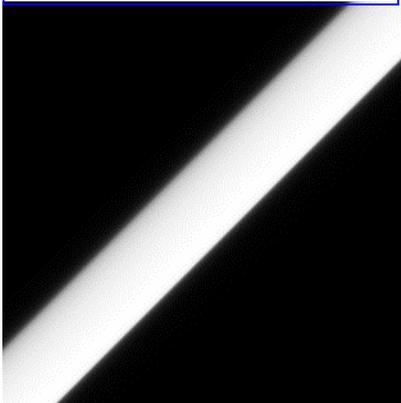
Wider slit increases unused photons (power) on the monochromator !

DuMond diagram: undulator & DCM

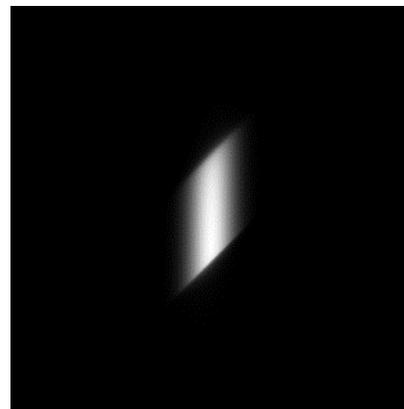
Undulator radiation



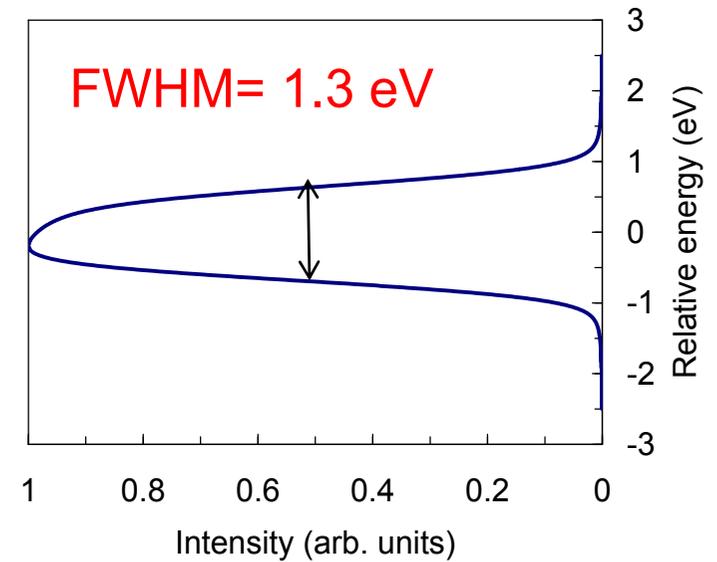
Acceptance by
Si 111 DCM



$$\Delta E/E = 5 \times 10^{-4}$$



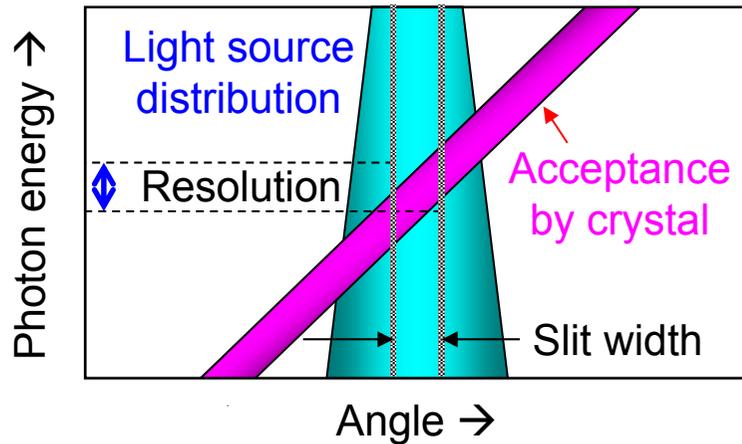
100 μ rad



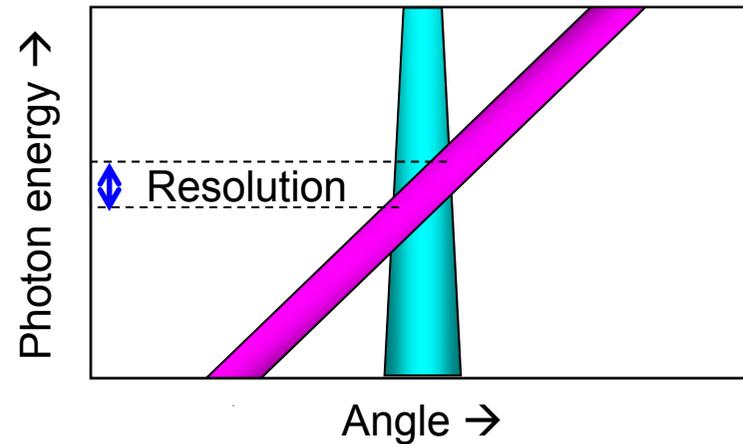
Spring-8 standard undulator + 20 μ rad slit + Si 111 DCM

10-keV photons \rightarrow 1.3×10^{-4}

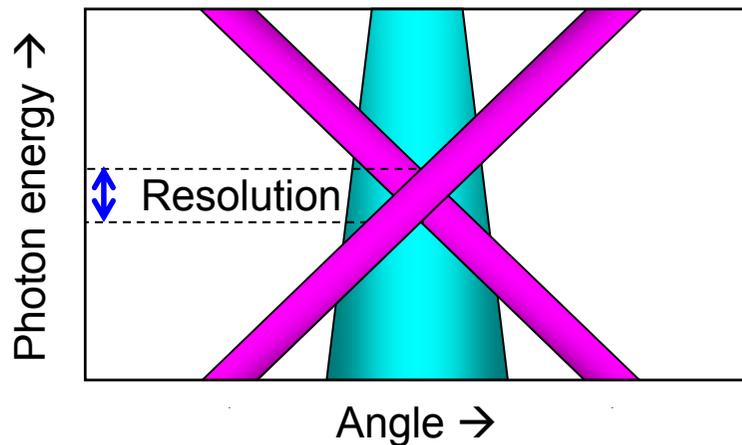
Improvement of energy resolution



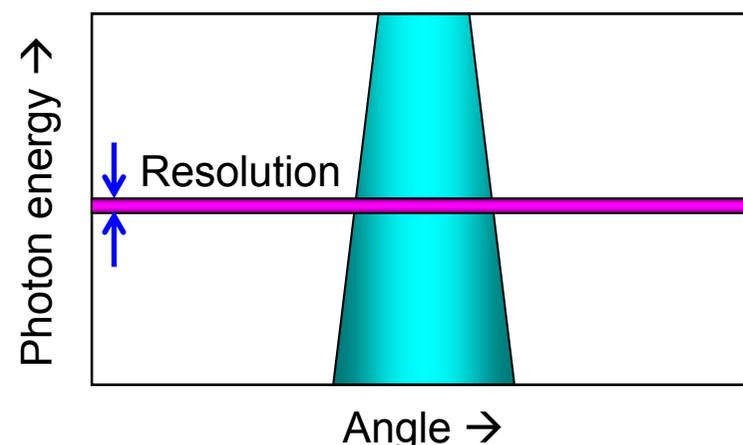
(A) Collimation using slit



(B) Collimation using pre-optics w/ collimation mirror, CRL,...



(C) Additional crystal w/ (+,+) setting

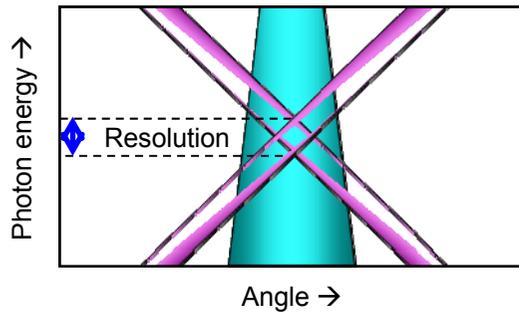


(D) HR monochromator of $\pi/2$ reflection (~meV)

(B)~(D): restriction on photon energy

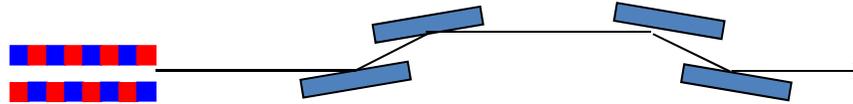
Improvement of energy resolution

(C) Additional crystal w/ (+,+) setting
 → HXPES

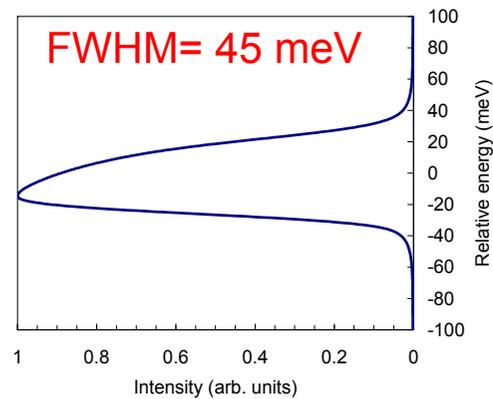
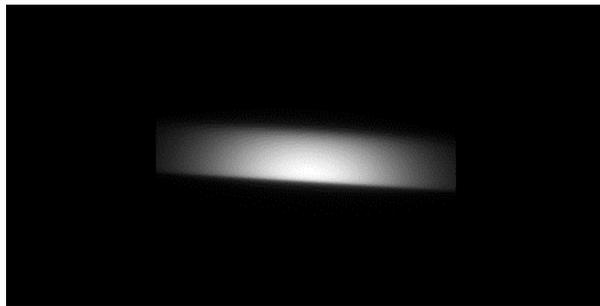


Si 111 DCM

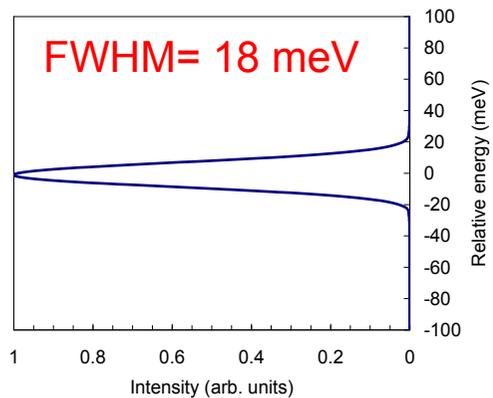
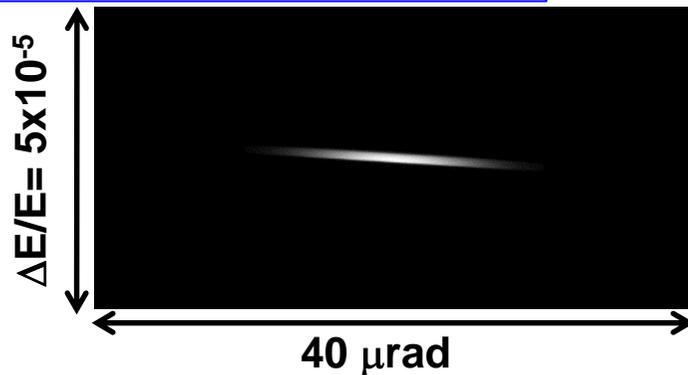
Si *nnn* channel-cut mono.



Si 333 refl. for 6 keV



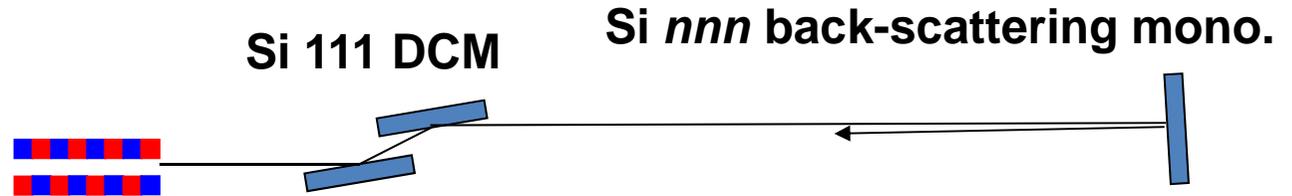
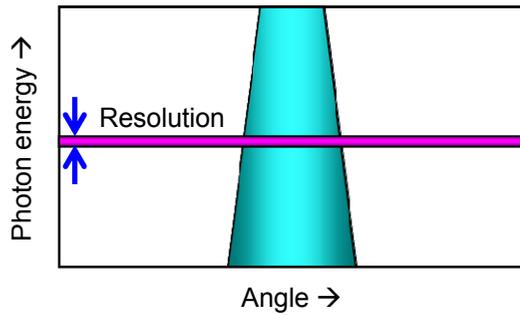
Si 555 refl. for 10 keV



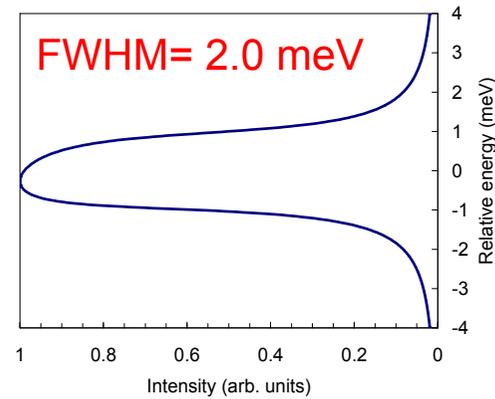
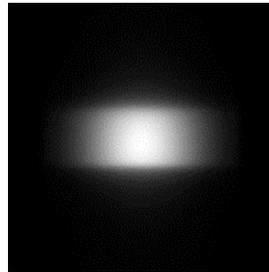
Improvement of energy resolution

(D) HR monochromator of $\sim\pi/2$ reflection ($\sim\text{meV}$)

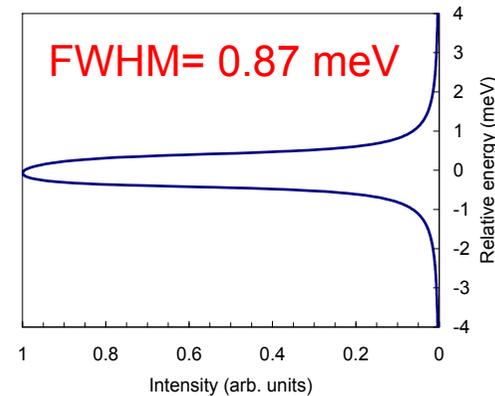
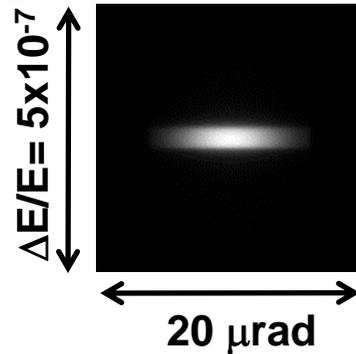
\rightarrow Inelastic scattering



Si 999 refl. for 17.8 keV



Si 11 11 11 refl. for 21.7 keV



Photon flux after monochromator

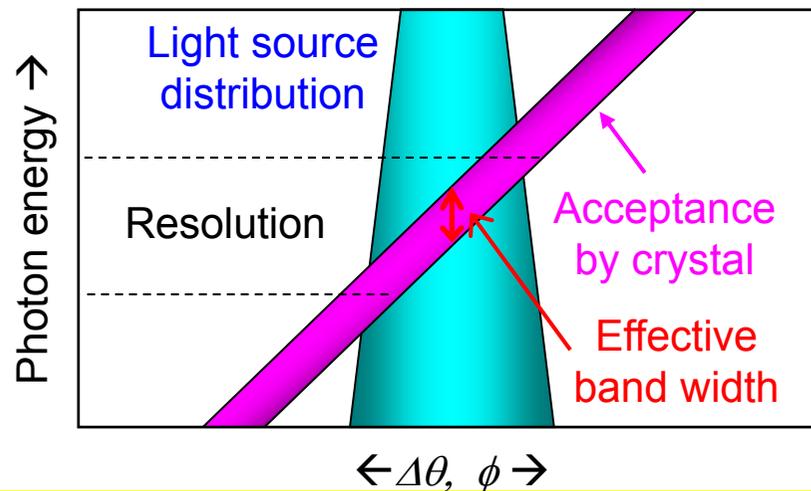
Photon flux (throughput) after monochromator can be estimated using effective band width:

Photon flux (ph/s) =

Photon flux from light source (ph/s/0.1%bw)

x 1000

x **Effective band width** of monochromator
~~Energy resolution~~



Throughput is estimated by overlapped area.

Note difference from energy resolution.

Effective band width

Starting with Darwin width in the energy axis

$$\frac{\Delta E}{E} \approx \frac{|\chi_{hr}|}{\sin^2 \theta_B}$$

$$\chi_{hr} \propto \lambda^2 \{f^0(d_{hkl}) + f'(\lambda)\}$$

Neglecting anomalous scattering factor f'

$$\chi_{hr} \propto \lambda^2 f^0(d_{hkl})$$

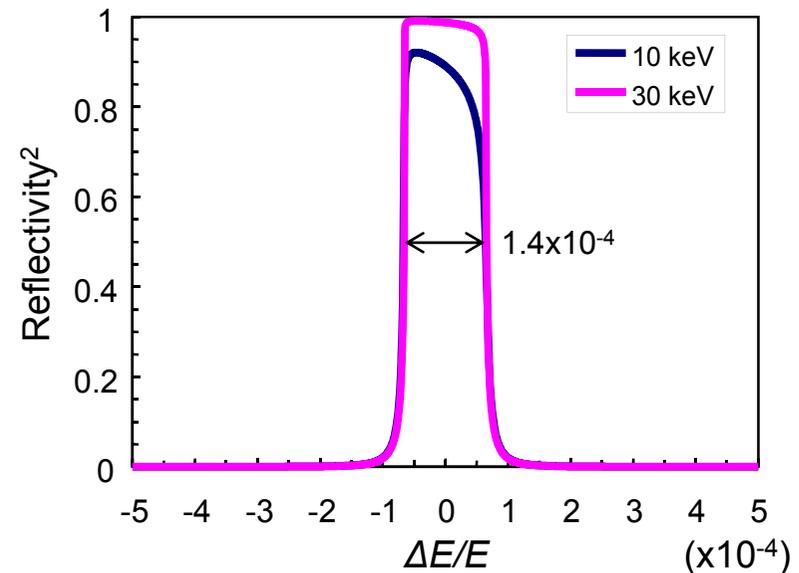
$$\frac{\Delta E}{E} = -\frac{\Delta \lambda}{\lambda} \approx \frac{|\chi_{hr}|}{\sin^2 \theta_B}$$

$$= 4d_{hkl}^2 \frac{|\chi_{hr}|}{\lambda^2}$$

$$\frac{\Delta E}{E} = -\frac{\Delta \lambda}{\lambda} \propto d_{hkl}^2 f^0(d_{hkl})$$



Independent of photon energy



e.g. for Si 111 refl. DCM case

Note relative energy width is constant.

Effective band width (Integrated intensity)

For single-bounce monochromator

$$\frac{\Delta E}{E} = \frac{|\chi_{hr}|}{2 \sin^2 \theta_B} \int R(W) dW$$

$$= \frac{8}{3} \frac{|\chi_{hr}|}{2 \sin^2 \theta_B}$$

↑ For no absorption

For double-crystal monochromator

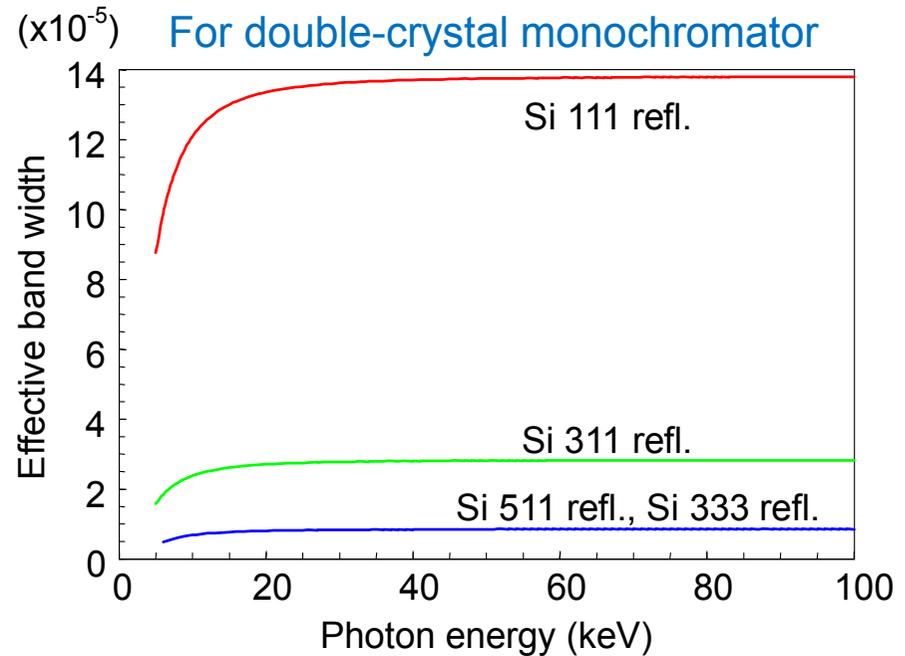
$$\frac{\Delta E}{E} = \frac{|\chi_{hr}|}{2 \sin^2 \theta_B} \int R(W)^2 dW$$

$$= \frac{32}{15} \frac{|\chi_{hr}|}{2 \sin^2 \theta_B}$$

↑ For no absorption

When you need flux → Lower order (Si 111 refl.,...)

When you need resolution → Higher order (Si 311, Si 511 refl.,...)



Effective band-width is obtained by integration of reflection curve.

Photon flux estimation

Effective band width

Reflection (nominal energy)	Effective band width
Si 111 DCM (6 keV)	1.0045x10 ⁻⁴
Si 111 DCM (8 keV)	1.1399x10 ⁻⁴
Si 111 DCM (10 keV)	1.2216x10 ⁻⁴
Si 111 DCM (12 keV)	1.2710x10 ⁻⁴
Si 111 DCM (14 keV)	1.3021x10 ⁻⁴
Si 333 DCM (14 keV)	8.0996x10 ⁻⁶

$$Flux = \int S(E, \phi) R(E, \phi)^2 dE d\phi$$

Photon flux (ph/s/100mA/20 μrad(H))

(A) SPECTRA × Effective band width ⇔ (B) SPECTRA × DuMond

Reflection	Flux (A)	Flux (B)
Si 111 DCM (6 keV)	5.68x10 ¹³	5.70x10 ¹³
Si 111 DCM (8 keV)	6.14x10 ¹³	6.15x10 ¹³
Si 111 DCM (10 keV)	6.01x10 ¹³	6.02x10 ¹³
Si 111 DCM (12 keV)	5.28x10 ¹³	5.29x10 ¹³
Si 111 DCM (14 keV)	4.20x10 ¹³	4.20x10 ¹³
Si 333 DCM (14 keV)	2.62x10 ¹²	2.61x10 ¹²

Photon flux estimation

Effective band width

Reflection (nominal energy)	Effective band width
Si 111 DCM (6 keV)	1.0045x10 ⁻⁴
Si 111 DCM (10 keV)	
Si 111 DCM (12 keV)	
Si 111 DCM (14 keV)	
Si 333 DCM (14 keV)	

Photon flux (throughput) after monochromator can be estimated using effective band width:

Photon flux (ph/s) =

Photon flux from light source (ph/s/0.1%bw)

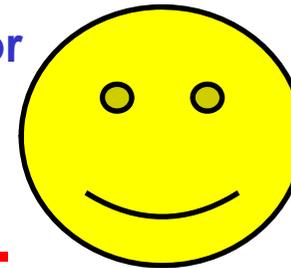
x 1000

x Effective band width of monochromator

$$(\phi)^2 dEd\phi$$

Photon flux
(A)

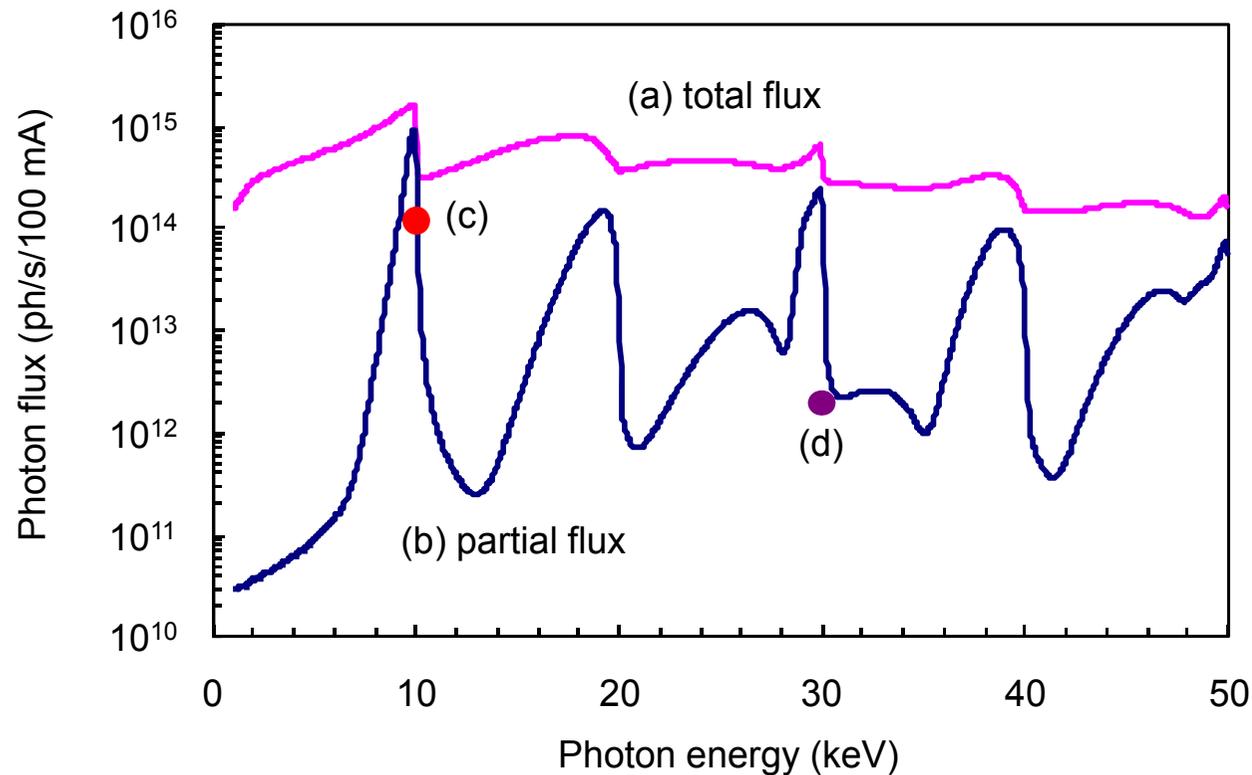
μMond



This approach is valid.

Si 111 DCM (10 keV)	6.01x10 ¹³	6.02x10 ¹³
Si 111 DCM (12 keV)	5.28x10 ¹³	5.29x10 ¹³
Si 111 DCM (14 keV)	4.20x10 ¹³	4.20x10 ¹³
Si 333 DCM (14 keV)	2.62x10 ¹²	2.61x10 ¹²

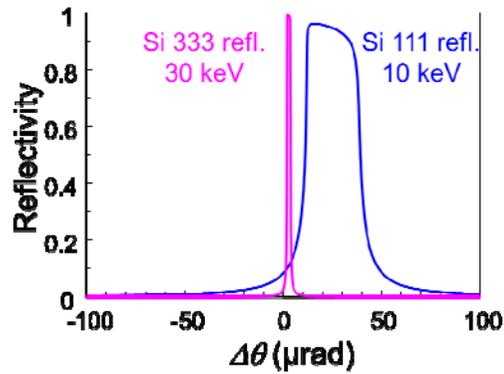
Photon flux at undulator beamline



- (a) Total flux @ 0.1% b.w.
- (b) After frontend slit
 $1 \times 1 \text{ mm}^2$ @30 m
- (c) Si 111 refl. @10 keV
Effective b.w. = 1.3×10^{-4}
- (d) 3rd harmonics @30 keV
Effective b.w. = 8.0×10^{-6}

Higher harmonics elimination more → mirror or detuning of DCM

We can obtain photon flux of $10^{13} \sim 10^{14}$ ph/s/100 mA/mm² using standard undulator sources and Si 111 reflections at SPring-8 beamlines.



Tailoring x-rays to application



X-ray monochromator

■ Principle

- ✓ Introduction of diffraction theory
- ✓ Dynamical theory
- ✓ DuMond diagram

■ Engineering

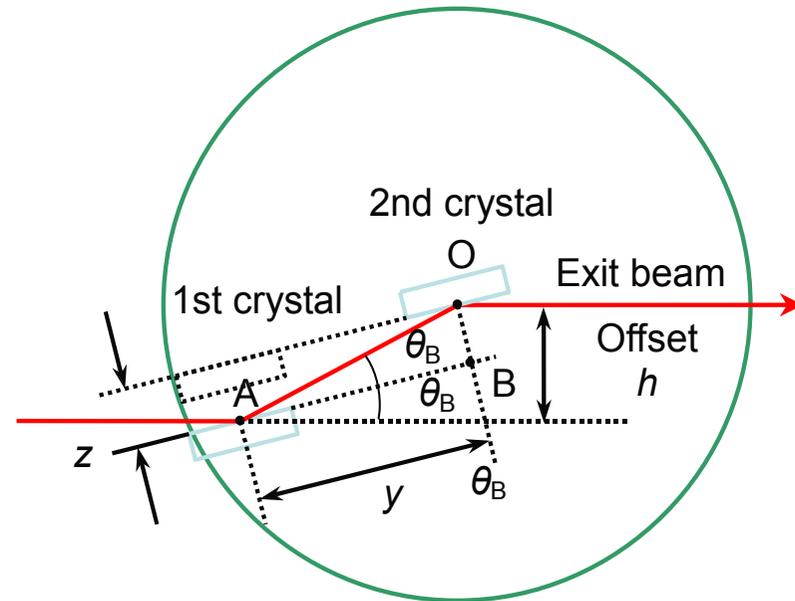


Double-crystal monochromator

- ✓ Fixed-exit operation for usability at experimental station.
- ✓ Choose suitable mechanism for energy range (Bragg angle range).
- ✓ Precision, stability, rigidity,...

$$y = AB = \frac{h}{2 \sin \theta_B}$$

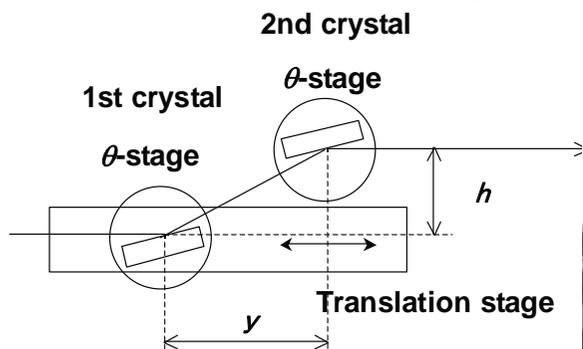
$$z = OB = \frac{h}{2 \cos \theta_B}$$



Fixed-exit operation using rotation (θ) + two translation mechanism

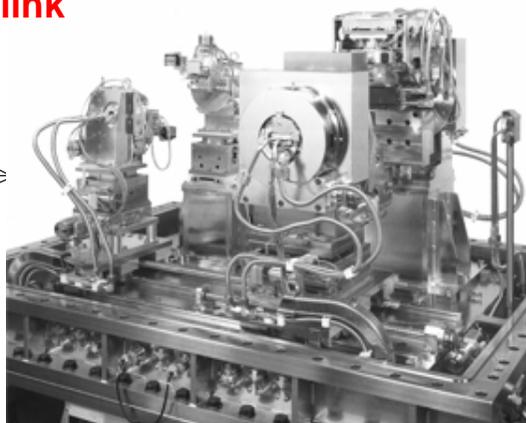
Double-crystal monochromator

θ_1 + translation + θ_2 computer link



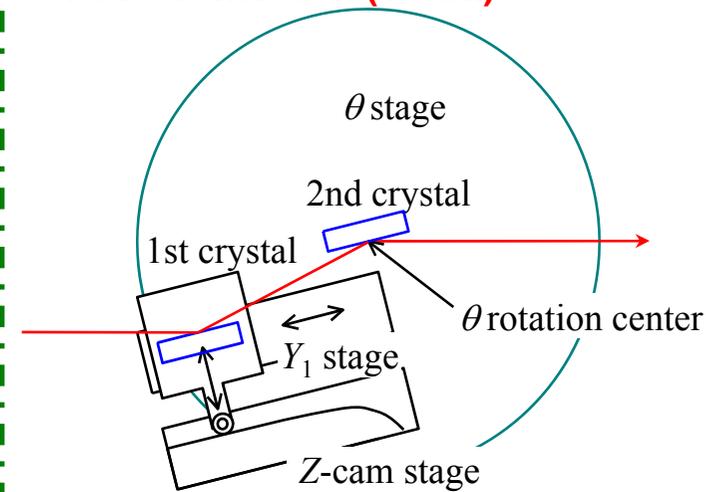
$h = 100$ mm,

$\theta_B = 5.7 \sim 72^\circ$ (for lower energy range)



SPring-8 BL15XU

θ + two translation (1 cam)



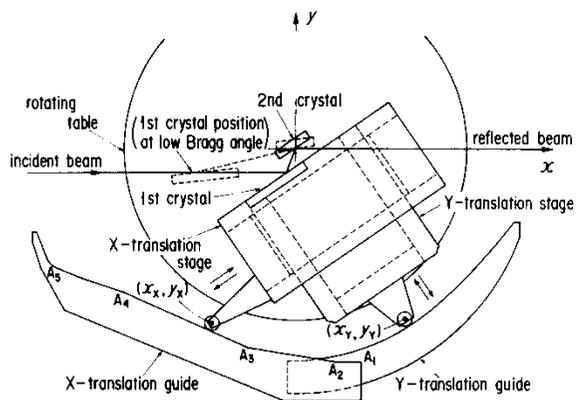
Offset $h = 30$ mm
 $= 3 \sim 27^\circ$ for higher energy range

θ_B

SPring-8 std. DCM 127

Yabashi et al., Proc. SPIE 3773, 2 (1999) 127

θ + two translation (2 cams)



$h = 25$ mm, $\theta_B = 5 \sim 70^\circ$

KEK-PF BL-4C

Matsushita et al., NIM A246 (1986)

Crystal cooling

Why crystal cooling ?

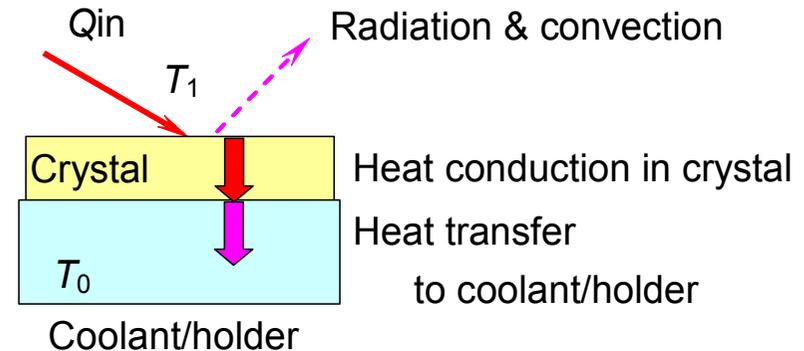
Q_{in} (Heat load by SR) = Q_{out} (Cooling + Radiation,...)

→ with temperature rise ΔT

→ $\alpha \Delta T = \Delta d$ (d -spacing change)

α : thermal expansion coefficient

or → $\Delta \theta$ (bump of lattice due to heat load)



Miss-matching between 1st and 2nd crystals occurs:

→ Thermal drift, loss of intensity, broadening of beam, loss of brightness

→ Melting or limit of thermal strain → **Broken !**

We must consider:

- Thermal expansion of crystal: α ,
- Thermal conductivity in crystal: κ ,
- Heat transfer to coolant and crystal holder.

Solutions:

(S-1) κ/α → Larger

(S-2) Contact area between crystal and coolant/holder
→ larger

(S-3) Irradiation area → Larger,
and power density → smaller

Figure of merit

	Silicon	Silicon	Diamond
	300 K	80 K	300 K
κ (W/m/K)	150	1000	2000
α (1/K)	2.5×10^{-6}	-5×10^{-7}	1×10^{-6}
$\kappa/\alpha \times 10^6$	60	2000	2000

Figure of merit of cooling:
Good for silicon (80 k)
and diamond (300 K)

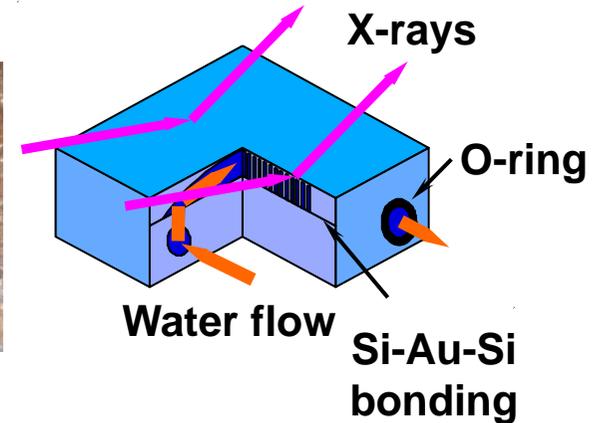
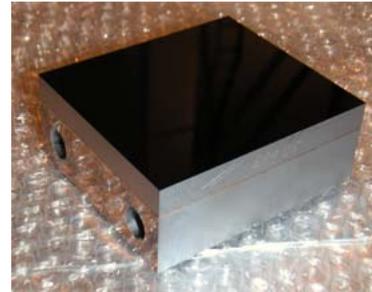
Crystal cooling at SPring-8



<Bending magnet beamline>

Power & power density:
~100 W, ~1 W/mm²

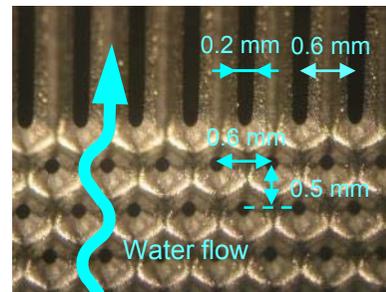
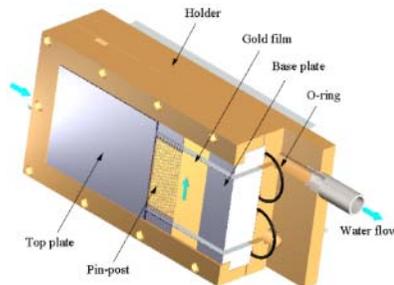
Fin crystal direct-cooling - (S2)



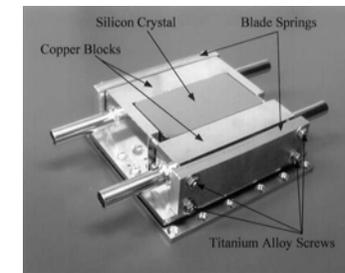
<Undulator beamline>

Linear undulator, $N=140$, $\lambda_u=32$ mm
Power & power density: 300~500 W ,
300~500 W/mm²

a) Direct cooling of silicon pin-post crystal - (S2) & (S3)



b) Silicon cryogenic cooling - (S1)



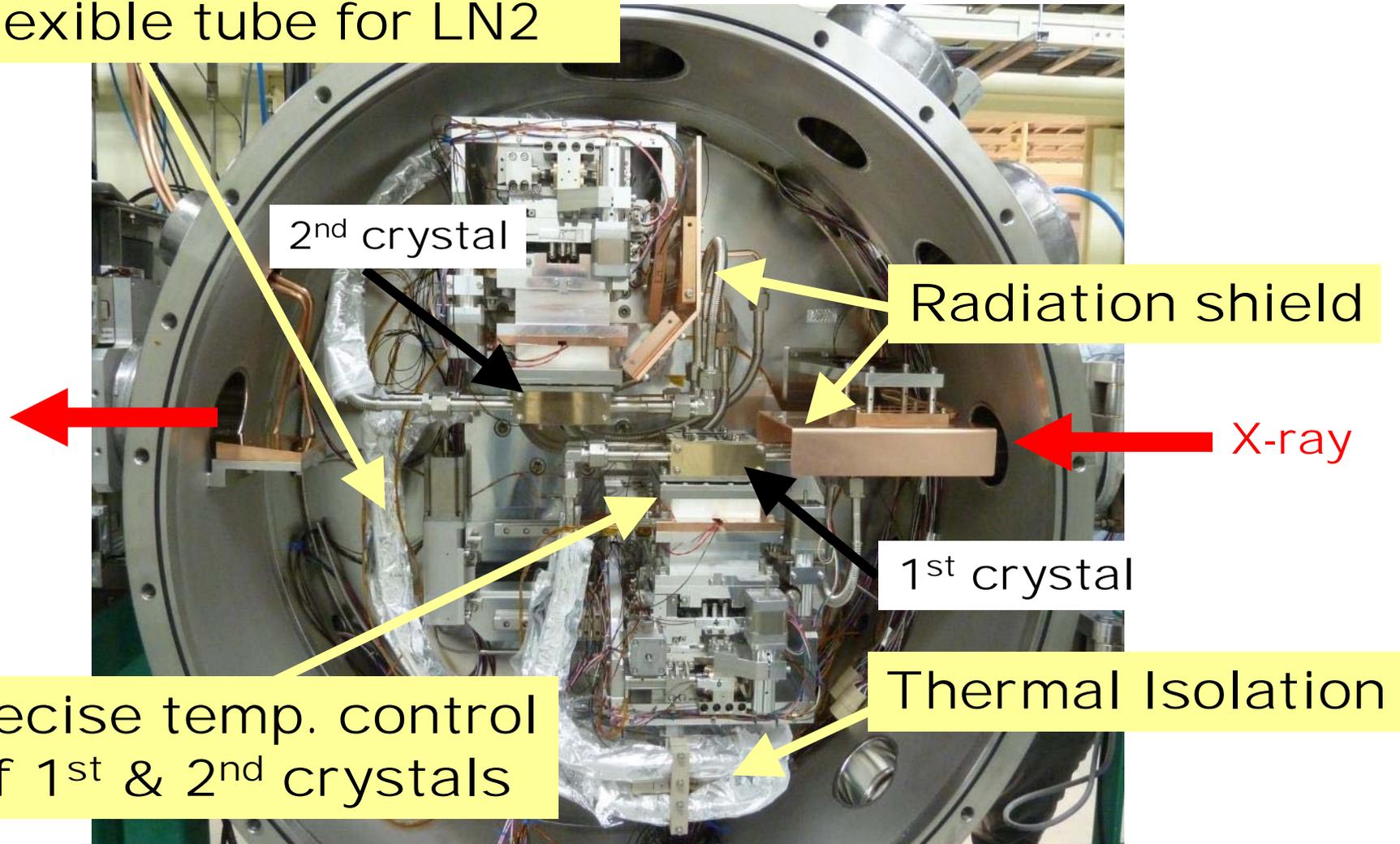
c) Ila diamond with indirect water cooling - (S1)



Improvement of stability of DCM



Turbulence suppressing flexible tube for LN2



Improvement of stability of DCM

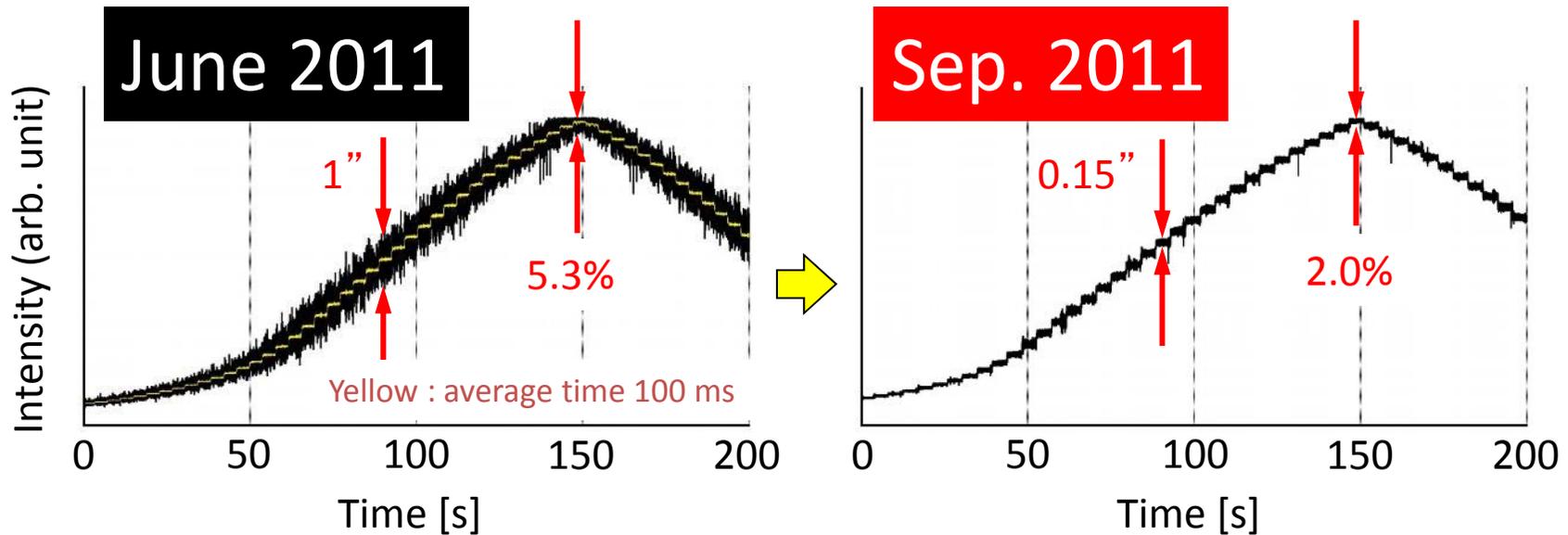
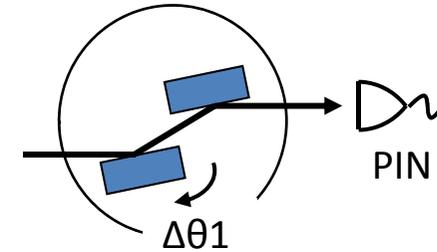


Measured Intensity fluctuation of 1 Å x-rays at BL13XU

Average time : 1 ms ··· very sensitive

Measurement frequency : 1 kHz

$\Delta\theta 1$ stage : 0.2" stepping at a time interval of 5 s



Angular fluctuation between the crystals : **1" → 0.15"**

Intensity fluctuation of 1 Å x-rays : **5% → 2%**

Key issues of X-ray monochromator

Introducing the [dynamical x-ray diffraction](#) for [large & perfect crystal](#),

w/ several important points:

- 1) Total reflection occurs at the gap between dispersion surfaces.
- 2) Normalized deviation parameter W is related to the gap.
- 3) W is parameter of angular deviation and energy (wavelength) deviation.

It gives [DuMond diagram](#) as a band of $|W| < 1$.

- 4) By combination of light source and monochromator crystals, photon energy, energy resolution, photon flux, . . . can be controlled / tuned.

Double-crystal monochromator w/ crystal cooling is needed for practical use at the SR beamline.

By understanding these, you will be approaching to good design/use of the beamline for your SR science.

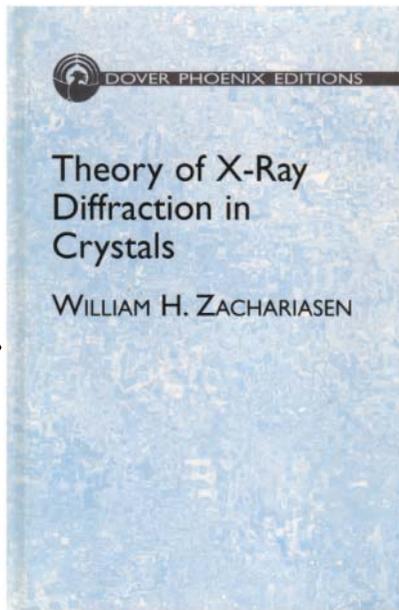
Text books following Laue's dynamical theory

Ergebnisse der Exakt Naturwiss.

10 (1931) 133-158.



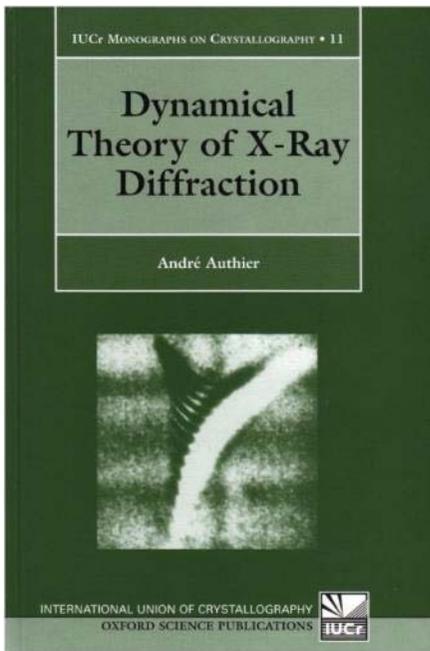
Dover (1945)



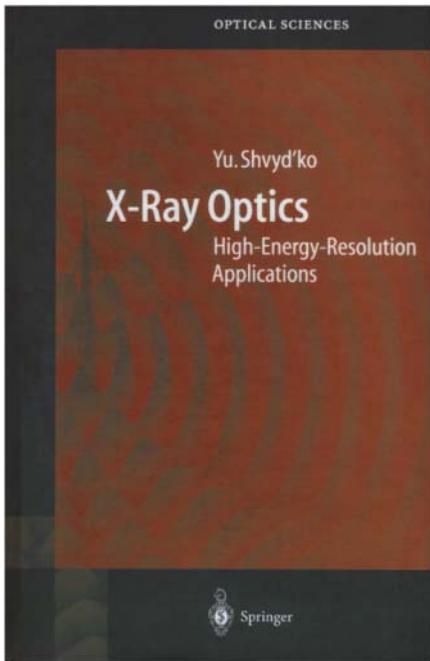
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Springer (2004)

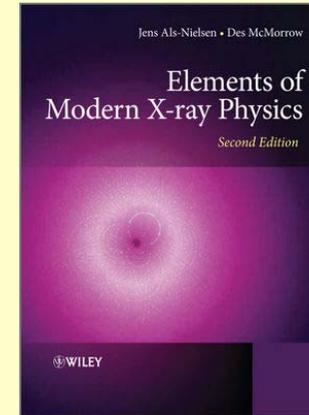


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 ISBN 978-4-13-062831-0
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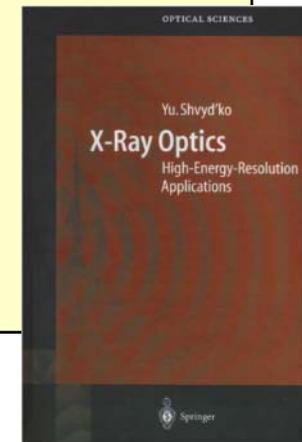
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For atomic scattering factor

➤ For f^0

[3] International Tables for X-ray Crystallography (IUCr).

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➤ For anomalous scattering factor f' , f''

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Thank you for your kind attention.

Enjoy Cheiron school

Enjoy SPring-8

and

Enjoy Japan!